

S5D9 Microcontroller Group

Datasheet

Renesas Synergy™ Platform
Synergy Microcontrollers
S5 Series

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Leading performance 120-MHz Arm® Cortex®-M4 core, up to 2-MB code flash memory, 640-KB SRAM, Graphics LCD Controller, 2D Drawing Engine, Capacitive Touch Sensing Unit, Ethernet MAC Controller with IEEE 1588 PTP, USB 2.0 High-Speed, USB 2.0 Full-Speed, SDHI, Quad SPI, security and safety features, and advanced analog.

Features

■ Arm Cortex-M4 Core with Floating Point Unit (FPU)

- Armv7E-M architecture with DSP instruction set
- Maximum operating frequency: 120 MHz
- Support for 4-GB address space
- On-chip debugging system: JTAG, SWD, and ETM
- Boundary scan and Arm Memory Protection Unit (Arm MPU)

■ Memory

- Up to 2-MB code flash memory (40 MHz zero wait states)
- 64-KB data flash memory (125,000 erase/write cycles)
- Up to 640-KB SRAM
- Flash Cache (FCACHE)
- Memory Protection Units (MPU)
- Memory Mirror Function (MMF)
- 128-bit unique ID

■ Connectivity

- Ethernet MAC Controller (ETHERC)
- Ethernet DMA Controller (EDMAC)
- Ethernet PTP Controller (EPTPC)
- USB 2.0 High-Speed (USBHS) module
 - On-chip transceiver with voltage regulator
 - Compliant with USB Battery Charging Specification 1.2
- USB 2.0 Full-Speed (USBFS) module
 - On-chip transceiver with voltage regulator
- Serial Communications Interface (SCI) with FIFO × 10
- Serial Peripheral Interface (SPI) × 2
- I²C bus interface (IIC) × 3
- Controller Area Network (CAN) × 2
- Serial Sound Interface Enhanced (SSIE) × 2
- SD/MMC Host Interface (SDHI) × 2
- Quad Serial Peripheral Interface (QSPI)
- IrDA interface
- Sampling Rate Converter (SRC)
- External address space
 - 8-bit or 16-bit bus space is selectable per area
 - SDRAM support

■ Analog

- 12-bit A/D Converter (ADC12) with 3 sample-and-hold circuits each × 2
- 12-bit D/A Converter (DAC12) × 2
- High-Speed Analog Comparator (ACMPHS) × 6
- Programmable Gain Amplifier (PGA) × 6
- Temperature Sensor (TSN)

■ Timers

- General PWM Timer 32-bit Enhanced High Resolution (GPT32EH) × 4
- General PWM Timer 32-bit Enhanced (GPT32E) × 4
- General PWM Timer 32-bit (GPT32) × 6
- Asynchronous General-Purpose Timer (AGT) × 2
- Watchdog Timer (WDT)

■ Safety

- Error Correction Code (ECC) in SRAM
- SRAM parity error check
- Flash area protection
- ADC self-diagnosis function
- Clock Frequency Accuracy Measurement Circuit (CAC)
- Cyclic Redundancy Check (CRC) calculator
- Data Operation Circuit (DOC)
- Port Output Enable for GPT (POEG)
- Independent Watchdog Timer (IWDT)
- GPIO readback level detection
- Register write protection
- Main oscillator stop detection
- Illegal memory access

■ System and Power Management

- Low power modes
- Realtime Clock (RTC) with calendar and VBATT support
- Event Link Controller (ELC)
- DMA Controller (DMAC) × 8
- Data Transfer Controller (DTC)
- Key Interrupt Function (KINT)
- Power-on reset
- Low Voltage Detection (LVD) with voltage settings

■ Security and Encryption

- AES128/192/256
- 3DES/ARC4
- SHA1/SHA224/SHA256/MD5
- GHASH
- RSA/DSA/ECC
- True Random Number Generator (TRNG)

■ Human Machine Interface (HMI)

- Graphics LCD Controller (GLCDC)
- JPEG codec
- 2D Drawing Engine (DRW)
- Capacitive Touch Sensing Unit (CTSU)
- Parallel Data Capture Unit (PDC)

■ Multiple Clock Sources

- Main clock oscillator (MOSC) (8 to 24 MHz)
- Sub-clock oscillator (SOSC) (32.768 kHz)
- High-speed on-chip oscillator (HOCO) (16/18/20 MHz)
- Middle-speed on-chip oscillator (MOCO) (8 MHz)
- Low-speed on-chip oscillator (LOCO) (32.768 kHz)
- IWDT-dedicated on-chip oscillator (15 kHz)
- Clock trim function for HOCO/MOCO/LOCO
- Clock out support

■ General-Purpose I/O Ports

- Up to 133 input/output pins
 - Up to 9 CMOS input
 - Up to 124 CMOS input/output
 - Up to 21 input/output 5 V tolerant
 - Up to 18 high current (20 mA)

■ Operating Voltage

- VCC: 2.7 to 3.6 V

■ Operating Temperature and Packages

- Ta = -40°C to +85°C
 - 176-pin BGA (13 mm × 13 mm, 0.8 mm pitch)
 - 145-pin LGA (7 mm × 7 mm, 0.5 mm pitch)
- Ta = -40°C to +105°C
 - 176-pin LQFP (24 mm × 24 mm, 0.5 mm pitch)
 - 144-pin LQFP (20 mm × 20 mm, 0.5 mm pitch)
 - 100-pin LQFP (14 mm × 14 mm, 0.5 mm pitch)

1. Overview

The MCU integrates multiple series of software- and pin-compatible Arm®-based 32-bit cores that share the same set of Renesas peripherals to facilitate design scalability and efficient platform-based product development.

The MCU in this series incorporates a high-performance Arm Cortex®-M4 core running up to 120 MHz, with the following features:

- Up to 2-MB code flash memory
- 640-KB SRAM
- Graphics LCD Controller (GLCDC)
- 2D Drawing Engine (DRW)
- Capacitive Touch Sensing Unit (CTSU)
- Ethernet MAC Controller (ETHERC) with IEEE 1588 PTP, USBFS, USBHS, SD/MMC Host Interface
- Quad Serial Peripheral Interface (QSPI)
- Security and safety features
- Analog peripherals.

1.1 Function Outline

Table 1.1 Arm core

Feature	Functional description
Arm Cortex-M4 core	<ul style="list-style-type: none"> • Maximum operating frequency: up to 120 MHz • Arm Cortex-M4 core: <ul style="list-style-type: none"> - Revision: r0p1-01rel0 - ARMv7E-M architecture profile - Single precision floating-point unit compliant with the ANSI/IEEE Std 754-2008. • Arm Memory Protection Unit (Arm MPU): <ul style="list-style-type: none"> - ARMv7 Protected Memory System Architecture - 8 protect regions. • SysTick timer: <ul style="list-style-type: none"> - Driven by SYSTICKCLK (LOCO) or ICLK.

Table 1.2 Memory

Feature	Functional description
Code flash memory	Maximum 2 MB of code flash memory. See section 55, Flash Memory in User's Manual.
Data flash memory	64 KB of data flash memory. See section 55, Flash Memory in User's Manual.
Memory Mirror Function (MMF)	The Memory Mirror Function (MMF) can be configured to mirror the target application image load address in code flash memory to the application image link address in the 23-bit unused memory space (memory mirror space addresses). Your application code is developed and linked to run from this MMF destination address. The application code does not need to know the load location where it is stored in code flash memory. See section 5, Memory Mirror Function (MMF) in User's Manual.
Option-setting memory	The option-setting memory determines the state of the MCU after a reset. See section 7, Option-Setting Memory in User's Manual.
SRAM	On-chip high-speed SRAM with either parity-bit or Error Correction Code (ECC). The first 32 KB in SRAM0 provides error correction capability using ECC. Parity check is performed for other areas. See section 53, SRAM in User's Manual.
Standby SRAM	On-chip SRAM that can retain data in Deep Software Standby mode. See section 54, Standby SRAM in User's Manual.

Table 1.3 System (1 of 2)

Feature	Functional description
Operating modes	<p>Two operating modes:</p> <ul style="list-style-type: none"> - Single-chip mode - SCI or USB boot mode. <p>See section 3, Operating Modes in User's Manual.</p>
Resets	<p>14 resets:</p> <ul style="list-style-type: none"> • RES pin reset • Power-on reset • Voltage monitor 0 reset • Voltage monitor 1 reset • Voltage monitor 2 reset • Independent watchdog timer reset • Watchdog timer reset • Deep software standby reset • SRAM parity error reset • SRAM ECC error reset • Bus master MPU error reset • Bus slave MPU error reset • Stack pointer error reset • Software reset. <p>See section 6, Resets in User's Manual.</p>
Low Voltage Detection (LVD)	The Low Voltage Detection (LVD) function monitors the voltage level input to the VCC pin, and the detection level can be selected using a software program. See section 8, Low Voltage Detection (LVD) in User's Manual.
Clocks	<ul style="list-style-type: none"> • Main clock oscillator (MOSC) • Sub-clock oscillator (SOSC) • High-speed on-chip oscillator (HOCO) • Middle-speed on-chip oscillator (MOCO) • Low-speed on-chip oscillator (LOCO) • PLL frequency synthesizer • IWDAT-dedicated on-chip oscillator • Clock out support. <p>See section 9, Clock Generation Circuit in User's Manual.</p>
Clock Frequency Accuracy Measurement Circuit (CAC)	<p>The Clock Frequency Accuracy Measurement Circuit (CAC) counts pulses of the clock to be measured (measurement target clock) within the time generated by the clock to be used as a measurement reference (measurement reference clock), and determines the accuracy depending on whether the number of pulses is within the allowable range.</p> <p>When measurement is complete or the number of pulses within the time generated by the measurement reference clock is not within the allowable range, an interrupt request is generated.</p> <p>See section 10, Clock Frequency Accuracy Measurement Circuit (CAC) in User's Manual.</p>
Interrupt Controller Unit (ICU)	The Interrupt Controller Unit (ICU) controls which event signals are linked to the NVIC/DTC module and DMAC module. The ICU also controls NMI interrupts. See section 14, Interrupt Controller Unit (ICU).
Key Interrupt Function (KINT)	A key interrupt can be generated by setting the Key Return Mode Register (KRM) and inputting a rising or falling edge to the key interrupt input pins. See section 21, Key Interrupt Function (KINT) in User's Manual.
Low power modes	Power consumption can be reduced in multiple ways, such as by setting clock dividers, controlling EBCLK output, controlling SDCLK output, stopping modules, selecting power control mode in normal operation, and transitioning to low power modes. See section 11, Low-Power Modes in User's Manual.
Battery backup function	A battery backup function is provided for partial powering by a battery. The battery-powered area includes the RTC, SOSC, backup memory, and switch between VCC and VBATT. See section 12, Battery Backup Function in User's Manual.
Register write protection	The register write protection function protects important registers from being overwritten because of software errors. See section 13, Register Write Protection in User's Manual.
Memory Protection Unit (MPU)	Four Memory Protection Units (MPUs) and a CPU stack pointer monitor function are provided for memory protection. See section 16, Memory Protection Unit (MPU) in User's Manual.

Table 1.3 System (2 of 2)

Feature	Functional description
Watchdog Timer (WDT)	The Watchdog Timer (WDT) is a 14-bit down-counter that can be used to reset the MCU when the counter underflows because the system has run out of control and is unable to refresh the WDT. In addition, a non-maskable interrupt or interrupt can be generated by an underflow. A refresh-permitted period can be set to refresh the counter and be used as the condition for detecting when the system runs out of control. See section 27, Watchdog Timer (WDT) in User's Manual.
Independent Watchdog Timer (IWDT)	The Independent Watchdog Timer (IWDT) consists of a 14-bit down-counter that must be serviced periodically to prevent counter underflow. It can be used to reset the MCU or to generate a non-maskable interrupt or interrupt for a timer underflow. Because the timer operates with an independent, dedicated clock source, it is particularly useful in returning the MCU to a known state as a fail safe mechanism when the system runs out of control. The IWDT can be triggered automatically on a reset, underflow, refresh error, or by a refresh of the count value in the registers. See section 28, Independent Watchdog Timer (IWDT) in User's Manual.

Table 1.4 Event link

Feature	Functional description
Event Link Controller (ELC)	The Event Link Controller (ELC) uses the interrupt requests generated by various peripheral modules as event signals to connect them to different modules, enabling direct interaction between the modules without CPU intervention. See section 19, Event Link Controller (ELC) in User's Manual.

Table 1.5 Direct memory access

Feature	Functional description
Data Transfer Controller (DTC)	A Data Transfer Controller (DTC) module is provided for transferring data when activated by an interrupt request. See section 18, Data Transfer Controller (DTC) in User's Manual.
DMA Controller (DMAC)	An 8-channel DMA Controller (DMAC) module is provided for transferring data without the CPU. When a DMA transfer request is generated, the DMAC transfers data stored at the transfer source address to the transfer destination address. See section 17, DMA Controller (DMAC) in User's Manual.

Table 1.6 External bus interface

Feature	Functional description
External buses	<ul style="list-style-type: none"> • CS area (EXBIU): Connected to the external devices (external memory interface) • SDRAM area (EXBIU): Connected to the SDRAM (external memory interface) • QSPI area (EXBIUT2): Connected to the QSPI (external device interface).

Table 1.7 Timers (1 of 2)

Feature	Functional description
General PWM Timer (GPT)	The General PWM Timer (GPT) is a 32-bit timer with 14 channels. PWM waveforms can be generated by controlling the up-counter, down-counter, or the up- and down-counter. In addition, PWM waveforms can be generated for controlling brushless DC motors. The GPT can also be used as a general-purpose timer. See section 23, General PWM Timer (GPT) in User's Manual.
Port Output Enable for GPT (POEG)	Use the Port Output Enable for GPT (POEG) function to place the General PWM Timer (GPT) output pins in the output disable state. See section 22, Port Output Enable for GPT (POEG) in User's Manual.
Asynchronous General-Purpose Timer (AGT)	The Asynchronous General-Purpose Timer (AGT) is a 16-bit timer that can be used for pulse output, external pulse width or period measurement, and counting of external events. This 16-bit timer consists of a reload register and a down-counter. The reload register and the down-counter are allocated to the same address, and can be accessed with the AGT register. See section 25, Asynchronous General-Purpose Timer (AGT) in User's Manual.

Table 1.7 Timers (2 of 2)

Feature	Functional description
Realtime Clock (RTC)	The Realtime Clock (RTC) has two counting modes, calendar count mode and binary count mode, that are controlled by the register settings. For calendar count mode, the RTC has a 100-year calendar from 2000 to 2099 and automatically adjusts dates for leap years. For binary count mode, the RTC counts seconds and retains the information as a serial value. Binary count mode can be used for calendars other than the Gregorian (Western) calendar. See section 26, Realtime Clock (RTC) in User's Manual.

Table 1.8 Communication interfaces (1 of 2)

Feature	Functional description
Serial Communications Interface (SCI)	The Serial Communications Interface (SCI) is configurable to five asynchronous and synchronous serial interfaces: <ul style="list-style-type: none">• Asynchronous interfaces (UART and Asynchronous Communications Interface Adapter (ACIA))• 8-bit clock synchronous interface• Simple IIC (master-only)• Simple SPI• Smart card interface. The smart card interface complies with the ISO/IEC 7816-3 standard for electronic signals and transmission protocol. Each SCI has FIFO buffers to enable continuous and full-duplex communication, and the data transfer speed can be configured independently using an on-chip baud rate generator. See section 34, Serial Communications Interface (SCI) in User's Manual.
IrDA interface	The IrDA interface sends and receives IrDA data communication waveforms in cooperation with the SCI1 based on the IrDA (Infrared Data Association) standard 1.0. See section 35, IrDA Interface in User's Manual.
I ² C bus interface (IIC)	The 3-channel I ² C bus interface (IIC) conforms with and provides a subset of the NXP I ² C (Inter-Integrated Circuit) bus interface functions. See section 36, I ² C Bus Interface (IIC) in User's Manual.
Serial Peripheral Interface (SPI)	Two independent Serial Peripheral Interface (SPI) channels are capable of high-speed, full-duplex synchronous serial communications with multiple processors and peripheral devices. See section 38, Serial Peripheral Interface (SPI) in User's Manual.
Serial Sound Interface Enhanced (SSIE)	The Serial Sound Interface Enhanced (SSIE) peripheral provides functionality to interface with digital audio devices for transmitting I ² S 2ch, 4ch, 6ch, 8ch, WS Continue/Monaural/TDM audio data over a serial bus. The SSIE supports an audio clock frequency of up to 50 MHz, and can be operated as a slave or master receiver, transmitter, or transceiver to suit various applications. The SSIE includes 32-stage FIFO buffers in the receiver and transmitter, and supports interrupts and DMA-driven data reception and transmission. See section 41, Serial Sound Interface Enhanced (SSIE) in User's Manual.
Quad Serial Peripheral Interface (QSPI)	The Quad Serial Peripheral Interface (QSPI) is a memory controller for connecting a serial ROM (nonvolatile memory such as a serial flash memory, serial EEPROM, or serial FeRAM) that has an SPI-compatible interface. See section 39, Quad Serial Peripheral Interface (QSPI) in User's Manual.
Controller Area Network (CAN) module	The Controller Area Network (CAN) module provides functionality to receive and transmit data using a message-based protocol between multiple slaves and masters in electromagnetically-noisy applications. The CAN module complies with the ISO 11898-1 (CAN 2.0A/CAN 2.0B) standard and supports up to 32 mailboxes, which can be configured for transmission or reception in normal mailbox and FIFO modes. Both standard (11-bit) and extended (29-bit) messaging formats are supported. See section 37, Controller Area Network (CAN) Module in User's Manual.
USB 2.0 Full-Speed (USBFS) module	The USB 2.0 Full-Speed (USBFS) module can operate as a host controller or device controller. The module supports full-speed and low-speed (host controller only) transfer as defined in Universal Serial Bus Specification 2.0. The module has an internal USB transceiver and supports all of the transfer types defined in the Universal Serial Bus Specification 2.0. The USB has buffer memory for data transfer, providing a maximum of 10 pipes. Pipes 1 to 9 can be assigned any endpoint number based on the peripheral devices used for communication or based on your system. See section 32, USB 2.0 Full-Speed Module (USBFS) in User's Manual.

Table 1.8 Communication interfaces (2 of 2)

Feature	Functional description
USB 2.0 High-Speed (USBHS) module	The USB 2.0 High-Speed (USBHS) module can operate as a host controller or a device controller. As a host controller, the USBHS supports high-speed transfer, full-speed transfer, and low-speed transfer as defined in the Universal Serial Bus Specification 2.0. As a device controller, the USBHS supports high-speed transfer and full-speed transfer as defined in the Universal Serial Bus Specification 2.0. The USBHS has an internal USB transceiver and supports all of the transfer types defined in the Universal Serial Bus Specification 2.0. The USBHS has FIFO buffers for data transfer, providing a maximum of 10 pipes. Any endpoint number can be assigned to pipes 1 to 9, based on the peripheral devices or your system for communication. See section 33, USB 2.0 High-Speed Module (USBHS) in User's Manual.
Ethernet MAC with IEEE 1588 PTP (ETHERC)	One-channel Ethernet MAC Controller (ETHERC) compliant with the Ethernet/IEEE802.3 Media Access Control (MAC) layer protocol. An ETHERC channel provides one channel of the MAC layer interface, connecting the MCU to the physical layer LSI (PHY-LSI) that allows transmission and reception of frames compliant with the Ethernet and IEEE802.3 standards. The ETHERC is connected to the Ethernet DMA Controller (EDMAC) so data can be transferred without using the CPU. To handle timing and synchronization between devices, an on-chip Precision Time Protocol (PTP) module for the Ethernet PTP Controller (EPTPC) applies the PTP defined in the IEEE 1588-2008 version 2.0 standard. The EPTPC is composed of: <ul style="list-style-type: none">• Synchronization Frame Processing unit (SYNFP0)• A Statistical Time Correction Algorithm unit (STCA). Use the EPTPC in combination with the on-chip Ethernet MAC Controller (ETHERC) and the DMA Controller for the PTP Ethernet Controller (PTPEDMAC). See section 29, Ethernet MAC Controller (ETHERC) in User's Manual.
SD/MMC Host Interface (SDHI)	The SDHI and MultiMediaCard (MMC) interface module provides the functionality required to connect a variety of external memory cards to the MCU. The SDHI supports both 1-bit and 4-bit buses for connecting memory cards that support SD, SDHC, and SDXC formats. When developing host devices that are compliant with the SD Specifications, you must comply with the SD Host/Ancillary Product License Agreement (SD HALA). The MMC interface supports 1-bit, 4-bit, and 8-bit MMC buses that provide eMMC 4.51 (JEDEC Standard JESD 84-B451) device access. This interface also provides backward compatibility and supports high-speed SDR transfer modes. See section 43, SD/MMC Host Interface (SDHI) in User's Manual.

Table 1.9 Analog

Feature	Functional description
12-bit A/D Converter (ADC12)	Up to two successive approximation 12-bit A/D Converters (ADC12) are provided. In unit 0, up to 13 analog input channels are selectable. In unit 1, up to 11 analog input channels, the temperature sensor output, and an internal reference voltage are selectable for conversion. The A/D conversion accuracy is selectable from 12-bit, 10-bit, and 8-bit conversion, making it possible to optimize the tradeoff between speed and resolution in generating a digital value. See section 47, 12-Bit A/D Converter (ADC12) in User's Manual.
12-bit D/A Converter (DAC12)	The 12-bit D/A Converter (DAC12) converts data and includes an output amplifier. See section 48, 12-Bit D/A Converter (DAC12) in User's Manual.
Temperature Sensor (TSN)	The on-chip Temperature Sensor (TSN) determines and monitors the die temperature for reliable operation of the device. The sensor outputs a voltage directly proportional to the die temperature, and the relationship between the die temperature and the output voltage is linear. The output voltage is provided to the ADC12 for conversion and can also be used by the end application. See section 49, Temperature Sensor (TSN) in User's Manual.
High-Speed Analog Comparator (ACMPHS)	The High-Speed Analog Comparator (ACMPHS) compares a test voltage with a reference voltage and provides a digital output based on the conversion result. Both the test and reference voltages can be provided to the comparator from internal sources such as the DAC12 output and internal reference voltage, and an external source with or without an internal PGA. Such flexibility is useful in applications that require go/no-go comparisons to be performed between analog signals without necessarily requiring A/D conversion. See section 50, High-Speed Analog Comparator (ACMPHS) in User's Manual.

Table 1.10 Human machine interfaces

Feature	Functional description
Capacitive Touch Sensing Unit (CTSU)	The Capacitive Touch Sensing Unit (CTSU) measures the electrostatic capacitance of the touch sensor. Changes in the electrostatic capacitance are determined by software, which enables the CTSU to detect whether a finger is in contact with the touch sensor. The electrode surface of the touch sensor is usually enclosed with an electrical insulator so that fingers do not come into direct contact with the electrodes. See section 51, Capacitive Touch Sensing Unit (CTSU) in User's Manual.

Table 1.11 Graphics

Feature	Functional description
Graphics LCD Controller (GLCDC)	The Graphics LCD Controller (GLCDC) provides multiple functions and supports various data formats and panels. Key GLCDC features include: <ul style="list-style-type: none"> GPX bus master function for accessing graphics data Superimposition of three planes (single-color background plane, graphic 1-plane, and graphic 2-plane) Support for many types of 32-bit or 16-bit per pixel graphics data and 8-bit, 4-bit, or 1-bit LUT data format Digital interface signal output supporting a video image size of WVGA or greater. See section 58, Graphics LCD Controller (GLCDC) in User's Manual.
2D Drawing Engine (DRW)	The 2D Drawing Engine (DRW) provides flexible functions that can support almost any object geometry rather than being bound to only a few specific geometries such as lines, triangles, or circles. The edges of every object can be independently blurred or antialiased. Rasterization is executed at one pixel per clock on the bounding box of the object from left to right and top to bottom. The DRW can also raster from bottom to top to optimize the performance in certain cases. In addition, optimization methods are available to avoid rasterization of many empty pixels of the bounding box. The distances to the edges of the object are calculated by a set of edge equations for every pixel of the bounding box. These edge equations can be combined to describe the entire object. If a pixel is inside the object, it is selected for rendering. If it is outside, it is discarded. If it is on the edge, an alpha value can be chosen proportional to the distance of the pixel to the nearest edge for antialiasing. Every pixel that is selected for rendering can be textured. The resulting aRGB quadruple can be modified by a general raster operation approach independently for each of the four channels. The aRGB quadruples can then be blended with one of the multiple blend modes of the DRW. The DRW provides two inputs (texture read and framebuffer read), and one output (framebuffer write). The internal color format is always aRGB (8888). The color formats from the inputs are converted to the internal format on read and a conversion back is made on write. See section 56, 2D Drawing Engine (DRW) in User's Manual.
JPEG codec	The JPEG incorporates a JPEG codec that conforms to the JPEG baseline compression and decompression standard. This provides high-speed compression of image data and high-speed decoding of JPEG data. See section 57, JPEG Codec (JPEG) in User's Manual.
Parallel Data Capture (PDC) unit	One Parallel Data Capture (PDC) unit is provided for communicating with external I/O devices, including image sensors, and transferring parallel data, such as an image output from the external I/O device through the DTC or DMAC to the on-chip SRAM and external address spaces (the CS and SDRAM areas). See section 44, Parallel Data Capture Unit (PDC) in User's Manual.

Table 1.12 Data processing (1 of 2)

Feature	Functional description
Cyclic Redundancy Check (CRC) calculator	The Cyclic Redundancy Check (CRC) calculator generates CRC codes to detect errors in the data. The bit order of CRC calculation results can be switched for LSB-first or MSB-first communication. Additionally, various CRC-generating polynomials are available. The snoop function allows monitoring reads from and writes to specific addresses. This function is useful in applications that require CRC code to be generated automatically in certain events, such as monitoring writes to the serial transmit buffer and reads from the serial receive buffer. See section 40, Cyclic Redundancy Check (CRC) Calculator in User's Manual.

Table 1.12 Data processing (2 of 2)

Feature	Functional description
Data Operation Circuit (DOC)	The Data Operation Circuit (DOC) compares, adds, and subtracts 16-bit data. See section 52, Data Operation Circuit (DOC) in User's Manual.
Sampling Rate Converter (SRC)	The Sampling Rate Converter (SRC) converts the sampling rate of data produced by various audio decoders, such as the WMA, MP3, and AAC. Both 16-bit stereo and monaural data are supported. See section 42, Sampling Rate Converter (SRC) in User's Manual.

Table 1.13 Security

Feature	Functional description
Secure Crypto Engine 7 (SCE7)	<ul style="list-style-type: none"> • Security algorithms: <ul style="list-style-type: none"> - Symmetric algorithms: AES, 3DES, and ARC4 - Asymmetric algorithms: RSA, DSA, and ECC. • Other support features: <ul style="list-style-type: none"> - TRNG (True Random Number Generator) - Hash-value generation: SHA1, SHA224, SHA256, GHASH, and MD5 - 128-bit unique ID. <p>See section 46, Secure Cryptographic Engine (SCE7) in User's Manual.</p>

1.2 Block Diagram

Figure 1.1 shows a block diagram of the MCU superset, some individual devices within the group have a subset of the features.

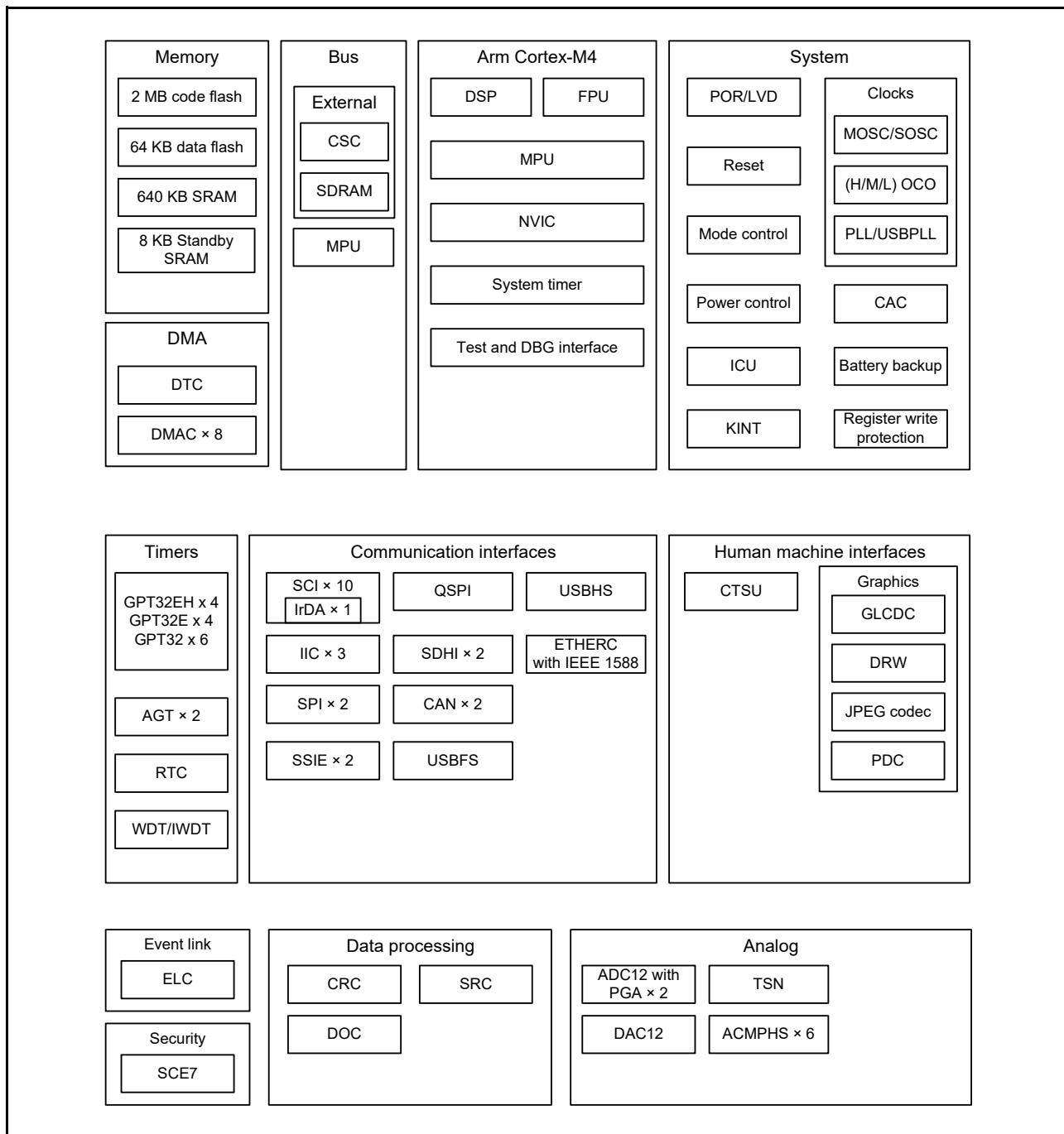


Figure 1.1 Block diagram

1.3 Part Numbering

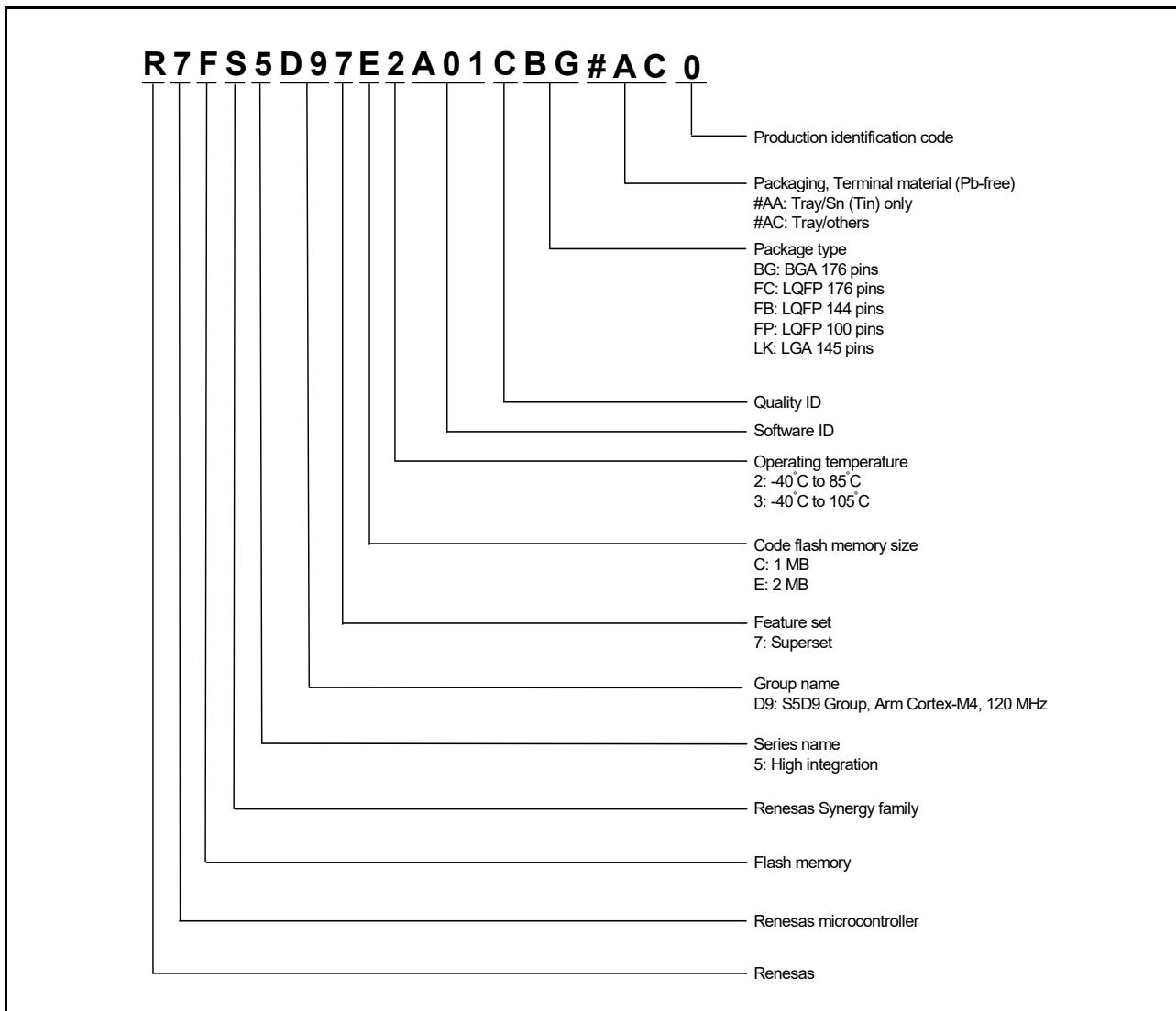


Figure 1.2 Part numbering scheme

Table 1.14 Product list

Product part number	Orderable part number	Package code	Code flash	Data flash	SRAM	Operating temperature
R7FS5D97E2A01CBG	R7FS5D97E2A01CBG#AC0	PLBG0176GE-A	2 MB	64 KB	640 KB	-40 to +85°C
R7FS5D97E3A01CFC	R7FS5D97E3A01CFC#AA0	PLQP0176KB-A				-40 to +105°C
R7FS5D97E2A01CLK	R7FS5D97E2A01CLK#AC0	PTLG0145KA-A				-40 to +85°C
R7FS5D97E3A01CFB	R7FS5D97E3A01CFB#AA0	PLQP0144KA-B				-40 to +105°C
R7FS5D97E3A01CFP	R7FS5D97E3A01CFP#AA0	PLQP0100KB-B				-40 to +105°C
R7FS5D97C2A01CBG	R7FS5D97C2A01CBG#AC0	PLBG0176GE-A	1 MB			-40 to +85°C
R7FS5D97C3A01CFC	R7FS5D97C3A01CFC#AA0	PLQP0176KB-A				-40 to +105°C
R7FS5D97C2A01CLK	R7FS5D97C2A01CLK#AC0	PTLG0145KA-A				-40 to +85°C
R7FS5D97C3A01CFB	R7FS5D97C3A01CFB#AA0	PLQP0144KA-B				-40 to +105°C
R7FS5D97C3A01CFP	R7FS5D97C3A01CFP#AA0	PLQP0100KB-B				-40 to +105°C

1.4 Function Comparison

Table 1.15 Functional comparison (Graphics)

		Part numbers						
Function		R7FS5D97E2XXXCBG/ R7FS5D97C2XXXCBG	R7FS5D97E3XXXCFC/ R7FS5D97C3XXXCFC	R7FS5D97E2XXXCLK/ R7FS5D97C2XXXCLK	R7FS5D97E3XXXCFB/ R7FS5D97C3XXXCFB	R7FS5D97E3XXCFP/ R7FS5D97C3XXCFP		
Pin count		176	176	145	144	100		
Package		BGA	LQFP	LGA	LQFP	LQFP		
Code flash memory		2/1 MB						
Data flash memory		64 KB						
SRAM		640 KB						
Standby SRAM	Parity	608 KB						
	ECC	32 KB						
Standby SRAM		8 KB						
System	CPU clock	120 MHz						
	Backup registers	512 B						
	ICU	Yes						
	KINT	8						
Event link	ELC	Yes						
DMA	DTC	Yes						
	DMAC	8						
BUS	External bus	16-bit bus				8-bit bus		
	SDRAM	Yes				No		
Timers	GPT32EH	4	4	4	4	4		
	GPT32E	4	4	4	4	4		
	GPT32	6	6	6	6	5		
	AGT	2	2	2	2	2		
	RTC	Yes						
	WDT/IWDT	Yes						
Communication	SCI	10						
	IIC	3				2		
	SPI	2						
	SSIE	2				1		
	QSPI	1						
	SDHI	2						
	CAN	2						
	USBFS	Yes						
	USBHS	Yes		No				
Analog	ETHERC	1						
	ADC12	24		22		19		
	DAC12	2						
	ACMPHS	6						
HMI	TSN	Yes						
	CTSU	13		18		12		
Graphics	GLCDC	RGB888						
	DRW	Yes						
	JPEG	Yes						
	PDC	Yes						
Data processing	CRC	Yes						
	DOC	Yes						
	SRC	Yes						
Security		SCE7						

1.5 Pin Functions

Table 1.16 Pin functions (1 of 5)

Function	Signal	I/O	Description
Power supply	VCC	Input	Digital voltage supply pin. This is used as the digital power supply for the respective modules and internal voltage regulator, and used to monitor the voltage of the POR/LVD. Connect to the system power supply. Connect to VSS through a 0.1- μ F smoothing capacitor close to each VCC pin.
	VCL0	-	Connect to VSS through a 0.1- μ F smoothing capacitor close to each VCL pin. Stabilize the internal power supply.
	VCL	-	
	VSS	Input	Ground pin. Connect to the system power supply (0 V).
Clock	VBATT	Input	Backup power pin
	XTAL	Output	Pins for a crystal resonator. An external clock signal can be input through the EXTAL pin.
	EXTAL	Input	
	XCIN	Input	Input/output pins for the sub-clock oscillator. Connect a crystal resonator between XCOUT and XCIN.
	XCOUT	Output	
	EBCLK	Output	Outputs the external bus clock for external devices
	SDCLK	Output	Outputs the SDRAM-dedicated clock
Operating mode control	CLKOUT	Output	Clock output pin
	MD	Input	Pin for setting the operating mode. The signal level on this pin must not be changed during operation mode transition or release from the reset state.
System control	RES	Input	Reset signal input pin. The MCU enters the reset state when this signal goes low.
CAC	CACREF	Input	Measurement reference clock input pin
Interrupt	NMI	Input	Non-maskable interrupt request pin
	IRQ0 to IRQ15	Input	Maskable interrupt request pins
KINT	KR00 to KR07	Input	A key interrupt can be generated by inputting a falling edge to the key interrupt input pins
On-chip emulator	TMS	I/O	On-chip emulator or boundary scan pins
	TDI	Input	
	TCK	Input	
	TDO	Output	
	TCLK	Output	This pin outputs the clock for synchronization with the trace data
	TDATA0 to TDATA3	Output	Trace data output
	SWDIO	I/O	Serial wire debug data input/output pin
	SWCLK	Input	Serial wire clock pin
	SWO	Output	Serial wire trace output pin
External bus interface	RD	Output	Strobe signal indicating that reading from the external bus interface space is in progress, active low
	WR	Output	Strobe signal indicating that writing to the external bus interface space is in progress, in 1-write strobe mode, active low
	WR0 to WR1	Output	Strobe signals indicating that either group of data bus pins (D07 to D00 or D15 to D08) is valid in writing to the external bus interface space, in byte strobe mode, active low
	BC0 to BC1	Output	Strobe signals indicating that either group of data bus pins (D07 to D00 or D15 to D08) is valid in access to the external bus interface space, in 1-write strobe mode, active low
	ALE	Output	Address latch signal when address/data multiplexed bus is selected
	WAIT	Input	Input pin for wait request signals in access to the external space, active low
	CS0 to CS7	Output	Select signals for CS areas, active low
	A00 to A23	Output	Address bus
	D00 to D15	I/O	Data bus
	A00/D00 to A15/D15	I/O	Address/data multiplexed bus

Table 1.16 Pin functions (2 of 5)

Function	Signal	I/O	Description
SDRAM interface	CKE	Output	SDRAM clock enable signal
	SDCS	Output	SDRAM chip select signal, active low
	RAS	Output	SDRAM low address strobe signal, active low
	CAS	Output	SDRAM column address strobe signal, active low
	WE	Output	SDRAM write enable signal, active low
	DQM0	Output	SDRAM I/O data mask enable signal for DQ07 to DQ00
	DQM1	Output	SDRAM I/O data mask enable signal for DQ15 to DQ08
	A00 to A15	Output	Address bus
	DQ00 to DQ15	I/O	Data bus
GPT	GTETRGA, GTETRGB, GTETRGC, GTETRGD	Input	External trigger input pins
	GTIOC0A to GTIOC13A, GTIOC0B to GTIOC13B	I/O	Input capture, output compare, or PWM output pins
	GTIU	Input	Hall sensor input pin U
	GTIV	Input	Hall sensor input pin V
	GTIW	Input	Hall sensor input pin W
	GTOUUP	Output	3-phase PWM output for BLDC motor control (positive U phase)
	GTOULO	Output	3-phase PWM output for BLDC motor control (negative U phase)
	GTOVUP	Output	3-phase PWM output for BLDC motor control (positive V phase)
	GTOVLO	Output	3-phase PWM output for BLDC motor control (negative V phase)
	GTOWUP	Output	3-phase PWM output for BLDC motor control (positive W phase)
	GTOWLO	Output	3-phase PWM output for BLDC motor control (negative W phase)
	AGTEE0, AGTEE1	Input	External event input enable signals
AGT	AGTIO0, AGTIO1	I/O	External event input and pulse output pins
	AGTO0, AGTO1	Output	Pulse output pins
	AGTOA0, AGTOA1	Output	Output compare match A output pins
	AGTOB0, AGTOB1	Output	Output compare match B output pins
	RTCOUT	Output	Output pin for 1-Hz or 64-Hz clock
RTC	RTCIC0 to RTCIC2	Input	Time capture event input pins
	SCK0 to SCK9	I/O	Input/output pins for the clock (clock synchronous mode)
	RXD0 to RXD9	Input	Input pins for received data (asynchronous mode/clock synchronous mode)
	TXD0 to TXD9	Output	Output pins for transmitted data (asynchronous mode/clock synchronous mode)
	CTS0_RTS0 to CTS9_RTS9	I/O	Input/output pins for controlling the start of transmission and reception (asynchronous mode/clock synchronous mode), active low
	SCL0 to SCL9	I/O	Input/output pins for the I ² C clock (simple I ² C mode)
	SDA0 to SDA9	I/O	Input/output pins for the I ² C data (simple I ² C mode)
	SCK0 to SCK9	I/O	Input/output pins for the clock (simple SPI mode)
	MISO0 to MISO9	I/O	Input/output pins for slave transmission of data (simple SPI mode)
	MOSI0 to MOSI9	I/O	Input/output pins for master transmission of data (simple SPI mode)
IIC	SS0 to SS9	Input	Chip-select input pins (simple SPI mode), active low
	SCL0 to SCL2	I/O	Input/output pins for the clock
	SDA0 to SDA2	I/O	Input/output pins for data
SSIE	SSIBCK0	I/O	SSIE serial bit clock pins
	SSIBCK1		
	SSILRCK0/SSIFS0	I/O	LR clock/frame synchronization pins
	SSILRCK1/SSIFS1		
	SSITXD0	Output	Serial data output pins
	SSIRXD0	Input	Serial data input pins
	SSIDATA1	I/O	Serial data input/output pins
	AUDIO_CLK	Input	External clock pin for audio (input oversampling clock)

Table 1.16 Pin functions (3 of 5)

Function	Signal	I/O	Description
SPI	RSPCKA, RSPCKB	I/O	Clock input/output pin
	MOSIA, MOSIB	I/O	Input or output pins for data output from the master
	MISOA, MISOB	I/O	Input or output pins for data output from the slave
	SSLA0, SSLB0	I/O	Input or output pin for slave selection
	SSLA1 to SSLA3, SSLB1 to SSLB3	Output	Output pins for slave selection
QSPI	QSPCLK	Output	QSPI clock output pin
	QSSL	Output	QSPI slave output pin
	QIO0 to QIO3	I/O	Data0 to Data3
CAN	CRX0, CRX1	Input	Receive data
	CTX0, CTX1	Output	Transmit data
USBFS	VCC_USB	Input	Power supply pins
	VSS_USB	Input	Ground pins
	USB_DP	I/O	D+ I/O pin of the USB on-chip transceiver. Connect this pin to the D+ pin of the USB bus
	USB_DM	I/O	D- I/O pin of the USB on-chip transceiver. Connect this pin to the D- pin of the USB bus
	USB_VBUS	Input	USB cable connection monitor pin. Connect this pin to VBUS of the USB bus. The VBUS pin status (connected or disconnected) can be detected when the USB module is operating as a function controller.
	USB_EXICEN	Output	Low-power control signal for external power supply (OTG) chip
	USB_VBUSEN	Output	VBUS (5 V) supply enable signal for external power supply chip
	USB_OVRCURA, USB_OVRCURB	Input	Connect the external overcurrent detection signals to these pins. Connect the VBUS comparator signals to these pins when the OTG power supply chip is connected.
	USB_ID	Input	Connect the MicroAB connector ID input signal to this pin during operation in OTG mode
	VCC_USBHS	Input	Power supply pin
USBHS	VSS1_USBHS	Input	Ground pin
	VSS2_USBHS	Input	Ground pin
	AVCC_USBHS	Input	Analog power supply pin for the USBHS
	AVSS_USBHS	Input	Analog ground pin for the USBHS. Must be shorted to the PVSS_USBHS pin
	PVSS_USBHS	Input	PLL circuit ground pin for the USBHS. Must be shorted to the AVSS_USBHS pin
	USBHS_RREF	I/O	USBHS reference current source pin. Connect this pin to the AVSS_USBHS pin through a 2.2-kΩ resistor (±1%)
	USBHS_DP	I/O	USB bus D+ data pin
	USBHS_DM	I/O	USB bus D- data pin
	USBHS_EXICEN	Output	Connect this pin to the OTG power supply IC
	USBHS_ID	Input	Connect this pin to the OTG power supply IC
	USBHS_VBUSEN	Output	VBUS power enable signal for USB
	USBHS_OVRCURA, USBHS_OVRCURB	Input	Overcurrent pin for USB
	USBHS_VBUS	Input	USB cable connection monitor input pin

Table 1.16 Pin functions (4 of 5)

Function	Signal	I/O	Description
ETHERC	REF50CK0	Input	50-MHz reference clock. This pin inputs reference signal for transmission/reception timing in RMII mode.
	RMII0_CRS_DV	Input	Indicates carrier detection signals and valid receive data on RMII0_RXD1 and RMII0_RXD0 in RMII mode
	RMII0_TXD0, RMII0_TXD1	Output	2-bit transmit data in RMII mode
	RMII0_RXD0, RMII0_RXD1	Input	2-bit receive data in RMII mode
	RMII0_TXD_EN	Output	Output pin for data transmit enable signal in RMII mode
	RMII0_RX_ER	Input	Indicates an error occurred during reception of data in RMII mode
	ET0_CRS	Input	Carrier detection/data reception enable signal
	ET0_RX_DV	Input	Indicates valid receive data on ET0_ERXD3 to ET0_ERXD0
	ET0_EXOUT	Output	General-purpose external output pin
	ET0_LINKSTA	Input	Input link status from the PHY-LSI
	ET0_ETXD0 to ET0_ETXD3	Output	4 bits of MII transmit data
	ET0_ERXD0 to ET0_ERXD3	Input	4 bits of MII receive data
	ET0_TX_EN	Output	Transmit enable signal. Functions as signal indicating that transmit data is ready on ET0_ETXD3 to ET0_ETXD0
	ET0_TX_ER	Output	Transmit error pin. Functions as signal notifying the PHY_LSI of an error during transmission
	ET0_RX_ER	Input	Receive error pin. Functions as signal to recognize an error during reception
	ET0_TX_CLK	Input	Transmit clock pin. This pin inputs reference signal for output timing from ET0_TX_EN, ET0_ETXD3 to ET0_ETXD0, and ET0_TX_ER
	ET0_RX_CLK	Input	Receive clock pin. This pin inputs reference signal for input timing to ET0_RX_DV, ET0_ERXD3 to ET0_ERXD0, and ET0_RX_ER
	ET0_COL	Input	Input collision detection signal
	ET0_WOL	Output	Receive Magic packets
	ET0_MDC	Output	Output reference clock signal for information transfer through ET0_MDIO.
	ET0_MDIO	I/O	Input or output bidirectional signal for exchange of management data with PHY-LSI
SDHI	SD0CLK, SD1CLK	Output	SD clock output pins
	SD0CMD, SD1CMD	I/O	Command output pin and response input signal pins
	SD0DAT0 to SD0DAT7, SD1DAT0 to SD1DAT7	I/O	SD and MMC data bus pins
	SD0CD, SD1CD	Input	SD card detection pins
	SD0WP, SD1WP	Input	SD write-protect signals
Analog power supply	AVCC0	Input	Analog voltage supply pin. This is used as the analog power supply for the respective modules. Supply this pin with the same voltage as the VCC pin.
	AVSS0	Input	Analog ground pin. This is used as the analog ground for the respective modules. Supply this pin with the same voltage as the VSS pin.
	VREFH0	Input	Analog reference voltage supply pin for the ADC12 (unit 0). Connect this pin to VCC when not using the ADC12 (unit 0) and sample-and-hold circuit for AN000 to AN002.
	VREFL0	Input	Analog reference ground pin for the ADC12. Connect this pin to VSS when not using the ADC12 (unit 0) and sample-and-hold circuit for AN000 to AN002
	VREFH	Input	Analog reference voltage supply pin for the ADC12 (unit 1) and D/A Converter. Connect this pin to VCC when not using the ADC12 (unit 1), sample-and-hold circuit for AN100 to AN102, and D/A Converter.
	VREFL	Input	Analog reference ground pin for the ADC12 and D/A Converter. Connect this pin to VSS when not using the ADC12 (unit 1), sample-and-hold circuit for AN100 to AN102, and D/A Converter.

Table 1.16 Pin functions (5 of 5)

Function	Signal	I/O	Description
ADC12	AN000 to AN007, AN016 to AN020	Input	Input pins for the analog signals to be processed by the ADC12 Input pins for the external trigger signals that start the A/D conversion
	AN100 to AN103, AN105 to AN107, AN116 to AN119	Input	
	ADTRG0	Input	
	ADTRG1	Input	
	PGAVSS000/PGAVS S100	Input	Differential input pins
DAC12	DA0, DA1	Output	Output pins for the analog signals processed by the D/A converter
ACMPHS	VCOUP	Output	Comparator output pin
	IVREF0 to IVREF3	Input	Reference voltage input pins for comparator
	IVCMP0 to IVCMP2	Input	Analog voltage input pins for comparator
CTSU	TS00 to TS17	Input	Capacitive touch detection pins (touch pins)
	TSCAP	-	Secondary power supply pin for the touch driver
I/O ports	P000 to P007	Input	General-purpose input pins
	P008 to P010, P014, P015	I/O	General-purpose input/output pins
	P100 to P115	I/O	General-purpose input/output pins
	P200	Input	General-purpose input pin
	P201 to P214	I/O	General-purpose input/output pins
	P300 to P315	I/O	General-purpose input/output pins
	P400 to P415	I/O	General-purpose input/output pins
	P500 to P508, P511 to P513	I/O	General-purpose input/output pins
	P600 to P615	I/O	General-purpose input/output pins
	P700 to P713	I/O	General-purpose input/output pins
	P800 to P806	I/O	General-purpose input/output pins
	P900, P901, P905 to P908	I/O	General-purpose input/output pins
GLCDC	PA00, PA01, PA08 to PA10	I/O	General-purpose input/output pins
	PB00, PB01	I/O	General-purpose input/output pins
	LCD_DATA23 to LCD_DATA00	Output	Data output pins for panel
	LCD_TCON3 to LCD_TCON0	Output	Output pins for panel timing adjustment
PDC	LCD_CLK	Output	Panel clock output pin
	LCD_EXTCLK	Input	Panel clock source input pin
	PIXCLK	Input	Image transfer clock pin
	VSYNC	Input	Vertical synchronization signal pin
	Hsync	Input	Horizontal synchronization signal pin
PDC	PIXD0 to PIXD7	Input	8-bit image data pins
	PCKO	Output	Output pin for dot clock

1.6 Pin Assignments

[Figure 1.3](#) to [Figure 1.7](#) show the pin assignments.

R7FS5D9XX2XXXCBG																	
	A	B	C	D	E	F	G	H	J	K	L	M	N	P	R		
15	P407	P409	P411	P414	P708	USBHS_DM	PVSS_USBHS	P212_EXTAL	XCIN	VCL0	P707	P703	P700	P405	P401	15	
14	USB_DP	USB_DM	P410	P412	P415	USBHS_DP	AVSS_USBHS	P213_XTAL	XCOUT	VBATT	P706	P701	P406	P402	P512	14	
13	P204	VCC_USB	VSS_USB	P408	P413	VCC_USBHS	USBHS_RREF	AVCC_USBHS	VSS	PB01	P704	P404	P400	P511	P805	13	
12	P313	P202	P207	P206	P205	VSS1_USBHS	VSS2_USBHS	VCC	PB00	P705	P702	P403	P513	P806	P000	12	
11	P900	P315	P314	P203									VCC	P001	P004	P002	11
10	P214	P211	P901	VSS									VSS	P006	P008	P005	10
9	P210	P209	RES	VCC									P009	AVSS0	VREFL0	VREFH0	9
8	P208	P201/MD	P200	P908									P010	AVCC0	VREFL	VREFH	8
7	P906	P905	P312	P907									VCC	VSS	P015	P014	7
6	P310	P309	P307	P311									P007	P507	P505	P508	6
5	P308	P305	VSS	VCC									P003	P503	P504	P506	5
4	P306	P304	P300/TCK_SWCLK	P111	VSS	P613	PA09	PA00	P607	VCC	VSS	VSS	VCC	P501	P502	4	
3	P303	P302	P108/TMS_SWDIO	P110/TDI	VCC	P610	VCC	VSS	P604	P603	P105	P102	P800	P804	P500	3	
2	P301	P112	P114	P608	P611	P614	PA10	PA01	P605	P601	P107	P104	P101	P802	P803	2	
1	P109/TDO	P113	P115	P609	P612	P615	PA08	VCL	P606	P602	P600	P106	P103	P100	P801	1	
	A	B	C	D	E	F	G	H	J	K	L	M	N	P	R		

Figure 1.3 Pin assignment for 176-pin BGA (top view)

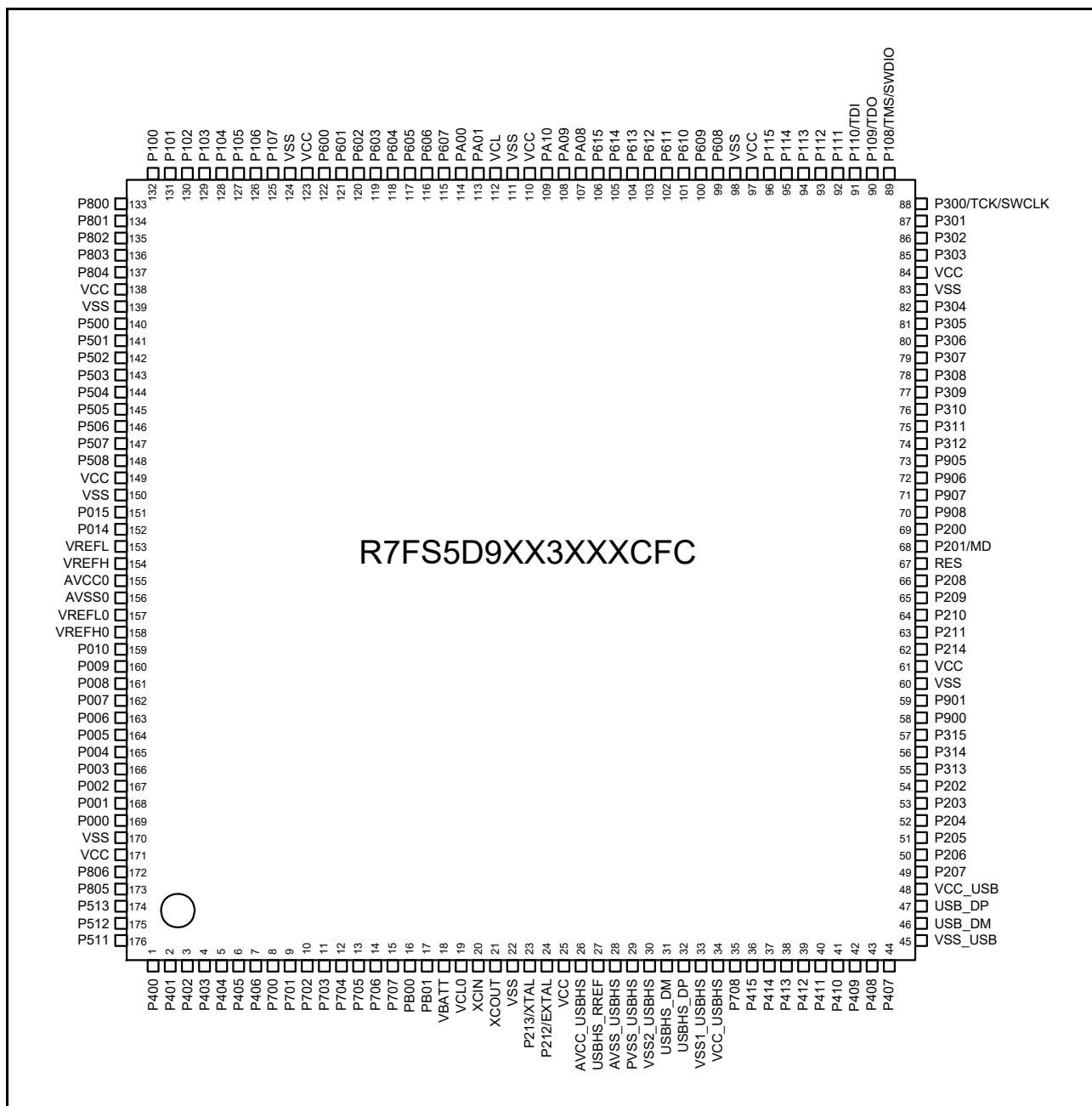


Figure 1.4 Pin assignment for 176-pin LQFP (top view)

R7FS5D9XX2XXXCLK

	A	B	C	D	E	F	G	H	J	K	L	M	N		
13	P407	P409	P412	P708	P711	VCC	P212 /EXTAL	XCIN	VCL0	P702	P405	P402	P400	13	
12	USB_DM	USB_DP	P410	P414	P710	VSS	P213 /XTAL	XCOUT	VBATT	P701	P404	P511	VCC	12	
11	VCC_USB	VSS_USB	P207	P411	P415	P712	P705	P704	P703	P403	P401	P512	VSS	11	
10	P205	P206	P204	P408	P413	P709	P713	P700	P406	P003	P000	P002	P001	10	
9	P203	P313	P202	VSS							P004	P006	P009	P008	9
8	P214	P211	P200	VCC							P005	AVSS0	VREFL0	VREFH0	8
7	P210	P209	RES	P310							P007	AVCC0	VREFL	VREFH	7
6	P208	P201/MD	P312	P305							P505	P506	P015	P014	6
5	P309	P311	P308	P303	NC	P503	P504	VSS	VCC	5					
4	P307	P306	P304	P109/TDO	P114	P608	P604	P600	P105	P500	P502	P501	P508	4	
3	VSS	VCC	P301	P112	P115	P610	P614	P603	P107	P106	P104	VSS	VCC	3	
2	P302	P300/TCK/SWCLK	P111	VCC	P609	P612	VSS	P605	P601	VCC	P800	P101	P801	2	
1	P108/TMS/SWDIO	P110/TDI	P113	VSS	P611	P613	VCC	VCL	P602	VSS	P103	P102	P100	1	

Figure 1.5 Pin assignment for 145-pin LGA (top view)

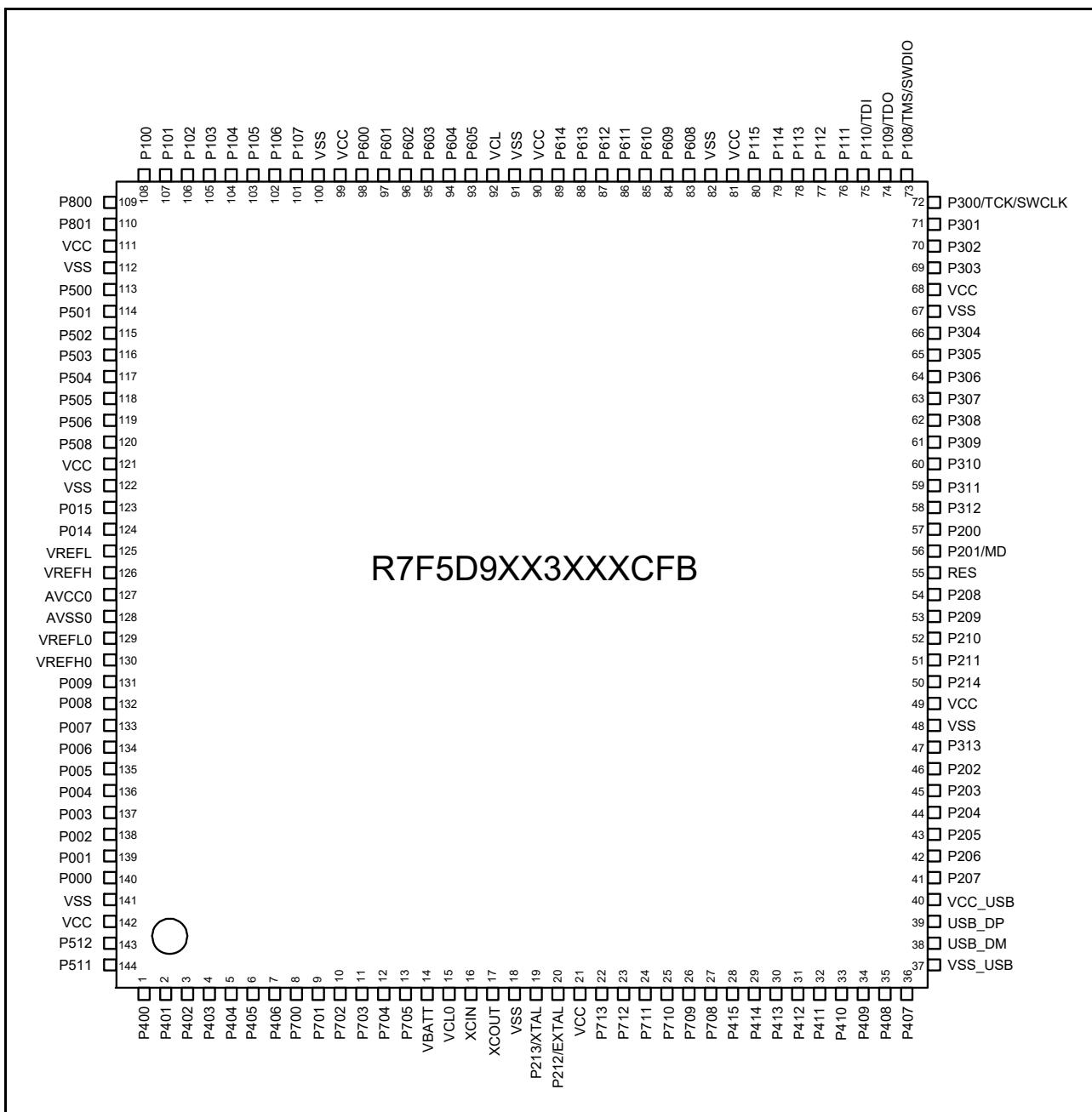


Figure 1.6 Pin assignment for 144-pin LQFP (top view)

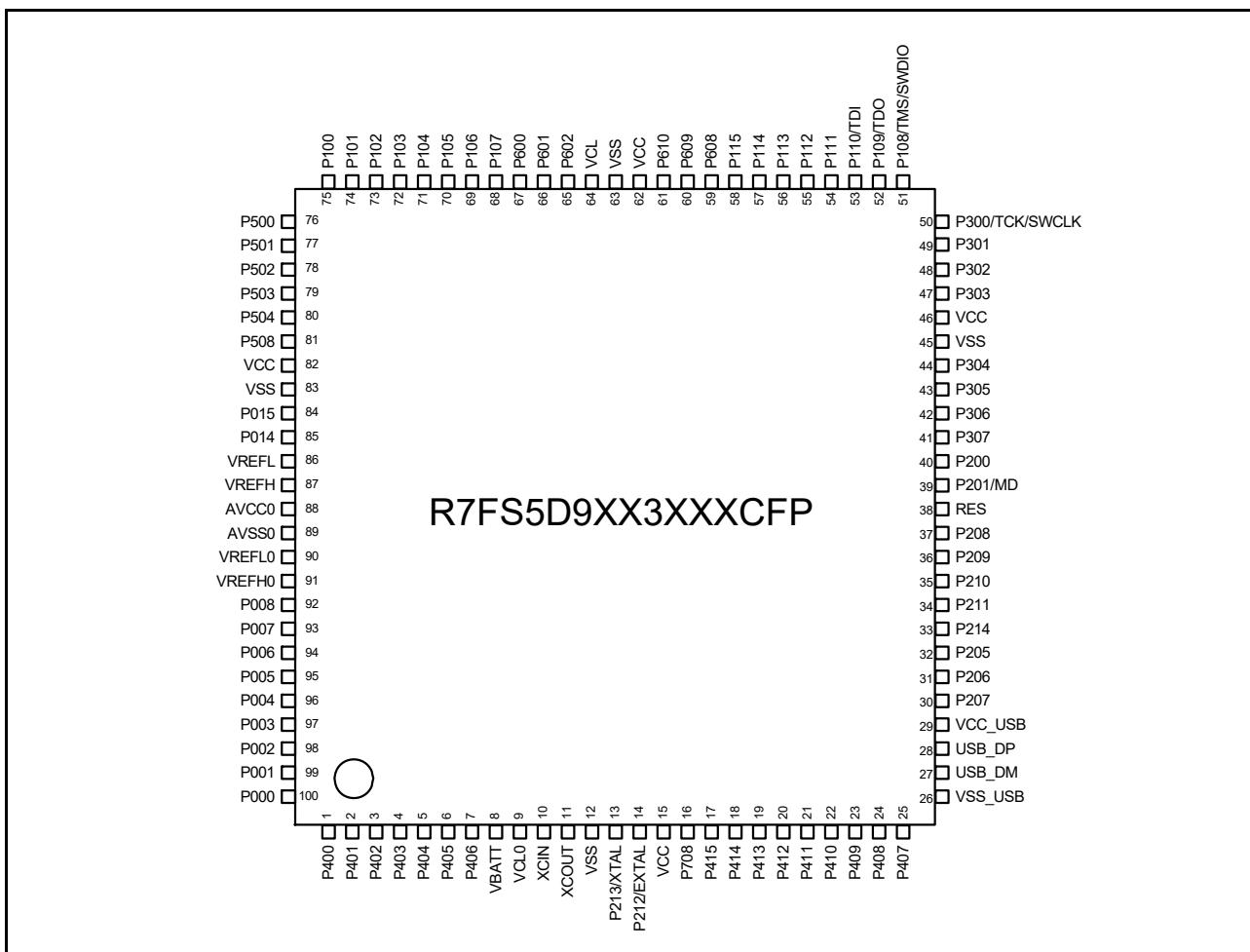


Figure 1.7 Pin assignment for 100-pin LQFP (top view)

Pin number				Extbus		Timers		Communication interfaces						Analog		HMI									
	BGA176	LQFP176	LGA145	LQFP144	LQFP100	Power, System, Clock, Debug, CAC	Interrupt	I/O port	External bus	SDRAM	AGT	GPT	RTC	USFS, CAN	SCI0,2,4,6,8 (30 MHz)	SCI1,3,5,7,9 (30 MHz)	IIC	SPI, QSPI	SSIE	ETHERC (MII) (25 MHz)	ETHERC (RMII) (50 MHz)	USBHS	SDHI	ADC12, DAC12, ACMPHS	CTSU
R5 146	146	L6	119	-	-	IRQ15	P506	-	-	-	-	-	-	TXD6/MOSI6/SDA6	-	-	-	-	SD1_CD_A	AN019	-	-	-	-	
N6 147	-	-	-	-	-	P507	-	-	-	-	-	-	-	CTS5/RTS5/SS5	-	-	-	-	SD1_WP_A	AN119	-	-	-	-	
R6 148	N4	120	81	-	-	P508	-	-	-	-	-	-	-	SCK6	SCK5	-	-	-	-	-	AN020	-	-	-	
M7 149	N5	121	82	VCC	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-		
N7 150	M5	122	83	VSS	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-		
P7 151	M6	123	84	-	-	IRQ13	P015	-	-	-	-	-	-	-	-	-	-	-	-	AN006/AN106	DA1/IVCMP1	-	-	-	
R7 152	N6	124	85	-	-	P014	-	-	-	-	-	-	-	-	-	-	-	-	-	AN005/AN105	DA0/IVREF3	-	-	-	
P8 153	M7	125	86	VREFL	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
R8 154	N7	126	87	VREFH	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
N8 155	L7	127	88	AVCC0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
N9 156	L8	128	89	AVSS0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
P9 157	M8	129	90	VREFL0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
R9 158	N8	130	91	VREFH0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
M8 159	-	-	-	IRQ14-DS	P010	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN103	-	-	-	-	
M9 160	M9	131	-	IRQ13-DS	P009	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN004	-	-	-	-	
P10 161	N9	132	92	-	IRQ12-DS	P008	-	-	-	-	-	-	-	-	-	-	-	-	-	AN003	-	-	-	-	
M6 162	K7	133	93	-	-	P007	-	-	-	-	-	-	-	-	-	-	-	-	-	PGAV/S100/A N107	-	-	-	-	
N10 163	L9	134	94	-	IRQ11-DS	P006	-	-	-	-	-	-	-	-	-	-	-	-	-	AN102	IVCMP2	-	-	-	
R10 164	K8	135	95	-	IRQ10-DS	P005	-	-	-	-	-	-	-	-	-	-	-	-	-	AN101	IVCMP2	-	-	-	
P11 165	K9	136	96	-	IRQ9-DS	P004	-	-	-	-	-	-	-	-	-	-	-	-	-	AN100	IVCMP2	-	-	-	
M5 166	K10	137	97	-	-	P003	-	-	-	-	-	-	-	-	-	-	-	-	-	PGAV/S000/A N007	-	-	-	-	
R11 167	M10	138	98	-	IRQ8-DS	P002	-	-	-	-	-	-	-	-	-	-	-	-	-	AN002	IVCMP2	-	-	-	
N11 168	N10	139	99	-	IRQ7-DS	P001	-	-	-	-	-	-	-	-	-	-	-	-	-	AN001	IVCMP2	-	-	-	
R12 169	L10	140	100	-	IRQ6-DS	P000	-	-	-	-	-	-	-	-	-	-	-	-	-	AN000	IVCMP2	-	-	-	
M10 170	N11	141	-	VSS	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
M11 171	N12	142	-	VCC	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
P12 172	-	-	-	-	P806	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_EXT_CLK_B	-	-	-	-	
R13 173	-	-	-	-	P805	-	-	-	-	-	-	-	-	TXD5	-	-	-	-	-	LCD_DATA_17_B	-	-	-	-	
N12 174	-	-	-	-	P513	-	-	-	-	-	-	-	-	RXD5	-	-	-	-	-	LCD_DATA_16_B	-	-	-	-	
R14 175	M11	143	-	IRQ14	P512	-	-	-	-	-	-	GTIOC0A	CTX1	TXD4/MOSI4/SDA4	-	SCL2	-	-	-	-	-	-	-	VSYNC	
P13 176	M12	144	-	-	IRQ15	P511	-	-	-	-	-	-	GTIOC0B	CRX1	RXD4/MISO4/SCL4	-	SDA2	-	-	-	-	-	-	-	PCKO

Note: Some pin names have the added suffix of _A, _B, and _C. When assigning the GPT, IIC, SPI, SSIE, ETHERC (RMII), SDHI, and GLCDC functionality, select the functional pins with the same suffix.

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

$VCC = AVCC0 = VCC_USB = VBATT = 2.7$ to 3.6 V, $2.7 \leq VREFH0/VREFH \leq AVCC0$, $VCC_USBHS = AVCC_USBHS = 3.0$ to 3.6 V, $VSS = AVSS0 = VREFL0/VREFL = VSS_USB = VSS1_USBHS = VSS2_USBHS = PVSS_USBHS = AVSS_USBHS = 0$ V, $T_a = Topr$.

Figure 2.1 shows the timing conditions.

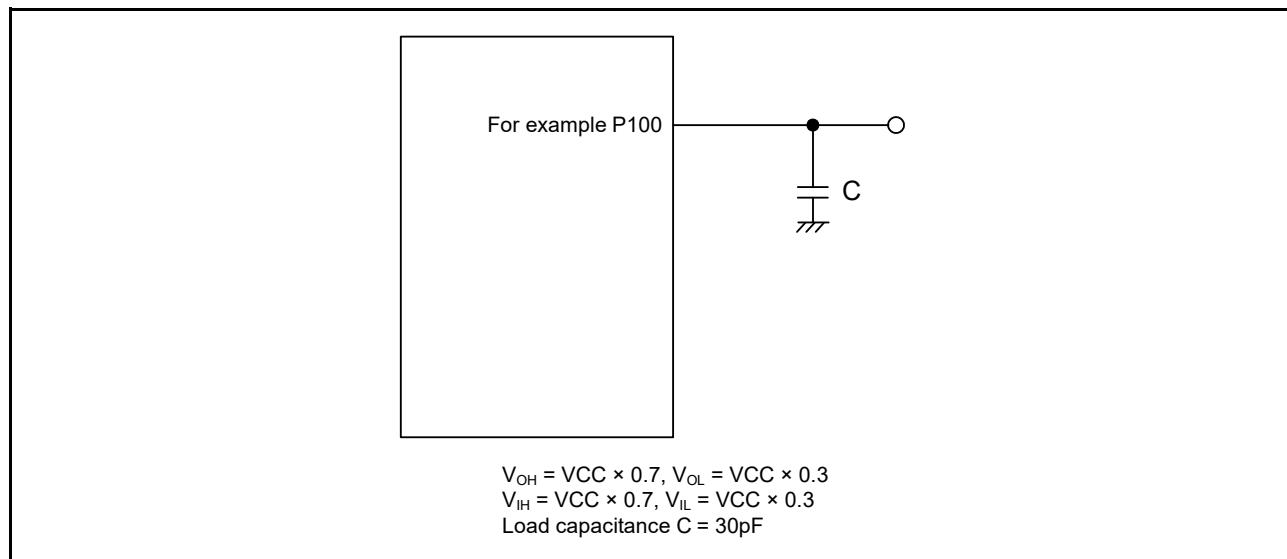


Figure 2.1 Input or output timing measurement conditions

The measurement conditions of timing specification in each peripherals are recommended for the best peripheral operation, however make sure to adjust driving abilities of each pins to meet your conditions.

2.1 Absolute Maximum Ratings

Table 2.1 Absolute maximum ratings

Parameter	Symbol	Value	Unit
Power supply voltage	VCC, VCC_USB *2	-0.3 to +4.0	V
VBATT power supply voltage	VBATT	-0.3 to +4.0	V
Input voltage (except for 5V-tolerant ports*1)	V_{in}	-0.3 to $VCC + 0.3$	V
Input voltage (5V-tolerant ports*1)	V_{in}	-0.3 to + $VCC + 4.0$ (max 5.8)	V
Reference power supply voltage	VREFH/VREFH0	-0.3 to $AVCC0 + 0.3$	V
Analog power supply voltage	$AVCC0$ *2	-0.3 to +4.0	V
USBHS power supply voltage	VCC_USBHS	-0.3 to +4.0	V
USBHS analog power supply voltage	$AVCC_USBHS$	-0.3 to +4.0	V
Analog input voltage (except for P000 to P007)	V_{AN}	-0.3 to $AVCC0 + 0.3$	V
Analog input voltage (P000 to P007) when PGA differential input is disabled	V_{AN}	-0.3 to $AVCC0 + 0.3$	V
Analog input voltage (P000 to P002, P004 to P006) when PGA differential input is enabled	V_{AN}	-1.3 to $AVCC0 + 0.3$	V
Analog input voltage (P003, P007) when PGA differential input is enabled	V_{AN}	-0.8 to $AVCC0 + 0.3$	V
Operating temperature*3,*4,*5	T_{opr}	-40 to +85 -40 to +105	°C
Storage temperature	T_{stg}	-55 to +125	°C

Caution: Permanent damage to the MCU might result if absolute maximum ratings are exceeded.

- Note 1. Ports P205, P206, P400, P401, P407 to P415, P511, P512, P708 to P713, and PB01 are 5V-tolerant.
- Note 2. Connect AVCC0 and VCC_USB to VCC.
- Note 3. See [section 2.2.1, T_j/T_a Definition](#).
- Note 4. Contact a Renesas Electronics sales office for information on derating operation when T_a = +85°C to +105°C. Derating is the systematic reduction of load for improved reliability.
- Note 5. The upper limit of operating temperature is 85°C or 105°C, depending on the product. For details, see [section 1.3, Part Numbering](#).

Table 2.2 Recommended operating conditions

Parameter	Symbol	Value	Min	Typ	Max	Unit
Power supply voltages	VCC	When USB/SDRAM is not used	2.7	-	3.6	V
		When USB/SDRAM is used	3.0	-	3.6	V
	VSS		-	0	-	V
USB power supply voltages	VCC_USB, VCC_USBHS			-	VCC	-
	VSS_USB, AVSS_USBHS, PVSS_USBHS, VSS1_USBHS, VSS2_USBHS			-	0	-
VBATT power supply voltage	VBATT		1.8	-	3.6	V
Analog power supply voltages	AVCC0*1			-	VCC	-
	AVSS0			-	0	-

- Note 1. Connect AVCC0 to VCC. When neither the A/D converter nor the D/A converter nor the comparator is in use, do not leave the AVCC0, VREFH/VREFH0, AVSS0, and VREFL/VREFL0 pins open. Connect the AVCC0 and VREFH/VREFH0 pins to VCC, and the AVSS0 and VREFL/VREFL0 pins to VSS, respectively.

2.2 DC Characteristics

2.2.1 T_j/T_a Definition

Table 2.3 DC characteristics

Conditions: Products with operating temperature (T_a) -40 to +105°C

Parameter	Symbol	Typ	Max	Unit	Test conditions
Permissible junction temperature	T _j	-	125	°C	High-speed mode
			105*1		Low-speed mode Subosc-speed mode

Note: Make sure that T_j = T_a + θ_{ja} × total power consumption (W), where total power consumption = (VCC - V_{OH}) × ΣI_{OH} + V_{OL} × ΣI_{OL} + I_{CCmax} × VCC.

- Note 1. The upper limit of operating temperature is 85°C or 105°C, depending on the product. For details, see [section 1.3, Part Numbering](#). If the part number shows the operation temperature to 85°C, then T_j max is 105°C, otherwise, 125°C.

2.2.2 I/O V_{IH} , V_{IL} **Table 2.4** I/O V_{IH} , V_{IL}

Parameter	Symbol	Min	Typ	Max	Unit		
Input voltage (except for Schmitt trigger input pins)	V_{IH}	$VCC \times 0.8$	-	-	V		
	V_{IL}	-	-	$VCC \times 0.2$			
	V_{IH}	$VCC \times 0.7$	-	-			
	V_{IL}	-	-	$VCC \times 0.3$			
	V_{IH}	2.3	-	-			
	V_{IL}	-	-	$VCC \times 0.2$			
	V_{IH}	2.1	-	-			
	V_{IL}	-	-	0.8			
	V_{IH}	2.1	-	$VCC + 3.6$ (max 5.8)			
	V_{IL}	-	-	0.8			
Schmitt trigger input voltage	V_{IH}	$VCC \times 0.7$	-	-			
	V_{IL}	-	-	$VCC \times 0.3$			
	ΔV_T	$VCC \times 0.05$	-	-			
	V_{IH}	$VCC \times 0.7$	-	$VCC + 3.6$ (max 5.8)			
	V_{IL}	-	-	$VCC \times 0.3$			
	ΔV_T	$VCC \times 0.05$	-	-			
	V_{IH}	$VCC \times 0.8$	-	$VCC + 3.6$ (max 5.8)			
	V_{IL}	-	-	$VCC \times 0.2$			
	ΔV_T	$VCC \times 0.05$	-	-			
	RTCIC0, RTCIC1, RTCIC2	When using the Battery Backup Function	V_{IH}	$V_{BATT} \times 0.8$			
			V_{IL}	-			
			ΔV_T	$V_{BATT} \times 0.05$			
		When VCC power supply is selected	V_{IH}	$VCC \times 0.8$			
			V_{IL}	-			
			ΔV_T	$VCC \times 0.05$			
	When not using the Battery Backup Function		V_{IH}	$VCC \times 0.8$			
			V_{IL}	-			
			ΔV_T	$VCC \times 0.05$			
		Other input pins*4	V_{IH}	$VCC \times 0.8$			
			V_{IL}	-			
			ΔV_T	$VCC \times 0.05$			
Ports	5V-tolerant ports*5, *7			V_{IH}	$VCC \times 0.8$		
				V_{IL}	-		
	Other input pins*6			V_{IH}	$VCC \times 0.8$		
				V_{IL}	-		

Note 1. SCL0_B (P204), SCL1_B, SDA1_B (total 3 pins).

Note 2. SCL0_A, SDA0_A, SCL0_B (P408), SDA0_B, SCL1_A, SDA1_A, SCL2, SDA2 (total 8 pins).

Note 3. RES and peripheral function pins associated with P205, P206, P400, P401, P407 to P415, P511, P512, P708 to P713, PB01 (total 23 pins).

- Note 4. All input pins except for the peripheral function pins already described in the table.
- Note 5. P205, P206, P400, P401, P407 to P415, P511, P512, P708 to P713, PB01 (total 22 pins).
- Note 6. All input pins except for the ports already described in the table.
- Note 7. When VCC is less than 2.7 V, the input voltage of 5 V-tolerant ports should be less than 3.6 V, otherwise breakdown might occur because the 5 V-tolerant ports are electrically controlled to not violate the breakdown voltage.

2.2.3 I/O I_{OH} , I_{OL}

Table 2.5 I/O I_{OH} , I_{OL}

Parameter			Symbol	Min	Typ	Max	Unit	
Permissible output current (average value per pin)	Ports P008 to P010, P201	-	I_{OH}	-	--	-2.0	mA	
			I_{OL}	-	-	2.0	mA	
	Ports P014, P015	-	I_{OH}	-	-	-4.0	mA	
			I_{OL}	-	-	4.0	mA	
	Ports P205, P206, P407 to P415, P602, P708 to P713, PB01 (total 19 pins)	Low drive* ¹	I_{OH}	-	-	-2.0	mA	
			I_{OL}	-	-	2.0	mA	
		Middle drive* ²	I_{OH}	-	-	-4.0	mA	
			I_{OL}	-	-	4.0	mA	
		High drive* ³	I_{OH}	-	-	-20	mA	
			I_{OL}	-	-	20	mA	
		Other output pins* ⁴	I_{OH}	-	-	-2.0	mA	
			I_{OL}	-	-	2.0	mA	
			I_{OH}	-	-	-4.0	mA	
			I_{OL}	-	-	4.0	mA	
			I_{OH}	-	-	-8.0	mA	
			I_{OL}	-	-	8.0	mA	
			I_{OH}	-	-	-4.0	mA	
			I_{OL}	-	-	4.0	mA	
Permissible output current (max value per pin)	Ports P008 to P010, P201	-	I_{OH}	-	-	-4.0	mA	
			I_{OL}	-	-	4.0	mA	
	Ports P014, P015	-	I_{OH}	-	-	-8.0	mA	
			I_{OL}	-	-	8.0	mA	
	Ports P205, P206, P407 to P415, P602, P708 to P713, PB01 (total 19 pins)	Low drive* ¹	I_{OH}	-	-	-4.0	mA	
			I_{OL}	-	-	4.0	mA	
		Middle drive* ²	I_{OH}	-	-	-8.0	mA	
			I_{OL}	-	-	8.0	mA	
		High drive* ³	I_{OH}	-	-	-40	mA	
			I_{OL}	-	-	40	mA	
		Other output pins* ⁴	I_{OH}	-	-	-4.0	mA	
			I_{OL}	-	-	4.0	mA	
			I_{OH}	-	-	-8.0	mA	
			I_{OL}	-	-	8.0	mA	
			I_{OH}	-	-	-32	mA	
			I_{OL}	-	-	32	mA	
Permissible output current (max value total pins)	Maximum of all output pins			$\Sigma I_{OH} \text{ (max)}$	-	-80	mA	
				$\Sigma I_{OL} \text{ (max)}$	-	-80	mA	

Caution: To protect the reliability of the MCU, the output current values should not exceed the values in this table. The average output current indicates the average value of current measured during 100 μ s.

- Note 1. This is the value when low driving ability is selected in the port drive capability bit in the PmnPFS register. The selected driving ability is retained in Deep Software Standby mode.
- Note 2. This is the value when middle driving ability is selected in the port drive capability bit in the PmnPFS register. The selected driving ability is retained in Deep Software Standby mode.
- Note 3. This is the value when high driving ability is selected in the port drive capability bit in the PmnPFS register. The selected driving ability is retained in Deep Software Standby mode.

Note 4. Except for P000 to P007, P200, which are input ports.

2.2.4 I/O V_{OH} , V_{OL} , and Other Characteristics

Table 2.6 I/O V_{OH} , V_{OL} , and other characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Output voltage	V_{OL}	-	-	0.4	V	$I_{OL} = 3.0 \text{ mA}$
	V_{OL}	-	-	0.6		$I_{OL} = 6.0 \text{ mA}$
	V_{OL}	-	-	0.4		$I_{OL} = 15.0 \text{ mA}$ (ICFER.FMPE = 1)
	V_{OL}	-	0.4	-		$I_{OL} = 20.0 \text{ mA}$ (ICFER.FMPE = 1)
	V_{OH}	VCC - 0.5	-	-		$I_{OH} = -1.0 \text{ mA}$
	V_{OL}	-	-	0.4		$I_{OL} = 1.0 \text{ mA}$
	V_{OH}	VCC - 1.0	-	-		$I_{OH} = -20 \text{ mA}$ VCC = 3.3 V
	V_{OL}	-	-	1.0		$I_{OL} = 20 \text{ mA}$ VCC = 3.3 V
	V_{OH}	VCC - 0.5	-	-		$I_{OH} = -1.0 \text{ mA}$
	V_{OL}	-	-	0.5		$I_{OL} = 1.0 \text{ mA}$
Input leakage current	$ I_{inl} $	-	-	5.0	μA	$V_{in} = 0 \text{ V}$ $V_{in} = 5.5 \text{ V}$
		-	-	1.0		$V_{in} = 0 \text{ V}$ $V_{in} = \text{VCC}$
		-	-	45.0		$V_{in} = 0 \text{ V}$ $V_{in} = \text{VCC}$
		-	-	1.0		$V_{in} = 0 \text{ V}$ $V_{in} = \text{VCC}$
		-	-	5.0		$V_{in} = 0 \text{ V}$ $V_{in} = 5.5 \text{ V}$
Three-state leakage current (off state)	$ I_{TSIL} $	-	-	1.0	μA	$V_{in} = 0 \text{ V}$ $V_{in} = \text{VCC}$
		-	-	5.0		$V_{in} = 0 \text{ V}$ $V_{in} = \text{VCC}$
Input pull-up MOS current	I_p	-300	-	-10	μA	VCC = 2.7 to 3.6 V $V_{in} = 0 \text{ V}$
Input capacitance	C_{in}	-	-	16	pF	$V_{bias} = 0 \text{ V}$ $V_{amp} = 20\text{mV}$ $f = 1 \text{ MHz}$ $T_a = 25^\circ\text{C}$
		-	-	8		

Note 1. SCL0_A, SDA0_A (total 2 pins).

Note 2. This is the value when high driving ability is selected in the port drive capability bit in the PmnPFS register.

The selected driving ability is retained in Deep Software Standby mode.

Note 3. P0nPFS.ASEL (n = 3 or 7) = 1.

Note 4. P0nPFS.ASEL (n = 3 or 7) = 0.

2.2.5 Operating and Standby Current

Table 2.7 Operating and standby current (1 of 2)

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions	
Supply current* ¹	High-speed mode	Maximum* ²	I _{CC} * ³	-	-	137* ²	mA	ICLK = 120 MHz PCLKA = 120 MHz ⁷ PCLKB = 60 MHz PCLKC = 60 MHz PCLKD = 120 MHz FCLK = 60 MHz BCLK = 120 MHz	
		CoreMark®* ⁵		-	21	-			
		Normal mode		-	34	-			
		All peripheral clocks enabled, while (1) code executing from flash* ⁴		-	14	-			
		All peripheral clocks disabled, while (1) code executing from flash* ^{5, *6}		-	12	46			
		Sleep mode* ^{5, *6}		-	6	-			
		Increase during BGO operation		-	8	-			
		Data flash P/E		-	2.4	-		ICLK = 1 MHz	
		Code flash P/E		-	2	-		ICLK = 32.768 kHz	
		Low-speed mode* ⁵		-	1.8	18		Ta ≤ 85°C	
		Subosc-speed mode* ⁵		-	1.8	28		Ta ≤ 105°C	
	Deep Software Standby mode	Software Standby mode		-	30	79	µA	Ta ≤ 85°C	
		Power supplied to Standby SRAM and USB resume detecting unit		-	30	113	µA	Ta ≤ 105°C	
		Power not supplied to SRAM or USB resume detecting unit	Power-on reset circuit low-power function disabled	-	13	33	µA	Ta ≤ 85°C	
				-	13	40	µA	Ta ≤ 105°C	
				-	6.3	28	µA	Ta ≤ 85°C	
				-	6.3	34	µA	Ta ≤ 105°C	
		Increase when the RTC and AGT are operating	When the low-speed on-chip oscillator (LOCO) is in use	-	5	-		-	
				-	1.0	-		-	
				-	1.5	-		-	
		RTC operating while VCC is off (with the battery backup function, only the RTC and sub-clock oscillator operate)	When a crystal oscillator for low clock loads is in use	-	0.9	-		V _{BATT} = 1.8 V, VCC = 0 V	
				-	1.3	-		V _{BATT} = 3.3 V, VCC = 0 V	
				-	1.1	-		V _{BATT} = 1.8 V, VCC = 0 V	
				-	1.8	-		V _{BATT} = 3.3 V, VCC = 0 V	
Analog power supply current	During 12-bit A/D conversion		AI _{CC}	-	0.8	1.1	mA	-	
	During 12-bit A/D conversion with S/H amp			-	2.3	3.3	mA	-	
	PGA (1ch)			-	1	3	mA	-	
	ACMPHS (1unit)			-	100	150	µA	-	
	Temperature sensor			-	0.1	0.2	mA	-	
	During D/A conversion (per unit)	Without AMP output		-	0.1	0.2	mA	-	
		With AMP output		-	0.6	1.1	mA	-	
	Waiting for A/D, D/A conversion (all units)			-	0.9	1.6	mA	-	
	ADC12, DAC12 in standby modes (all units)* ⁸			-	2	8	µA	-	
Reference power supply current (VREFH0)	During 12-bit A/D conversion (unit 0)		AI _{REFHO}	-	70	120	µA	-	
	Waiting for 12-bit A/D conversion (unit 0)			-	0.07	0.5	µA	-	
	ADC12 in standby modes (unit 0)			-	0.07	0.5	µA	-	
	ADC12 in standby modes (unit 0)								
Reference power supply current (VREFH)	During 12-bit A/D conversion (unit 1)		AI _{REFH}	-	70	120	µA	-	
	During D/A conversion (per unit)	Without AMP output		-	0.1	0.4	mA	-	
		With AMP ouput		-	0.1	0.4	mA	-	
	Waiting for 12-bit A/D (unit 1), D/A (all units) conversion			-	0.07	0.8	µA	-	
	ADC12 unit 1 in standby modes			-	0.07	0.8	µA	-	
	ADC12 unit 1 in standby modes								

Table 2.7 Operating and standby current (2 of 2)

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
USB operating current	Low speed	USB	I _{CCUSBL}	-	3.5	6.5	mA VCC_USB
		USBHS		-	10.5	13.5	mA VCC_USBHS = AVCC_USBHS (PHYSET.HSEB = 0)
		USBHS		-	2.8	3.6	mA VCC_USBHS = AVCC_USBHS (PHYSET.HSEB = 1)
	Full speed	USB	I _{CCUSBFS}	-	4.0	10.0	mA VCC_USB
		USBHS		-	14	22	mA VCC_USBHS = AVCC_USBHS (PHYSET.HSEB = 0)
		USBHS		-	6.5	13.0	mA VCC_USBHS = AVCC_USBHS (PHYSET.HSEB = 1)
	High speed	USBHS	I _{CCUSBHS}	-	50	65	mA VCC_USBHS = AVCC_USBHS
	Standby mode (direct power down)	USBHS	I _{CCUSBSBY}	-	0.5	4.5	μA VCC_USBHS = AVCC_USBHS

Note 1. Supply current values are with all output pins unloaded and all input pull-up MOS transistors in the off state.

Note 2. Measured with clocks supplied to the peripheral functions. This does not include the BGO operation.

Note 3. ICC depends on f (ICLK) as follows. (ICLK:PCLKA:PCLKB:PCLKC:PCLKD:BCK:EBCLK = 2:2:1:1:2:1:1)

$$\text{ICC Max.} = 0.84 \times f + 37 \text{ (max. operation in High-speed mode)}$$

$$\text{ICC Typ.} = 0.09 \times f + 3.7 \text{ (normal operation in High-speed mode)}$$

$$\text{ICC Typ.} = 0.6 \times f + 1.8 \text{ (Low-speed mode 1)}$$

$$\text{ICC Max.} = 0.08 \times f + 37 \text{ (Sleep mode).}$$

Note 4. This does not include the BGO operation.

Note 5. Supply of the clock signal to peripherals is stopped in this state. This does not include the BGO operation.

Note 6. FCLK, BCLK, PCLKA, PCLKB, PCLKC, and PCLKD are set to divided by 64 (3.75 MHz).

Note 7. When using ETHERC, GLCDC, DRW, and JPEG, PCLKA frequency is such that PCLKA = ICLK.

Note 8. When the MCU is in Software Standby mode or the MSTPCRD.MSTPD16 (ADC120 Module Stop bit) and MSTPCRD.MSTPD15 (ADC121 Module Stop bit) are in the module-stop state. See section 47.6.8, Available Functions and Register Settings of AN000 to AN002, AN007, AN100 to AN102, and AN107 in User's Manual.

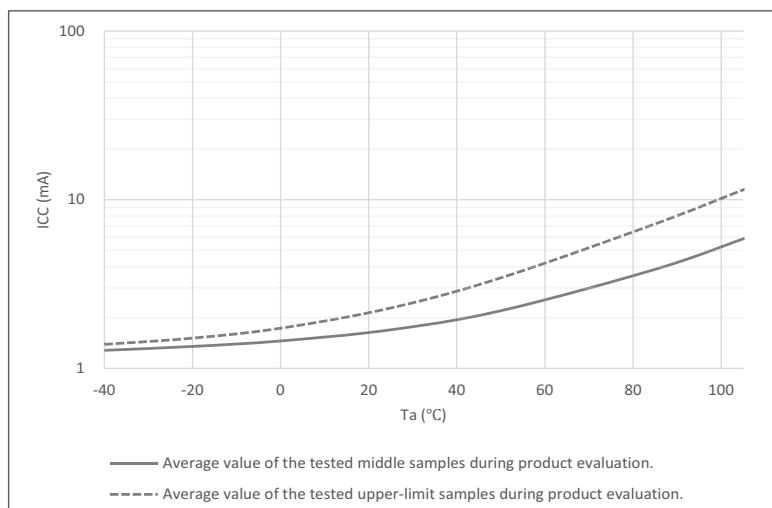


Figure 2.2 Temperature dependency in Software Standby mode (reference data)

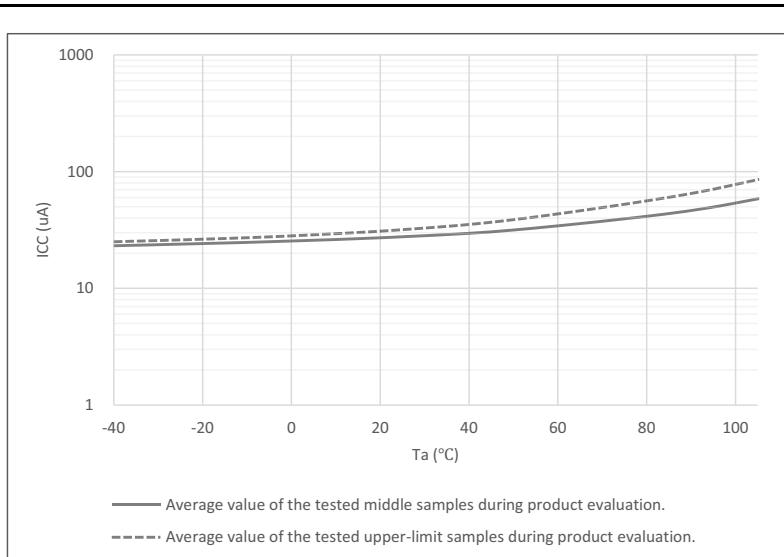


Figure 2.3 Temperature dependency in Deep Software Standby mode, power supplied to standby SRAM and USB resume detecting unit (reference data)

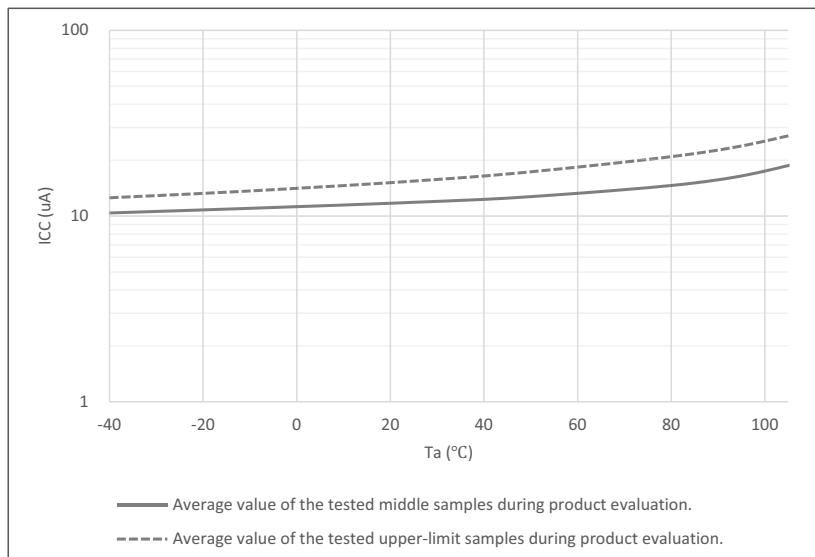


Figure 2.4 Temperature dependency in Deep Software Standby mode, power not supplied to SRAM or USB resume detecting unit, power-on reset circuit low-power function disabled (reference data)

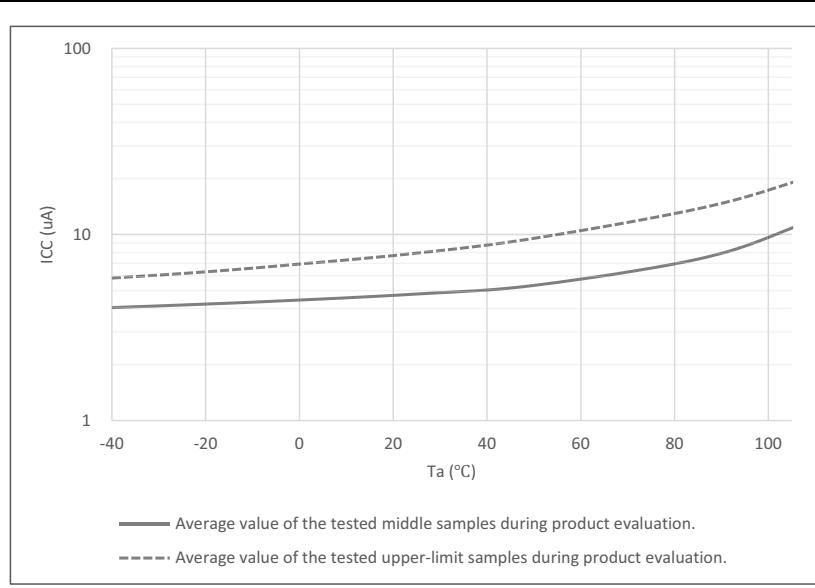


Figure 2.5 Temperature dependency in Deep Software Standby mode, power not supplied to SRAM or USB resume detecting unit, power-on reset circuit low-power function enabled (reference data)

2.2.6 VCC Rise and Fall Gradient and Ripple Frequency

Table 2.8 Rise and fall gradient characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
VCC rising gradient	SrVCC	0.0084	-	20	ms/V	-
		0.0084	-	-		-
		0.0084	-	20		-
VCC falling gradient*2	SfVCC	0.0084	-	-	ms/V	-

Note 1. At boot mode, the reset from voltage monitor 0 is disabled regardless of the value of OFS1.LVDAS bit.

Note 2. This applies when VBATT is used.

Table 2.9 Rise and fall gradient and ripple frequency characteristics

The ripple voltage must meet the allowable ripple frequency $f_{r(VCC)}$ within the range between the VCC upper limit (3.6 V) and lower limit (2.7 V). When the VCC change exceeds $VCC \pm 10\%$, the allowable voltage change rising and falling gradient $dt/dVCC$ must be met.

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Allowable ripple frequency	$f_r(VCC)$	-	-	10	kHz	Figure 2.6 $V_{r(VCC)} \leq VCC \times 0.2$
		-	-	1	MHz	Figure 2.6 $V_{r(VCC)} \leq VCC \times 0.08$
		-	-	10	MHz	Figure 2.6 $V_{r(VCC)} \leq VCC \times 0.06$
Allowable voltage change rising and falling gradient	$dt/dVCC$	1.0	-	-	ms/V	When VCC change exceeds $VCC \pm 10\%$

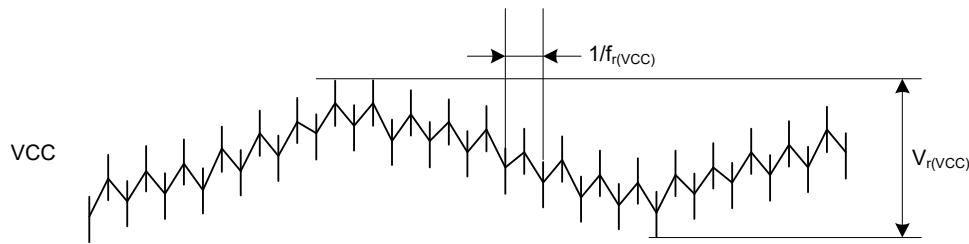


Figure 2.6 Ripple waveform

2.3 AC Characteristics

2.3.1 Frequency

Table 2.10 Operation frequency value in high-speed mode

Parameter	Symbol	Min	Typ	Max	Unit
Operation frequency	f	-	-	120	MHz
		-	-	120	
		-	-	60	
		- ³	-	60	
		-	-	120	
		- ¹	-	60	
		-	-	120	
		-	-	60	
		-	-	120	
SDCLK pin output	$VCC \geq 3.0\text{ V}$				
EBCLK pin output					

- Note 1. FCLK must run at a frequency of at least 4 MHz when programming or erasing the flash memory.
 Note 2. See section 9, Clock Generation Circuit in User's Manual for the relationship between the ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK frequencies.
 Note 3. When the ADC12 is used, the PCLKC frequency must be at least 1 MHz.

Table 2.11 Operation frequency value in low-speed mode

Parameter		Symbol	Min	Typ	Max	Unit
Operation frequency	System clock (ICLK)*2	f	-	-	1	MHz
	Peripheral module clock (PCLKA)*2		-	-	1	
	Peripheral module clock (PCLKB)*2		-	-	1	
	Peripheral module clock (PCLKC)*2,*3		*3	-	1	
	Peripheral module clock (PCLKD)*2		-	-	1	
	Flash interface clock (FCLK)*1, *2		-	-	1	
	External bus clock (BCLK)		-	-	1	
	EBCLK pin output		-	-	1	

- Note 1. Programming or erasing the flash memory is disabled in low-speed mode.
 Note 2. See section 9, Clock Generation Circuit in User's Manual for the relationship between the ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK frequencies.
 Note 3. When the ADC12 is used, the PCLKC frequency must be set to at least 1 MHz.

Table 2.12 Operation frequency value in Subosc-speed mode

Parameter		Symbol	Min	Typ	Max	Unit
Operation frequency	System clock (ICLK)*2	f	27.8	-	37.7	kHz
	Peripheral module clock (PCLKA)*2		-	-	37.7	
	Peripheral module clock (PCLKB)*2		-	-	37.7	
	Peripheral module clock (PCLKC)*2,*3		-	-	37.7	
	Peripheral module clock (PCLKD)*2		-	-	37.7	
	Flash interface clock (FCLK)*1, *2		27.8	-	37.7	
	External bus clock (BCLK)*2		-	-	37.7	
	EBCLK pin output		-	-	37.7	

- Note 1. Programming or erasing the flash memory is disabled in Subosc-speed mode.
 Note 2. See section 9, Clock Generation Circuit in User's Manual for the relationship between the ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK frequencies.
 Note 3. The ADC12 cannot be used.

2.3.2 Clock Timing

Table 2.13 Clock timing except for sub-clock oscillator (1 of 2)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
EBCLK pin output cycle time	t _{Bcyc}	16.6	-	-	ns	Figure 2.7
EBCLK pin output high pulse width	t _{CH}	3.3	-	-	ns	
EBCLK pin output low pulse width	t _{CL}	3.3	-	-	ns	
EBCLK pin output rise time	t _{Cr}	-	-	5.0	ns	
EBCLK pin output fall time	t _{Cf}	-	-	5.0	ns	
SDCLK pin output cycle time	t _{SDcyc}	8.33	-	-	ns	
SDCLK pin output high pulse width	t _{CH}	1.0	-	-	ns	
SDCLK pin output low pulse width	t _{CL}	1.0	-	-	ns	
SDCLK pin output rise time	t _{Cr}	-	-	3.0	ns	
SDCLK pin output fall time	t _{Cf}	-	-	3.0	ns	

Table 2.13 Clock timing except for sub-clock oscillator (2 of 2)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
EXTAL external clock input cycle time	t_{EXcyc}	41.66	-	-	ns	Figure 2.8	
EXTAL external clock input high pulse width	t_{EXH}	15.83	-	-	ns		
EXTAL external clock input low pulse width	t_{EXL}	15.83	-	-	ns		
EXTAL external clock rise time	t_{EXr}	-	-	5.0	ns		
EXTAL external clock fall time	t_{EXf}	-	-	5.0	ns		
Main clock oscillator frequency	f_{MAIN}	8	-	24	MHz	-	
Main clock oscillation stabilization wait time (crystal) *1	$t_{MAINOSCWT}$	-	-	*1	ms	Figure 2.9	
LOCO clock oscillation frequency	f_{LOCO}	27.8528	32.768	37.6832	kHz	-	
LOCO clock oscillation stabilization wait time	t_{LOCOWT}	-	-	60.4	μs	Figure 2.10	
ILOCO clock oscillation frequency	f_{ILOCO}	12.75	15	17.25	kHz	-	
MOCO clock oscillation frequency	f_{MOCO}	6.8	8	9.2	MHz	-	
MOCO clock oscillation stabilization wait time	t_{MOCOWT}	-	-	15.0	μs	-	
HOCO clock oscillator oscillation frequency	Without FLL	f_{HOCO16}	15.78	16	16.22	MHz	$-20 \leq Ta \leq 105^{\circ}C$
		f_{HOCO18}	17.75	18	18.25		
		f_{HOCO20}	19.72	20	20.28		
		f_{HOCO16}	15.71	16	16.29	MHz	$-40 \leq Ta \leq -20^{\circ}C$
		f_{HOCO18}	17.68	18	18.32		
		f_{HOCO20}	19.64	20	20.36		
	With FLL	f_{HOCO16}	15.955	16	16.045		$-40 \leq Ta \leq 105^{\circ}C$ Sub-clock frequency accuracy is ± 50 ppm.
		f_{HOCO18}	17.949	18	18.051		
		f_{HOCO20}	19.944	20	20.056		
HOCO clock oscillation stabilization wait time*2	t_{HOCOWT}	-	-	64.7	μs	-	
FLL stabilization wait time	t_{FLLWT}	-	-	1.8	ms	-	
PLL clock frequency	f_{PLL}	120	-	240	MHz	-	
PLL clock oscillation stabilization wait time	t_{PLLWT}	-	-	174.9	μs	Figure 2.11	

- Note 1. When setting up the main clock oscillator, ask the oscillator manufacturer for an oscillation evaluation and use the results as the recommended oscillation stabilization time. Set the MOSCWT register to a value equal to or greater than the recommended value.
After changing the setting in the MOSCCR.MOSTP bit to start main clock operation, read the OSCSF.MOSCSF flag to confirm that it is 1, and then start using the main clock oscillator.
- Note 2. This is the time from release from reset state until the HOCO oscillation frequency (f_{HOCO}) reaches the range for guaranteed operation.

Table 2.14 Clock timing for the sub-clock oscillator

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Sub-clock frequency	f_{SUB}	-	32.768	-	kHz	-
Sub-clock oscillation stabilization wait time	$t_{SUBOSCWT}$	-	-	*1	s	Figure 2.12

- Note 1. When setting up the sub-clock oscillator, ask the oscillator manufacturer for an oscillation evaluation and use the results as the recommended oscillation stabilization time.
After changing the setting in the SOSCCR.SOSTP bit to start sub-clock operation, only start using the sub-clock oscillator after the sub-clock oscillation stabilization time elapses with an adequate margin. Two times the value shown is recommended.

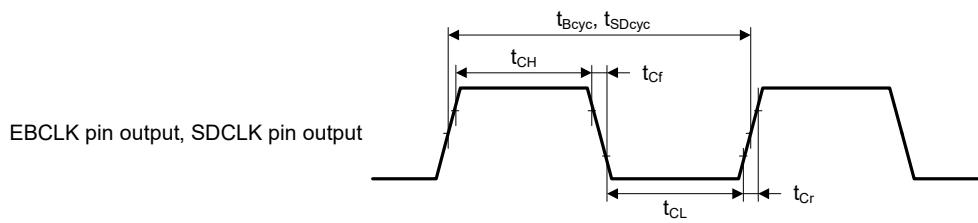


Figure 2.7 EBCLK and SDCLK output timing

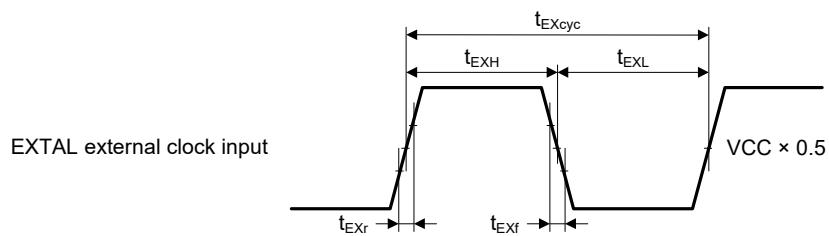


Figure 2.8 EXTAL external clock input timing

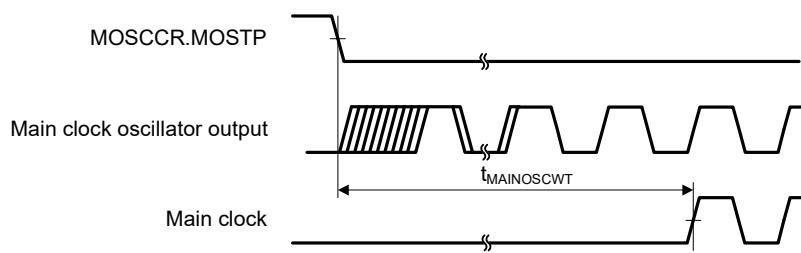


Figure 2.9 Main clock oscillation start timing

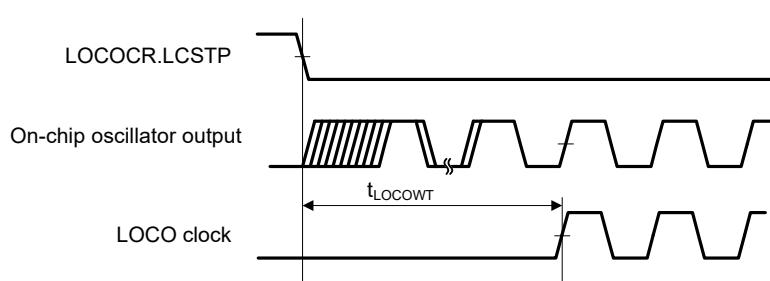
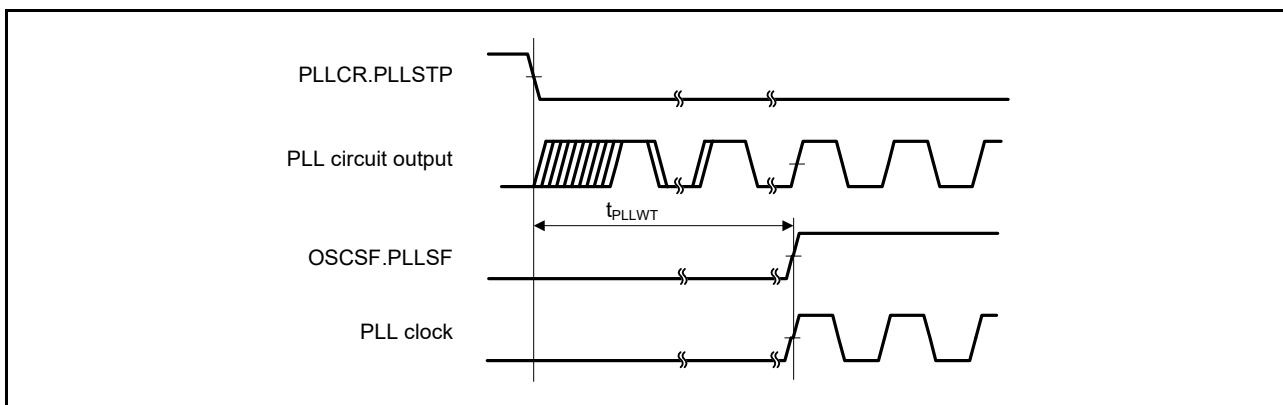
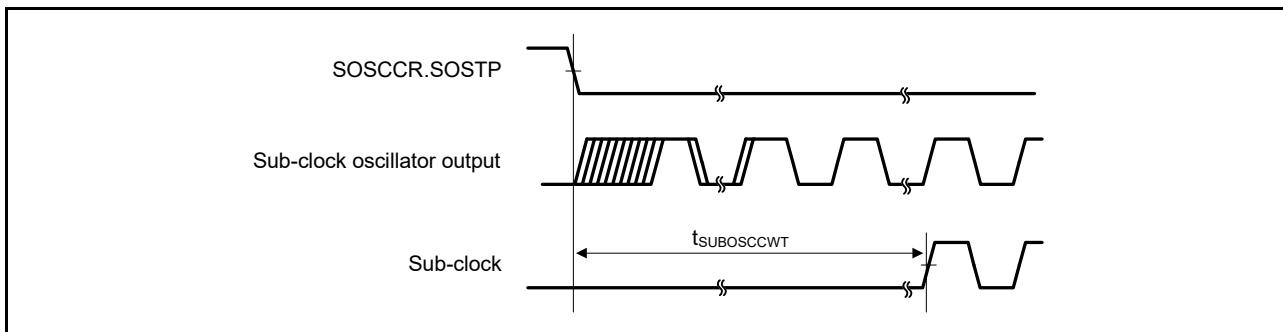


Figure 2.10 LOCO clock oscillation start timing

**Figure 2.11** PLL clock oscillation start timing

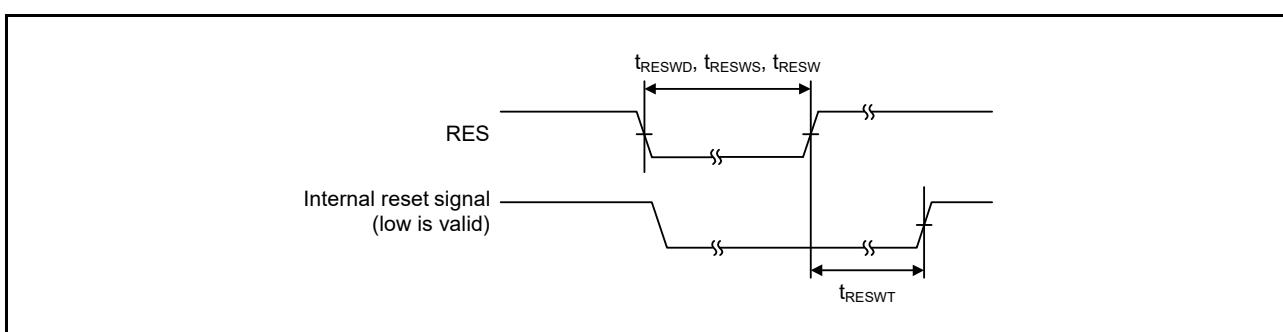
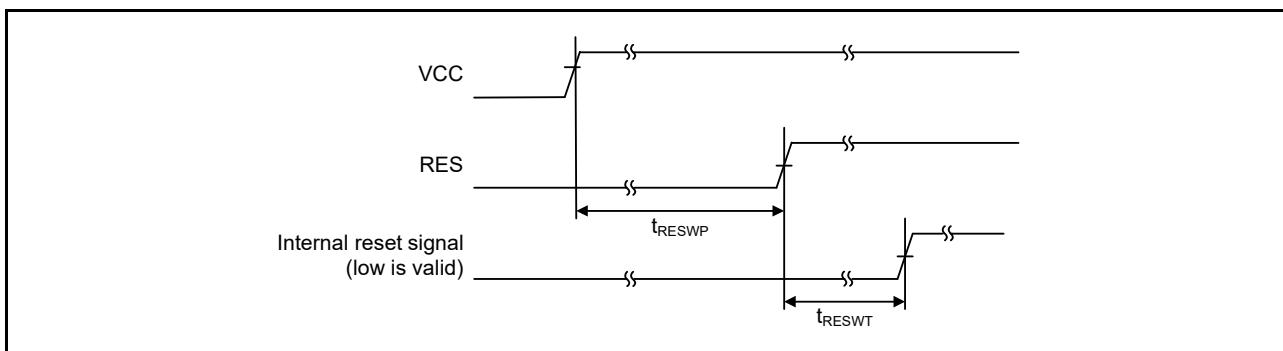
Note: Only operate the PLL is operated after main clock oscillation has stabilized.

**Figure 2.12** Sub-clock oscillation start timing

2.3.3 Reset Timing

Table 2.15 Reset timing

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
RES pulse width	Power-on	t_{RESWP}	1	-	-	ms	Figure 2.13
	Deep Software Standby mode	t_{RESWD}	0.6	-	-	ms	Figure 2.14
	Software Standby mode, Subosc-speed mode	t_{RESWS}	0.3	-	-	ms	
	All other	t_{RESW}	200	-	-	μs	
Wait time after RES cancellation		t_{RESWT}	-	29	33	μs	Figure 2.13
Wait time after internal reset cancellation (IWDT reset, WDT reset, software reset, SRAM parity error reset, SRAM ECC error reset, bus master MPU error reset, bus slave MPU error reset, stack pointer error reset)		t_{RESW2}	-	320	408	μs	-



2.3.4 Wakeup Timing

Table 2.16 Timing of recovery from low power modes

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions		
Recovery time from Software Standby mode ^{*1}	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator ^{*2}	t _{SBYMC}	-	2.4 ^{*9}	2.8 ^{*9}	ms	Figure 2.15 The division ratio of all oscillators is 1.		
		System clock source is PLL with main clock oscillator ^{*3}	t _{SBYPC}	-	2.7 ^{*9}	3.2 ^{*9}	ms			
	External clock input to main clock oscillator	System clock source is main clock oscillator ^{*4}	t _{SBYEX}	-	230 ^{*9}	280 ^{*9}	μs			
		System clock source is PLL with main clock oscillator ^{*5}	t _{SBYPE}	-	570 ^{*9}	700 ^{*9}	μs			
	System clock source is sub-clock oscillator ^{*8}		t _{SBYSC}	-	1.2 ^{*9}	1.3 ^{*9}	ms			
	System clock source is LOCO ^{*8}		t _{SBYLO}	-	1.2 ^{*9}	1.4 ^{*9}	ms			
	System clock source is HOCO clock oscillator ^{*6}		t _{SBYHO}	-	240 ^{*9, *10}	310 ^{*9, *10}	μs			
	System clock source is MOCO clock oscillator ^{*7}		t _{SBYMO}	-	220 ^{*9}	300 ^{*9}	μs			
Recovery time from Deep Software Standby mode			t _{DSBY}	-	0.65	1.0	ms	Figure 2.16		
Wait time after cancellation of Deep Software Standby mode			t _{DSBYWT}	34	-	35	t _{cyc}			
Recovery time from Software Standby mode to Snooze mode	High-speed mode when system clock source is HOCO (20 MHz)		t _{SNZ}	-	35 ^{*9, *10}	71 ^{*9, *10}	μs	Figure 2.17		
	High-speed mode when system clock source is MOCO (8 MHz)		t _{SNZ}	-	11 ^{*9}	14 ^{*9}	μs			

- Note 1. The recovery time is determined by the system clock source. When multiple oscillators are active, the recovery time can be determined with the following equation:
 Total recovery time = recovery time for an oscillator as the system clock source + the longest oscillation stabilization time of any oscillators requiring longer stabilization times than the system clock source + 2 LOCO cycles (when LOCO is operating) + 3 SOSC cycles (when Subosc is oscillating and MSTPC0 = 0 (CAC module stop)).
- Note 2. When the frequency of the crystal is 24 MHz (Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h). For other settings (MOSCWTCR is set to Xh), the recovery time can be determined with the following equation:
 $t_{SBYMC} (\text{MOSCWTCR} = Xh) = t_{SBYMC} (\text{MOSCWTCR} = 05h) + (t_{MAINOSCWT} (\text{MOSCWTCR} = Xh) - t_{MAINOSCWT} (\text{MOSCWTCR} = 05h))$
- Note 3. When the frequency of PLL is 240 MHz (Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h). For other settings (MOSCWTCR is set to Xh), the recovery time can be determined with the following equation:
 $t_{SBYMC} (\text{MOSCWTCR} = Xh) = t_{SBYMC} (\text{MOSCWTCR} = 05h) + (t_{MAINOSCWT} (\text{MOSCWTCR} = Xh) - t_{MAINOSCWT} (\text{MOSCWTCR} = 05h))$
- Note 4. When the frequency of the external clock is 24 MHz (Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h). For other settings (MOSCWTCR is set to Xh), the recovery time can be determined with the following equation:
 $t_{SBYMC} (\text{MOSCWTCR} = Xh) = t_{SBYMC} (\text{MOSCWTCR} = 00h) + (t_{MAINOSCWT} (\text{MOSCWTCR} = Xh) - t_{MAINOSCWT} (\text{MOSCWTCR} = 00h))$
- Note 5. When the frequency of PLL is 240 MHz (Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h). For other settings (MOSCWTCR is set to Xh), the recovery time can be determined with the following equation:
 $t_{SBYMC} (\text{MOSCWTCR} = Xh) = t_{SBYMC} (\text{MOSCWTCR} = 00h) + (t_{MAINOSCWT} (\text{MOSCWTCR} = Xh) - t_{MAINOSCWT} (\text{MOSCWTCR} = 00h))$
- Note 6. The HOCO frequency is 20 MHz.
- Note 7. The MOCO frequency is 8 MHz.
- Note 8. In Subosc-speed mode, the sub-clock oscillator or LOCO continues oscillating in Software Standby mode.
- Note 9. When the SNZCR.RXDREQEN bit is set to 0, the following time is added as the power supply recovery time:
 STCONR.STCON[1:0] = 00b:16 μ s (typical), 34 μ s (maximum)
 STCONR.STCON[1:0] = 11b:16 μ s (typical), 104 μ s (maximum).
- Note 10. When the SNZCR.RXDREQEN bit is set to 0, 16 μ s (typical) or 18 μ s (maximum) is added as the HOCO wait time.

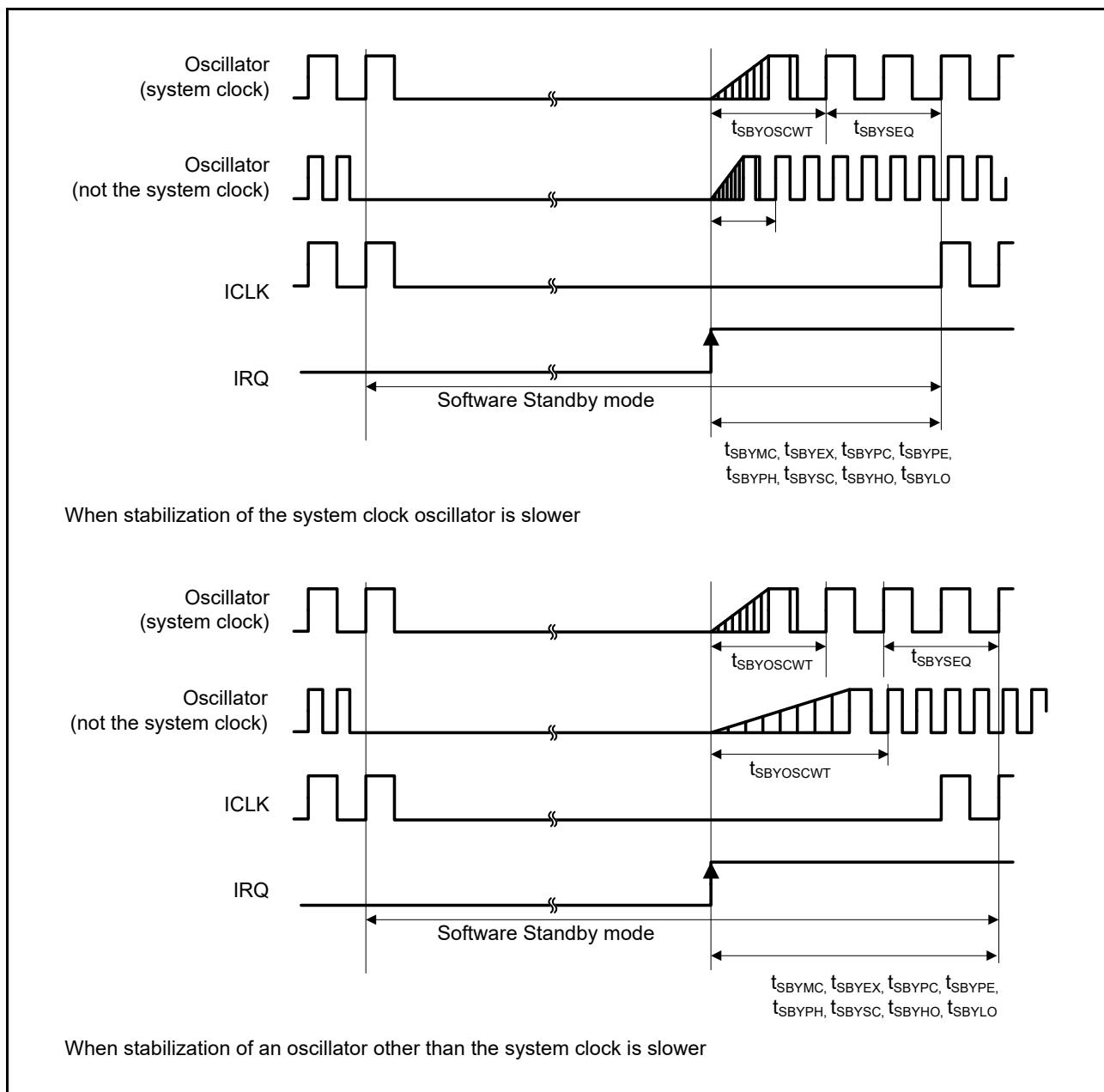


Figure 2.15 Software Standby mode cancellation timing

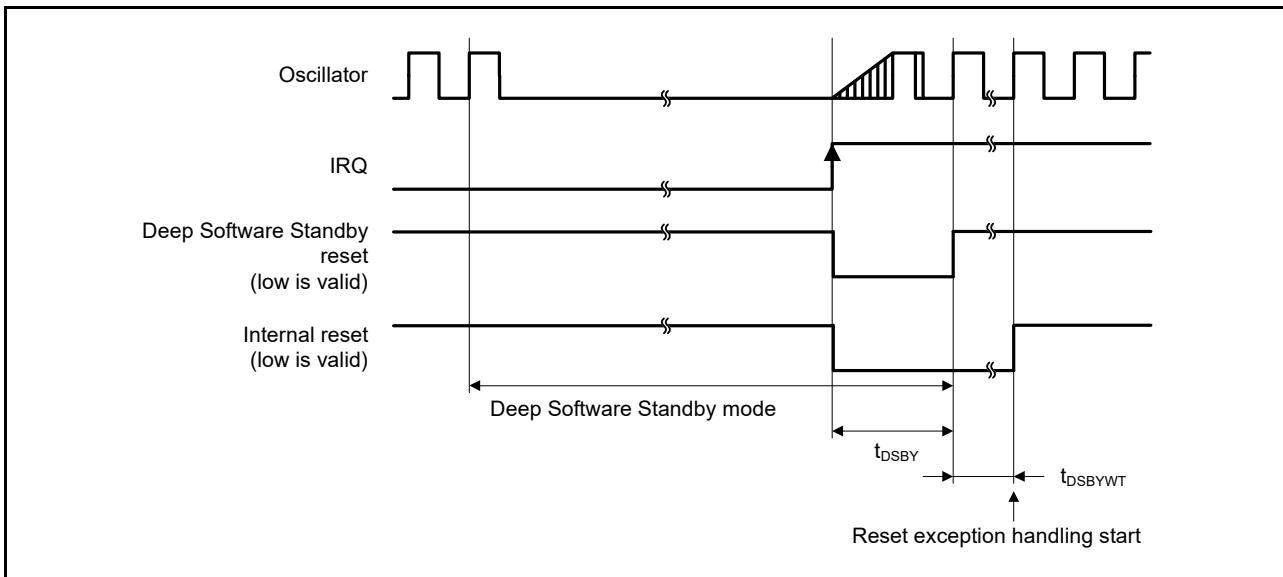


Figure 2.16 Deep Software Standby mode cancellation timing

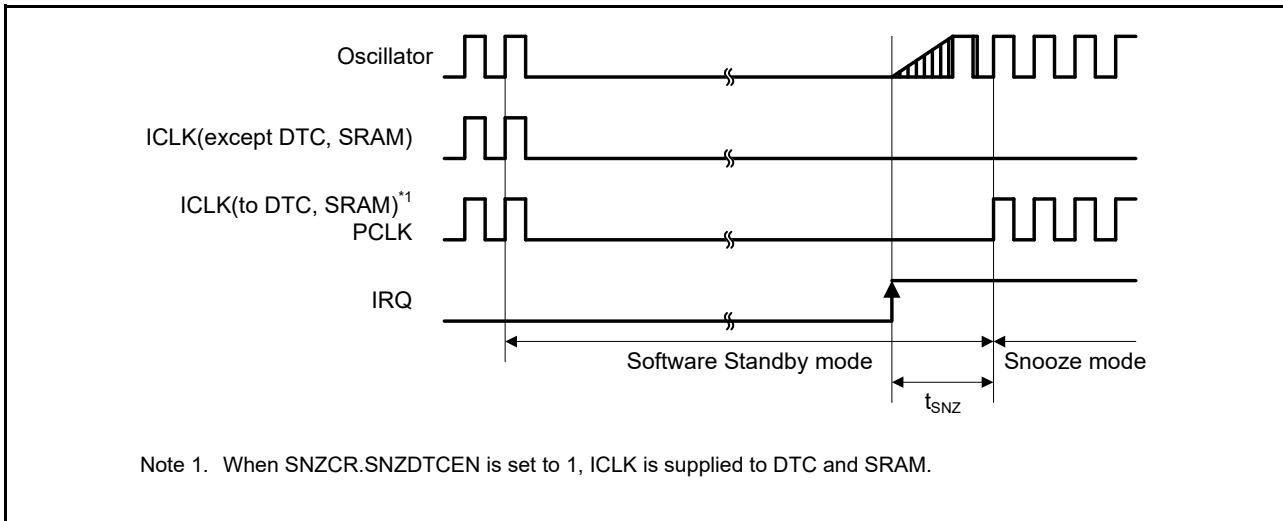


Figure 2.17 Recovery timing from Software Standby mode to Snooze mode

2.3.5 NMI and IRQ Noise Filter

Table 2.17 NMI and IRQ noise filter

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
NMI pulse width	t_{NMIW}	200	-	-	ns	NMI digital filter disabled	$t_{Pcyc} \times 2 \leq 200$ ns
		$t_{Pcyc} \times 2^{*1}$	-	-			$t_{Pcyc} \times 2 > 200$ ns
		200	-	-	ns	NMI digital filter enabled	$t_{NMICK} \times 3 \leq 200$ ns
		$t_{NMICK} \times 3.5^{*2}$	-	-			$t_{NMICK} \times 3 > 200$ ns
IRQ pulse width	t_{IRQW}	200	-	-	ns	IRQ digital filter disabled	$t_{Pcyc} \times 2 \leq 200$ ns
		$t_{Pcyc} \times 2^{*1}$	-	-			$t_{Pcyc} \times 2 > 200$ ns
		200	-	-	ns	IRQ digital filter enabled	$t_{IRQCK} \times 3 \leq 200$ ns
		$t_{IRQCK} \times 3.5^{*3}$	-	-			$t_{IRQCK} \times 3 > 200$ ns

Note: 200 ns minimum in Software Standby mode.

Note 1. t_{Pcyc} indicates the PCLKB cycle.

Note 2. t_{NMICK} indicates the cycle of the NMI digital filter sampling clock.

Note 3. t_{IRQCK} indicates the cycle of the IRQi digital filter sampling clock.

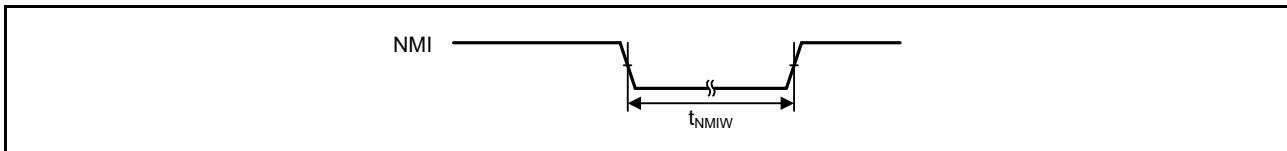


Figure 2.18 NMI interrupt input timing

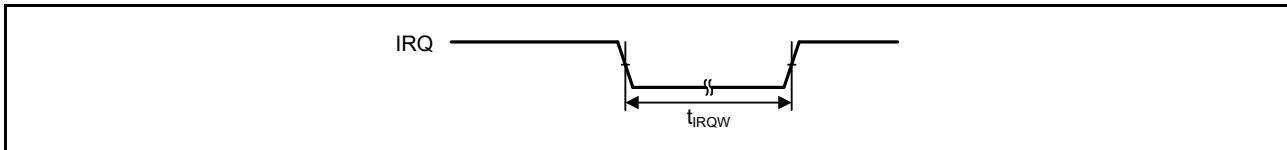


Figure 2.19 IRQ interrupt input timing

2.3.6 Bus Timing

Table 2.18 Bus timing (1 of 2)

Condition 1: When using the CS area controller (CSC).

BCLK = 8 to 120 MHz, EBCLK = 8 to 60 MHz

VCC = AVCC0 = VCC_USB = VBATT = 2.7 to 3.6 V, VREFH/VREFH0 = 2.7 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 30 pF

EBCLK: High drive output is selected in the port drive capability bit in the PmnPFS register.

Others: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Condition 2: When using the SDRAM area controller (SDRAMC).

BCLK = SDCLK = 8 to 120 MHz

VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, VREFH/VREFH0 = 3.0 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 15 pF

High drive output is selected in the port drive capability bit in the PmnPFS register.

Condition 3: When using the SDRAM area controller (SDRAMC) and CS area controller (CSC) simultaneously.

BCLK = SDCLK = 8 to 60 MHz

VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, VREFH/VREFH0 = 3.0 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 15 pF

High drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Max	Unit	Test conditions
Address delay	t_{AD}	-	12.5	ns	Figure 2.20 to Figure 2.25
Byte control delay	t_{BCD}	-	12.5	ns	
CS delay	t_{CSD}	-	12.5	ns	
ALE delay time	t_{ALED}	-	12.5	ns	
RD delay	t_{RSD}	-	12.5	ns	
Read data setup time	t_{RDS}	12.5	-	ns	
Read data hold time	t_{RDH}	0	-	ns	
WR/WRn delay	t_{WRD}	-	12.5	ns	
Write data delay	t_{WDD}	-	12.5	ns	
Write data hold time	t_{WDH}	0	-	ns	
WAIT setup time	t_{WTS}	12.5	-	ns	Figure 2.26
WAIT hold time	t_{WTH}	0	-	ns	

Table 2.18 Bus timing (2 of 2)

Condition 1: When using the CS area controller (CSC).

BCLK = 8 to 120 MHz, EBCLK = 8 to 60 MHz

VCC = AVCC0 = VCC_USB = VBATT = 2.7 to 3.6 V, VREFH/VREFH0 = 2.7 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 30 pF

EBCLK: High drive output is selected in the port drive capability bit in the PmnPFS register.

Others: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Condition 2: When using the SDRAM area controller (SDRAMC).

BCLK = SDCLK = 8 to 120 MHz

VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, VREFH/VREFH0 = 3.0 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 15 pF

High drive output is selected in the port drive capability bit in the PmnPFS register.

Condition 3: When using the SDRAM area controller (SDRAMC) and CS area controller (CSC) simultaneously.

BCLK = SDCLK = 8 to 60 MHz

VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, VREFH/VREFH0 = 3.0 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 15 pF

High drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Max	Unit	Test conditions
Address delay 2 (SDRAM)	t _{AD2}	0.8	6.8	ns	Figure 2.27 to Figure 2.33
CS delay 2 (SDRAM)	t _{CSD2}	0.8	6.8	ns	
DQM delay (SDRAM)	t _{DQMD}	0.8	6.8	ns	
CKE delay (SDRAM)	t _{CKED}	0.8	6.8	ns	
Read data setup time 2 (SDRAM)	t _{RDS2}	2.9	-	ns	
Read data hold time 2 (SDRAM)	t _{RDH2}	1.5	-	ns	
Write data delay 2 (SDRAM)	t _{WDD2}	-	6.8	ns	
Write data hold time 2 (SDRAM)	t _{WDH2}	0.8	-	ns	
WE delay (SDRAM)	t _{WED}	0.8	6.8	ns	
RAS delay (SDRAM)	t _{RASD}	0.8	6.8	ns	
CAS delay (SDRAM)	t _{CASD}	0.8	6.8	ns	

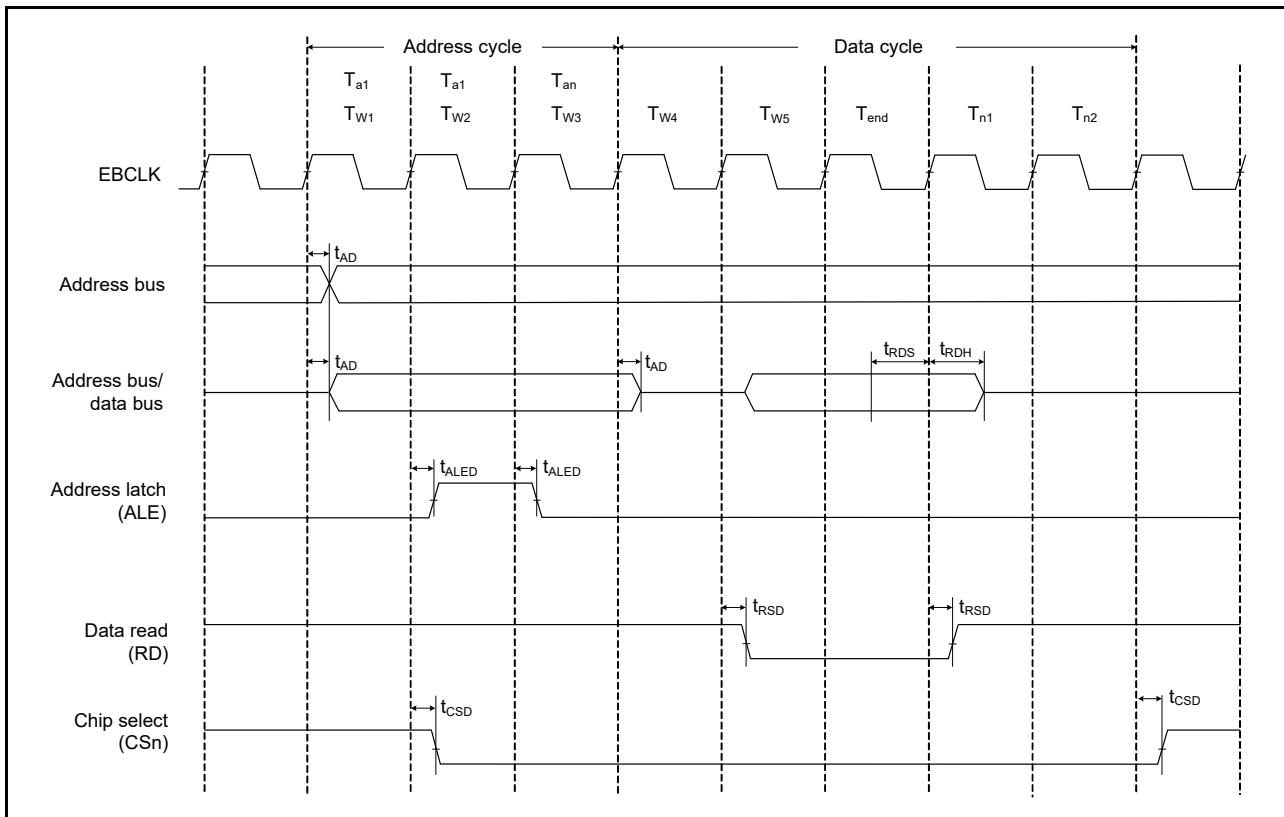


Figure 2.20 Address/data multiplexed bus read access timing

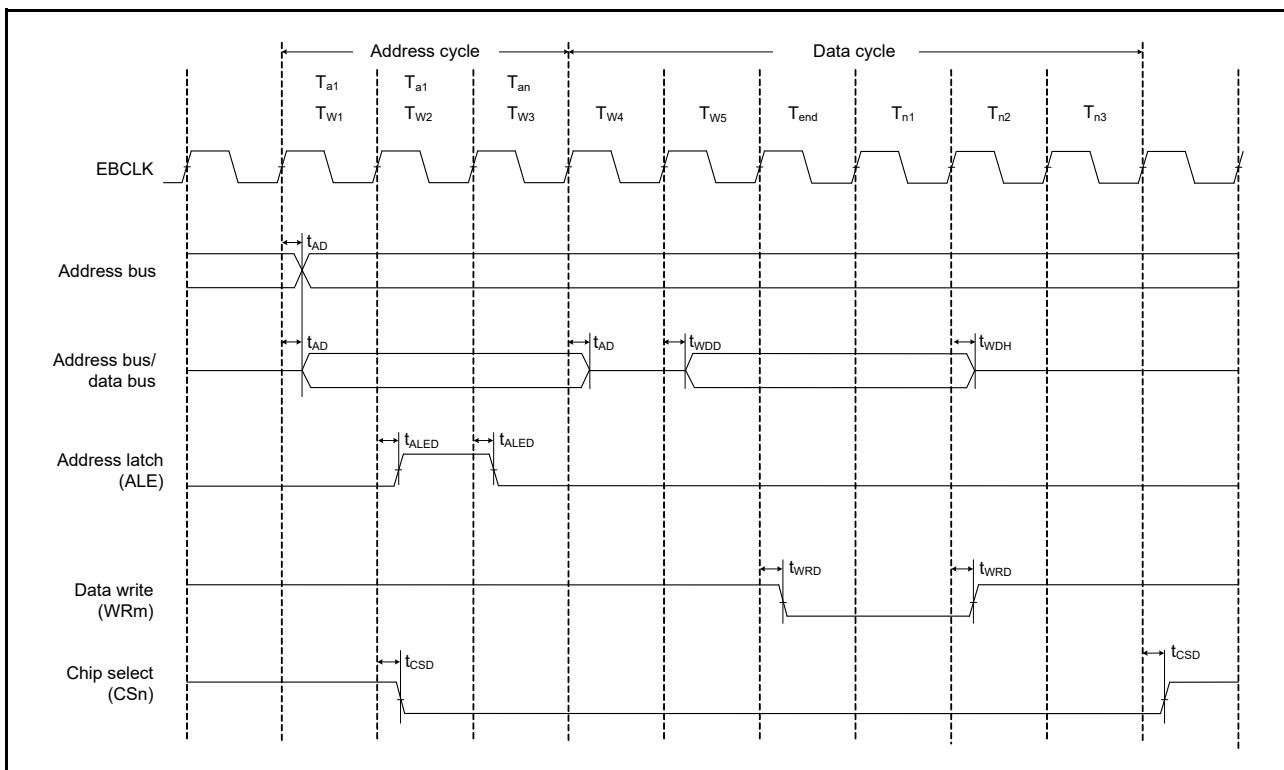


Figure 2.21 Address/data multiplexed bus write access timing

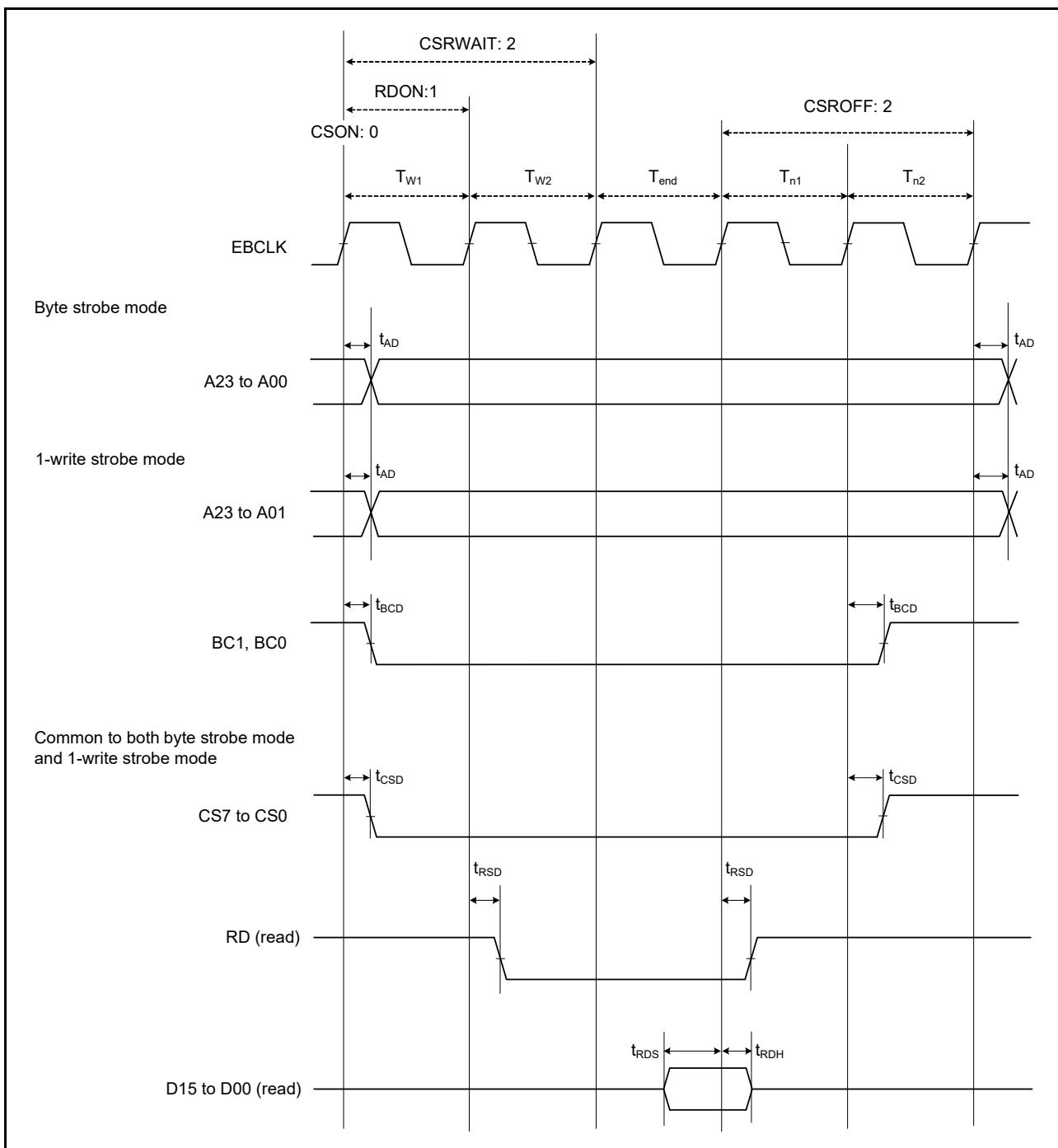


Figure 2.22 External bus timing for normal read cycle with bus clock synchronized

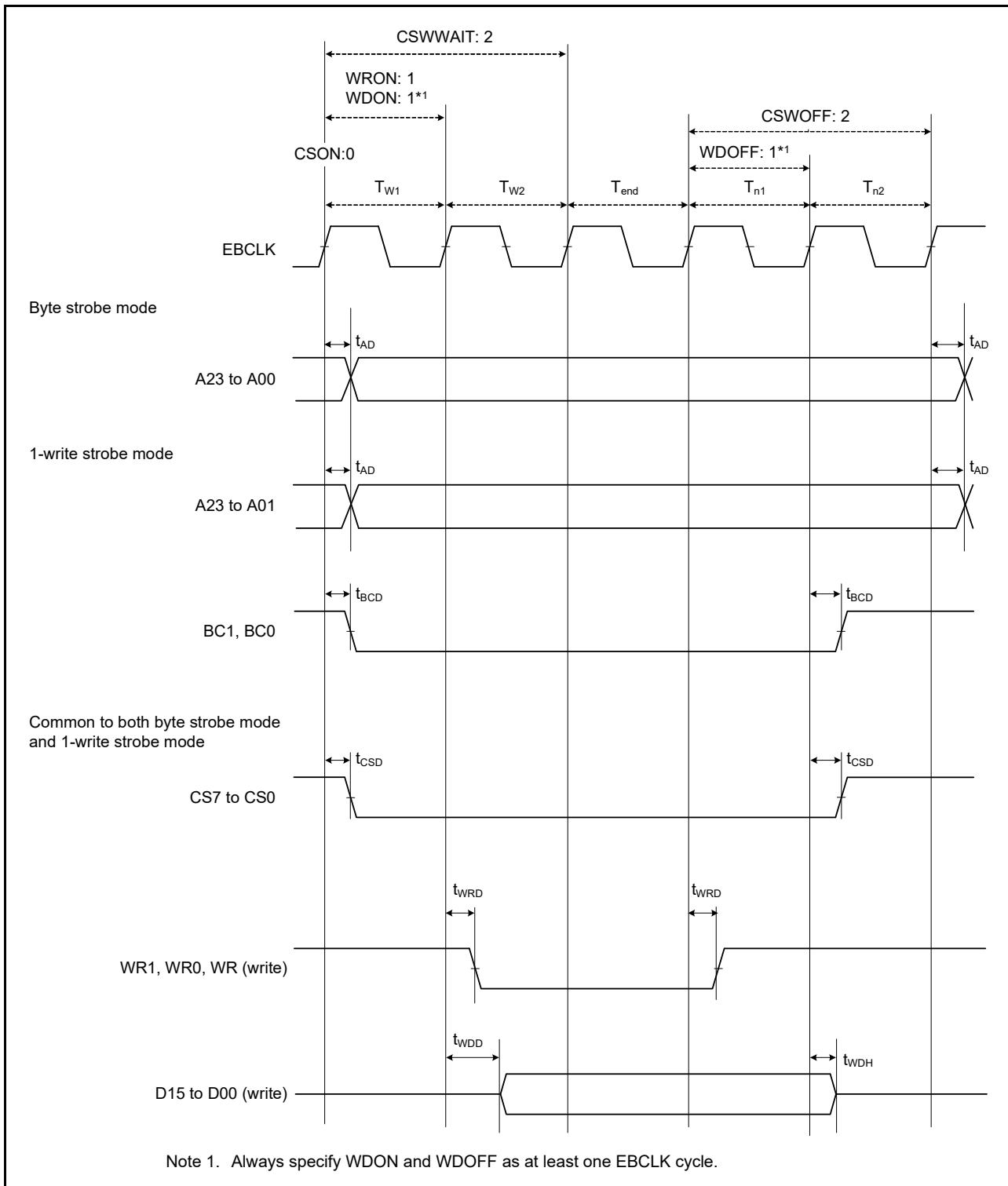


Figure 2.23 External bus timing for normal write cycle with bus clock synchronized

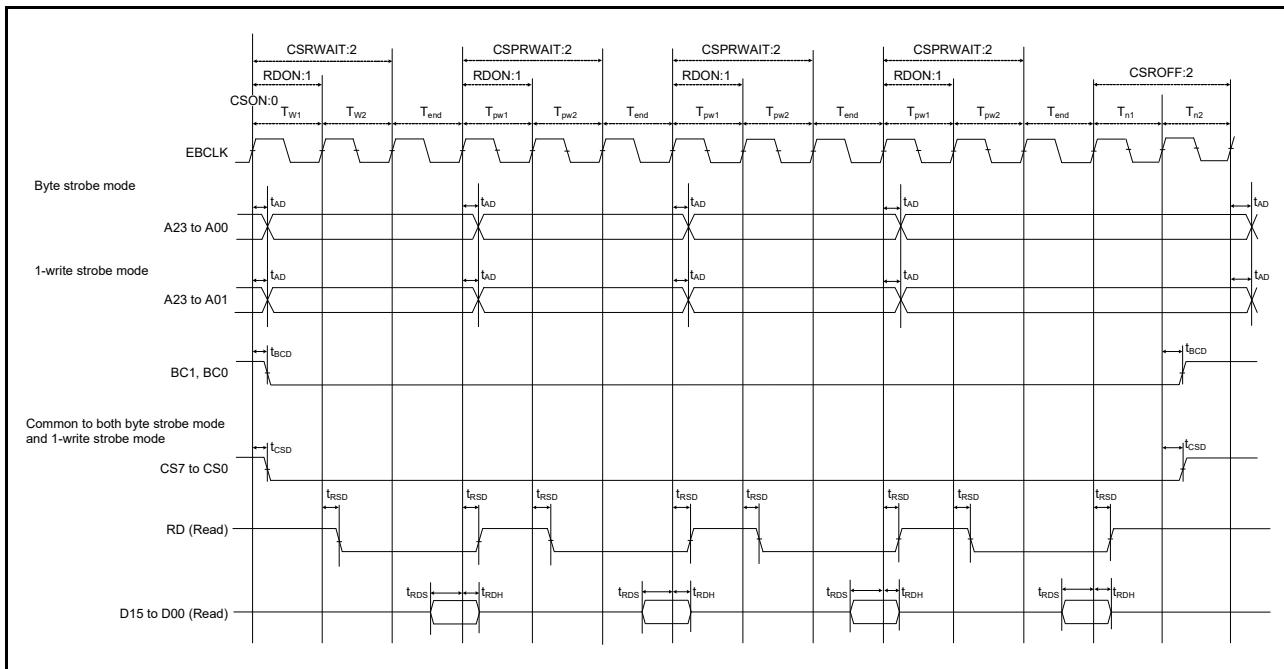


Figure 2.24 External bus timing for page read cycle with bus clock synchronized

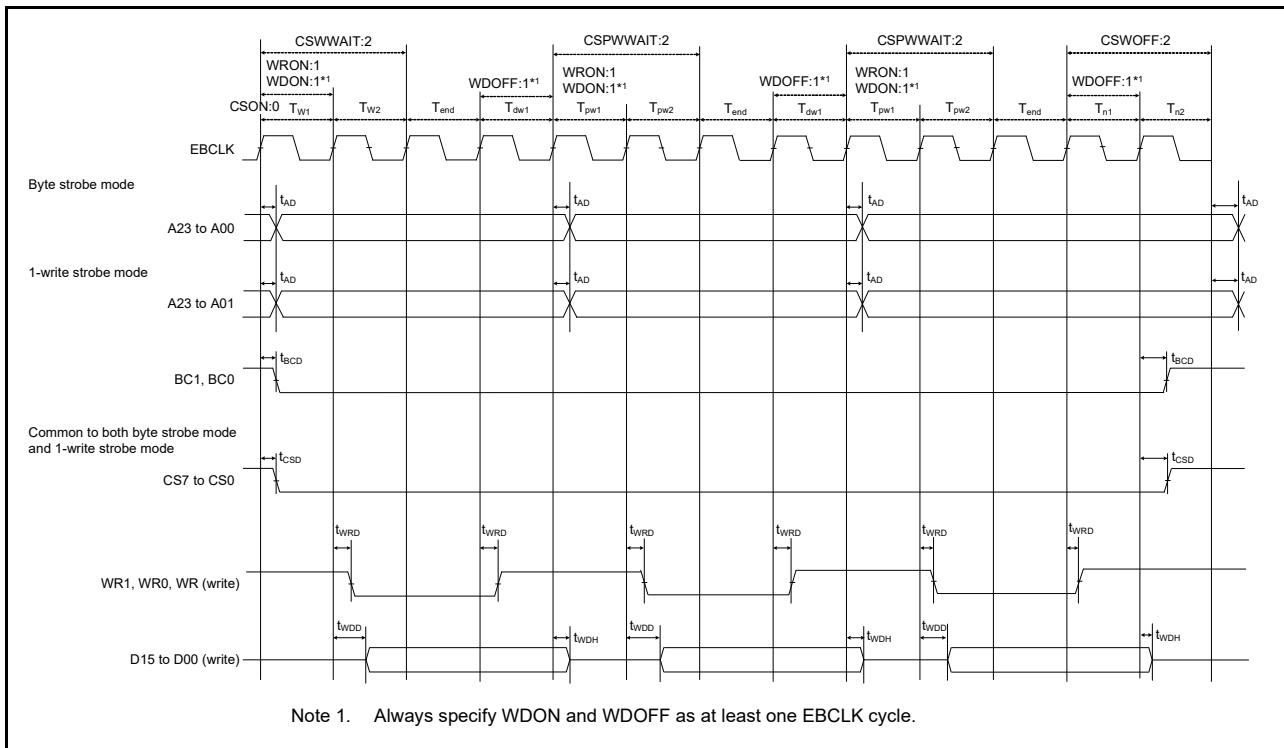


Figure 2.25 External bus timing for page write cycle with bus clock synchronized

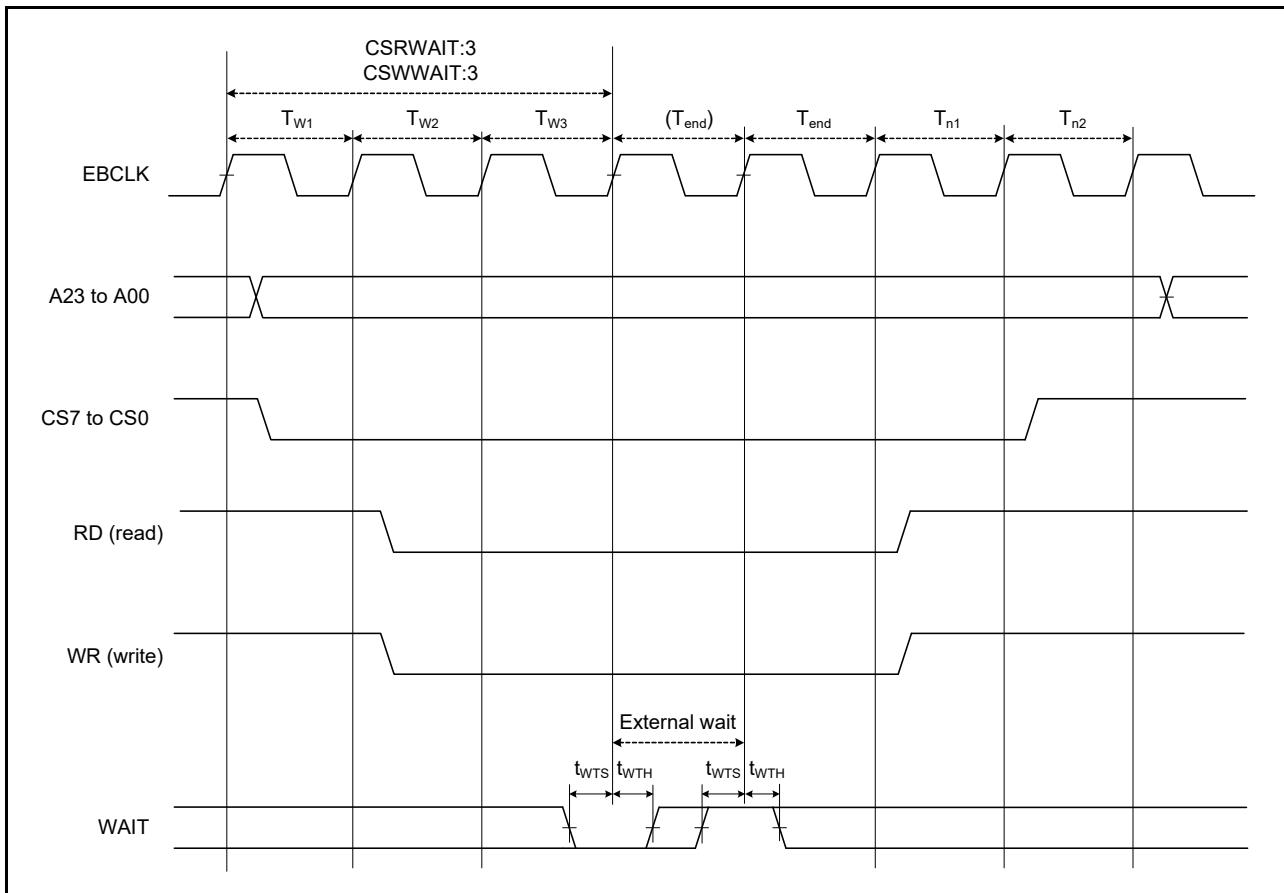


Figure 2.26 External bus timing for external wait control

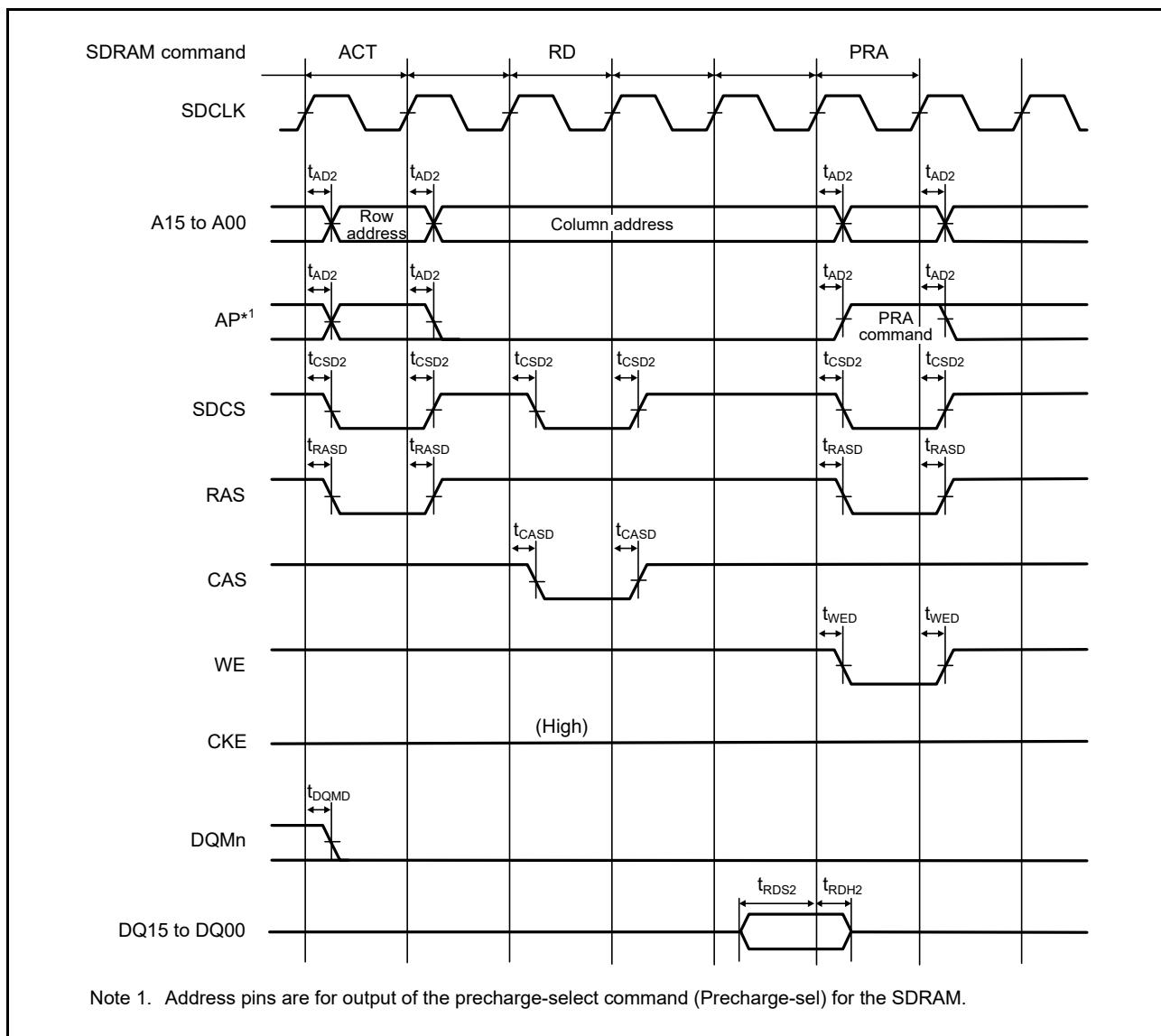


Figure 2.27 SDRAM single read timing

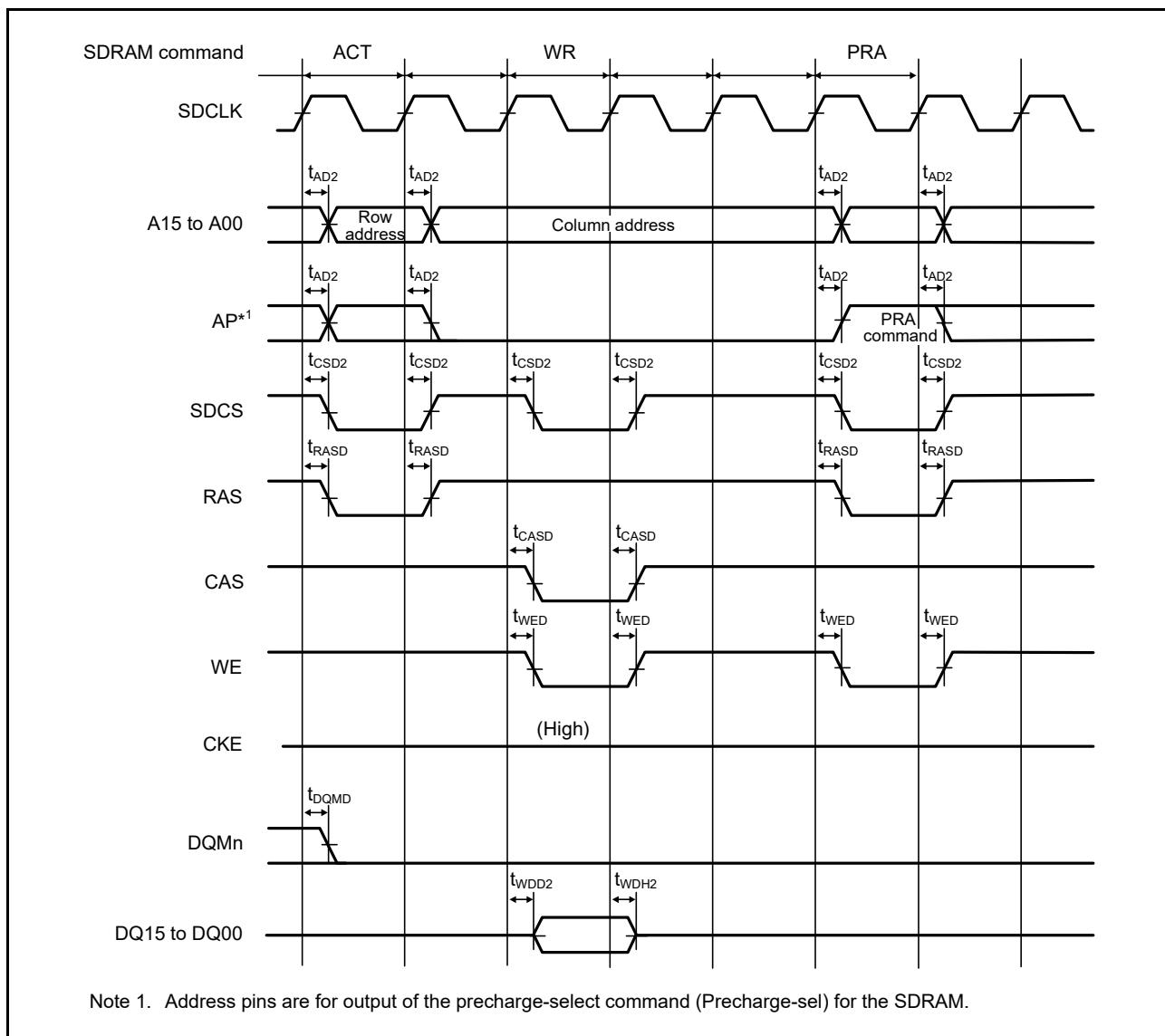


Figure 2.28 SDRAM single write timing

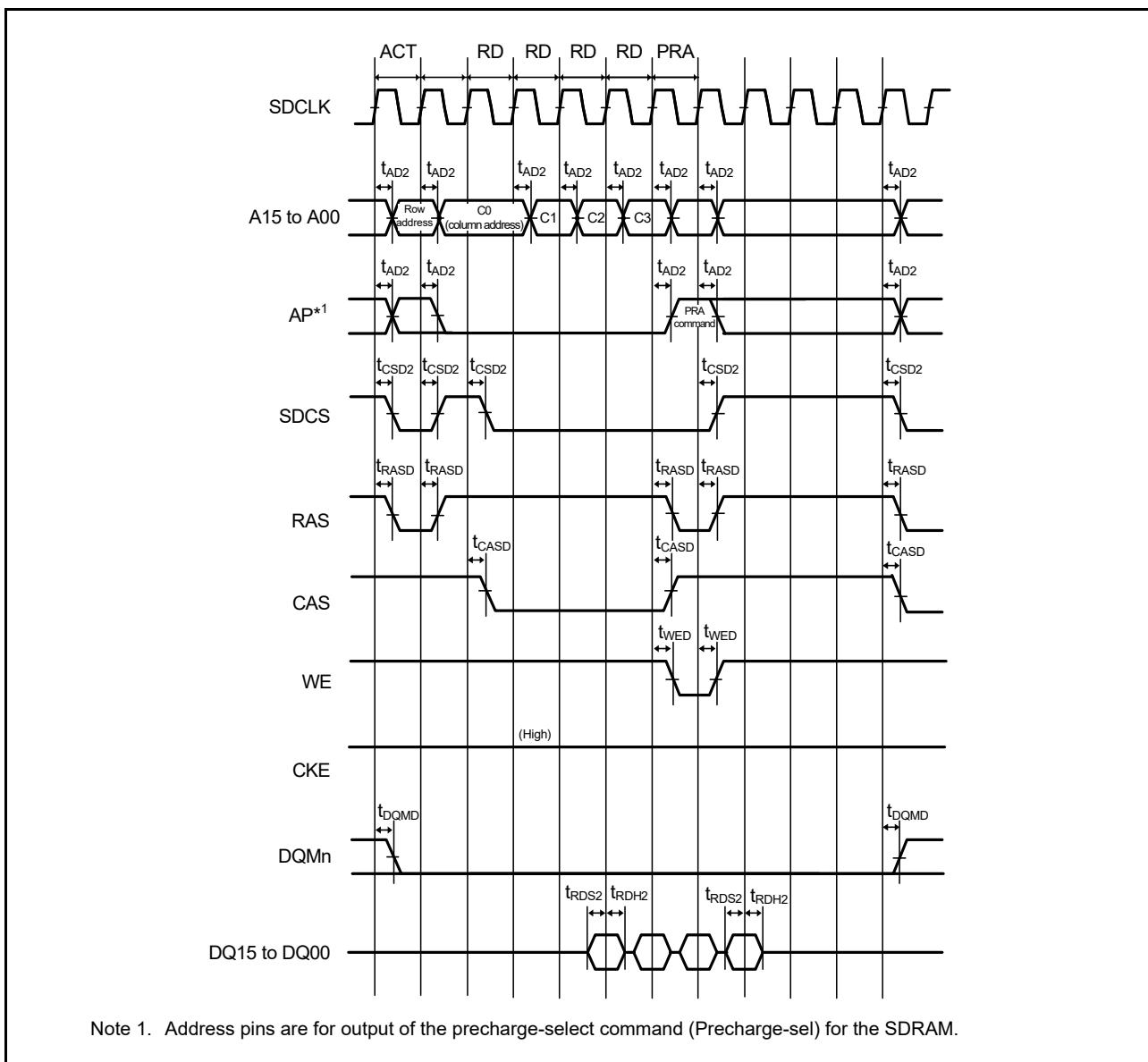


Figure 2.29 SDRAM multiple read timing

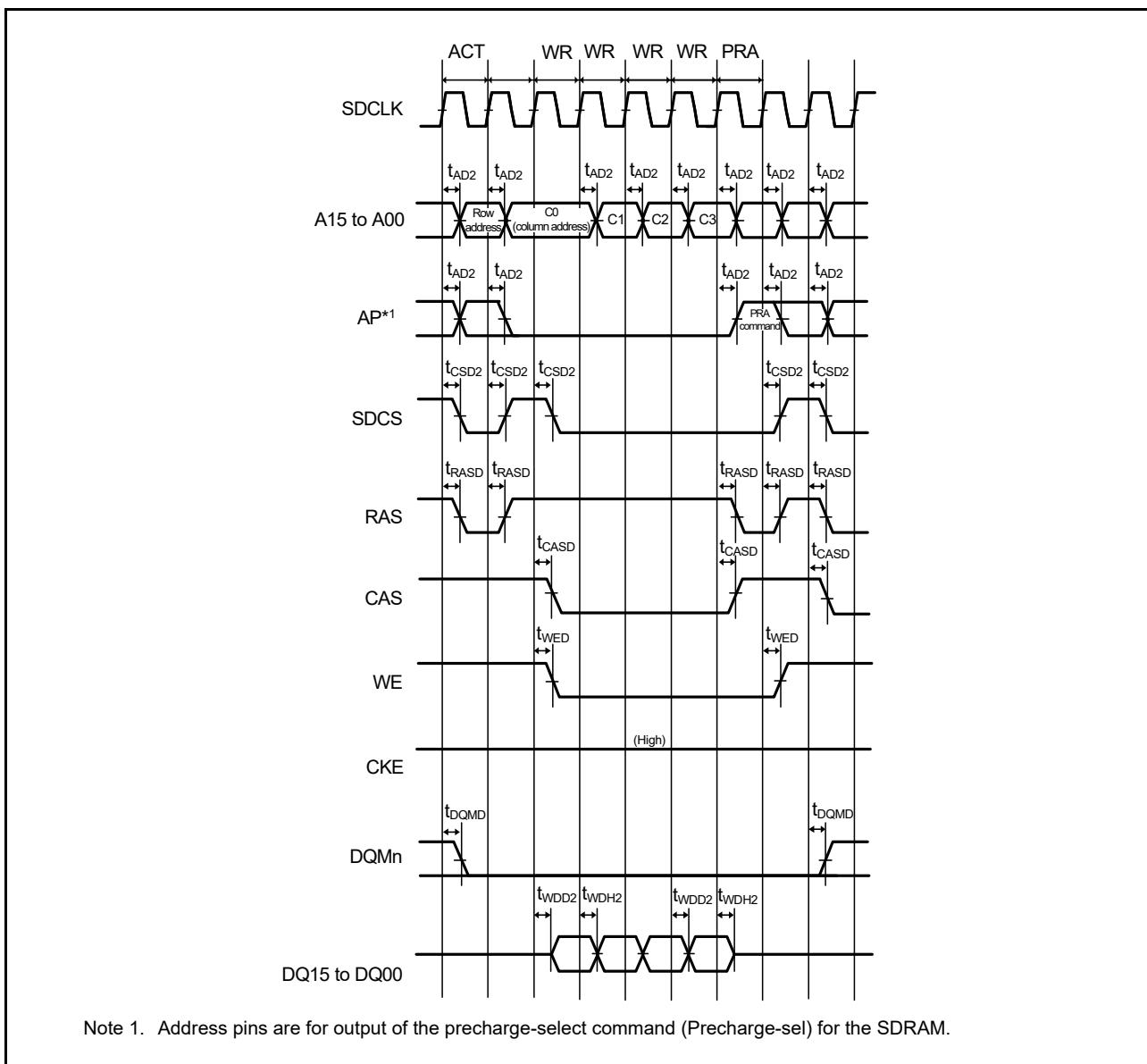


Figure 2.30 SDRAM multiple write timing

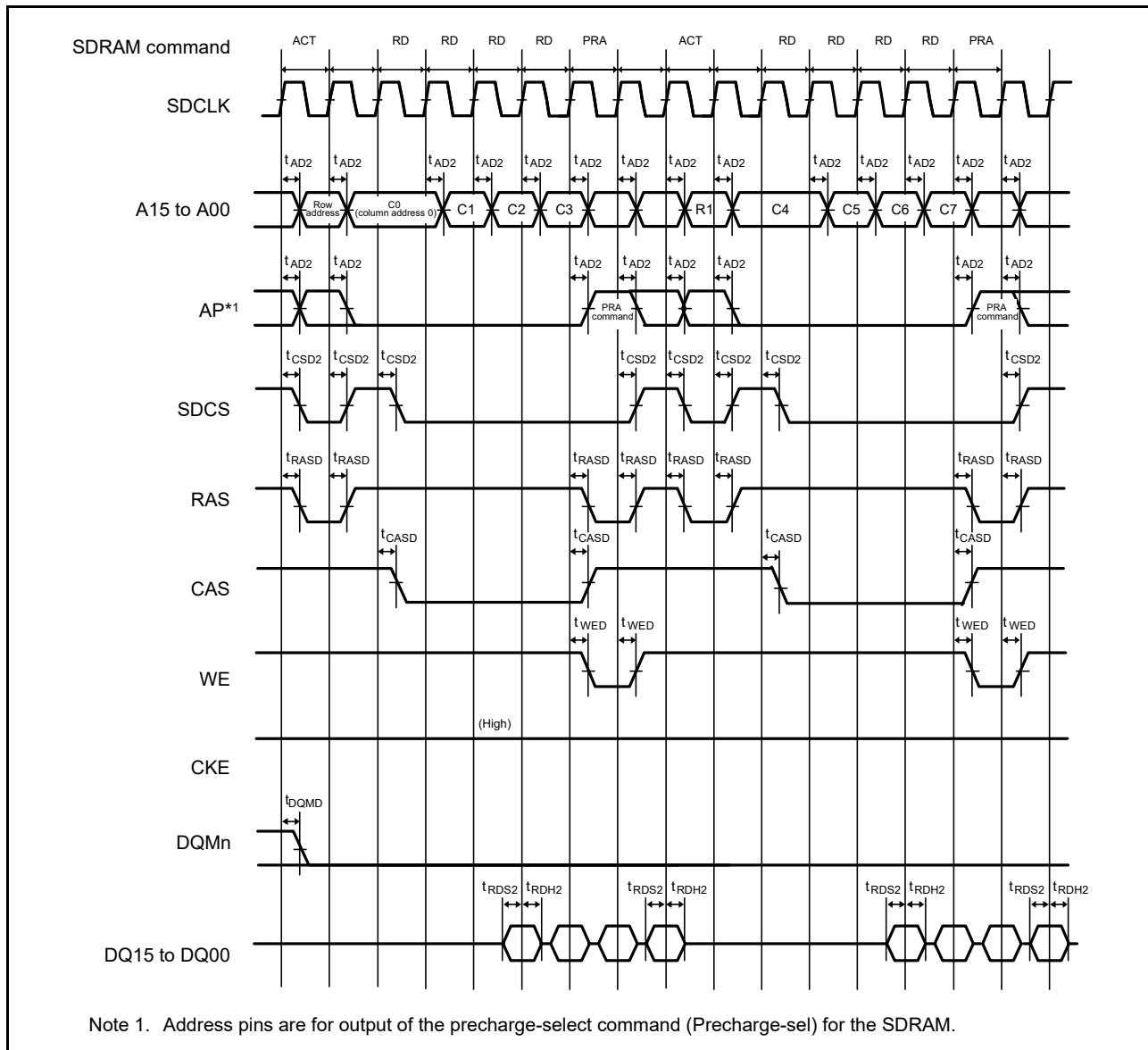
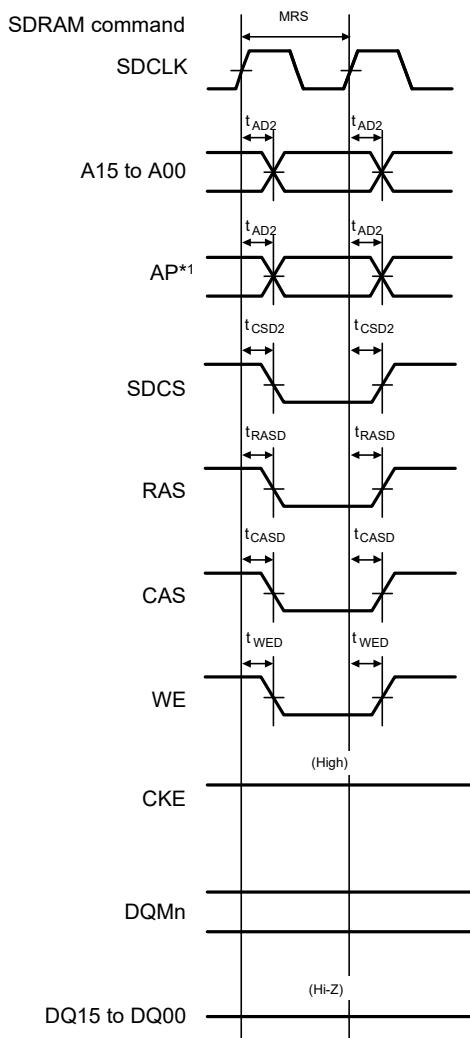
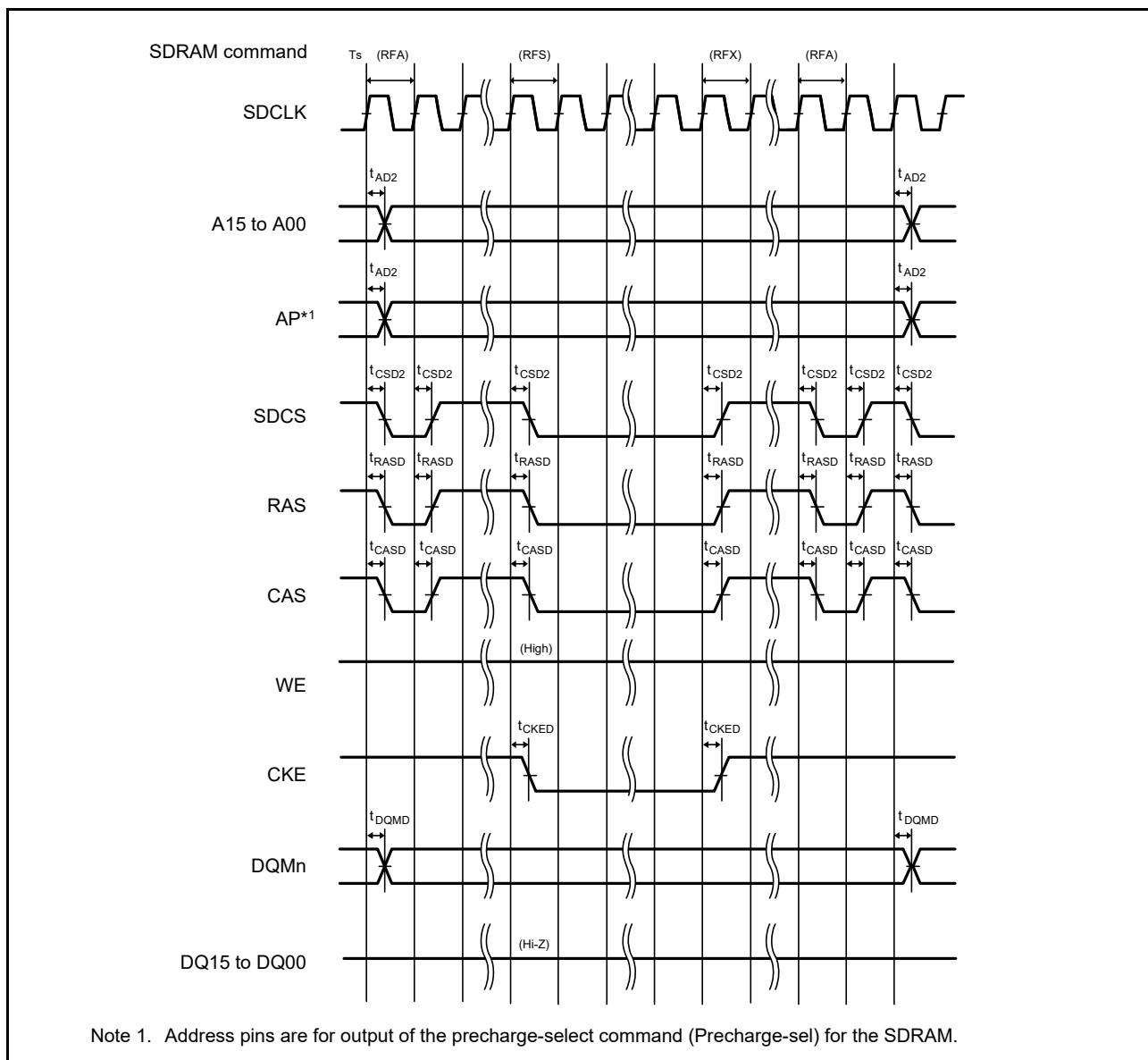


Figure 2.31 SDRAM multiple read line stride timing



Note 1. Address pins are for output of the precharge-select command (Precharge-sel) for the SDRAM.

Figure 2.32 SDRAM mode register set timing

**Figure 2.33 SDRAM self-refresh timing****2.3.7 I/O Ports, POEG, GPT32, AGT, KINT, and ADC12 Trigger Timing****Table 2.19 I/O ports, POEG, GPT32, AGT, KINT, and ADC12 trigger timing (1 of 2)**

GPT32 Conditions:

High drive output is selected in the port drive capability bit in the PmnPFS register.

AGT Conditions:

Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min	Max	Unit	Test conditions
I/O ports	Input data pulse width	t_{PRW}	1.5	-	t_{Pcyc}	Figure 2.34
POEG	POEG input trigger pulse width	t_{POEW}	3	-	t_{Pcyc}	Figure 2.35

Table 2.19 I/O ports, POEG, GPT32, AGT, KINT, and ADC12 trigger timing (2 of 2)

GPT32 Conditions:

High drive output is selected in the port drive capability bit in the PmnPFS register.

AGT Conditions:

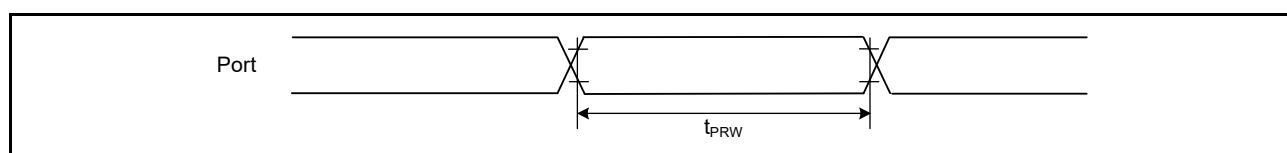
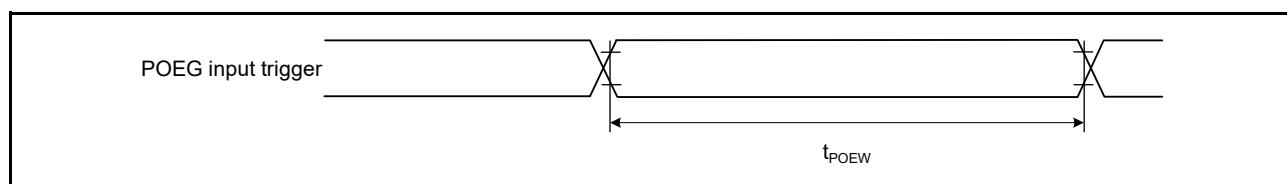
Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min	Max	Unit	Test conditions
GPT32	Input capture pulse width	Single edge	t_{GTICW}	1.5	-	t_{PDcyc}
				2.5	-	
	GTIOC _x Y output skew (x = 0 to 7, Y= A or B)	Middle drive buffer	t_{GTISK}^{*2}	-	4	
		High drive buffer		-	4	
	GTIOC _x Y output skew (x = 8 to 13, Y = A or B)	Middle drive buffer		-	4	
		High drive buffer		-	4	
	GTIOC _x Y output skew (x = 0 to 13, Y = A or B)	Middle drive buffer	t_{GTISK}	-	6	
		High drive buffer		-	6	
	OPS output skew GTOUUP, GTOULO, GTOVUP, GTOVLO, GTOWUP, GTOWLO		t_{GTOSK}	-	5	ns
GPT(PWM Delay Generation Circuit)	GTIOC _x Y_Z output skew (x = 0 to 3, Y = A or B, Z = A)		t_{HRSK}^{*3}	-	2.0	ns
AGT	AGTIO, AGTEE input cycle		t_{ACYC}^{*4}	100	-	ns
	AGTIO, AGTEE input high width, low width		t_{ACKWH}, t_{ACKWL}	40	-	ns
	AGTIO, AGTO, AGTOA, AGTOB output cycle		t_{ACYC2}	62.5	-	ns
ADC12	ADC12 trigger input pulse width		t_{TRGW}	1.5	-	t_{Pcyc}
KINT	KR _n (n = 00 to 07) pulse width		t_{KR}	250	-	ns

Note 1. t_{Pcyc} : PCLKB cycle, t_{PDcyc} : PCLKD cycle.

Note 2. This skew applies when the same driver I/O is used. If the I/O of the middle and high drivers is mixed, operation is not guaranteed.

Note 3. The load is 30 pF.

Note 4. Constraints on AGTIO input: $t_{Pcyc} \times 2$ (t_{Pcyc} : PCLKB cycle) < t_{ACYC} .**Figure 2.34 I/O ports input timing****Figure 2.35 POEG input trigger timing**

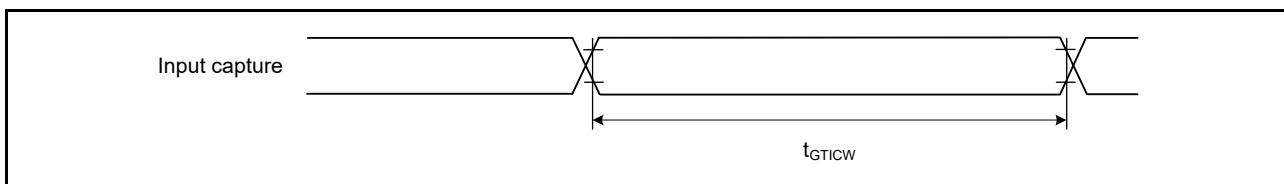


Figure 2.36 GPT32 input capture timing

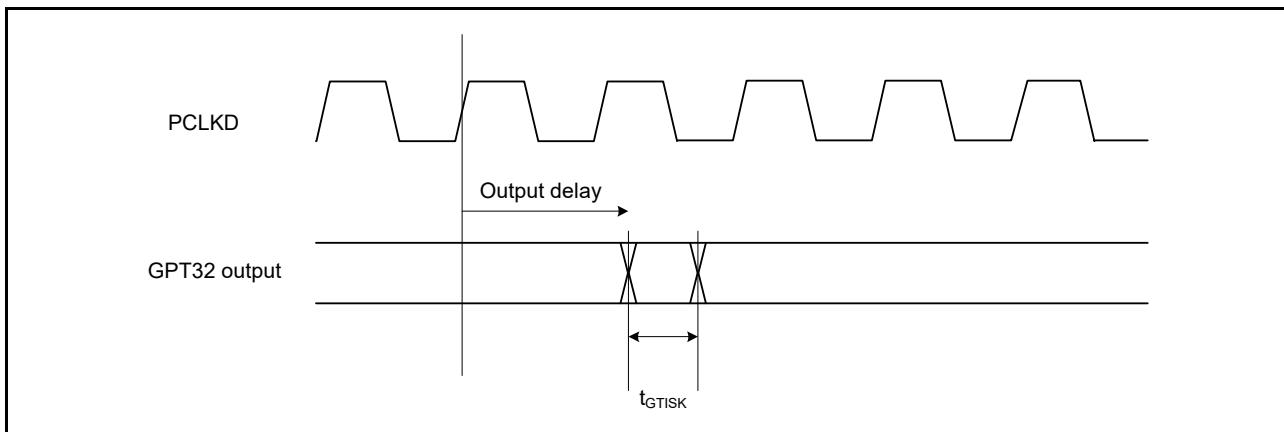


Figure 2.37 GPT32 output delay skew

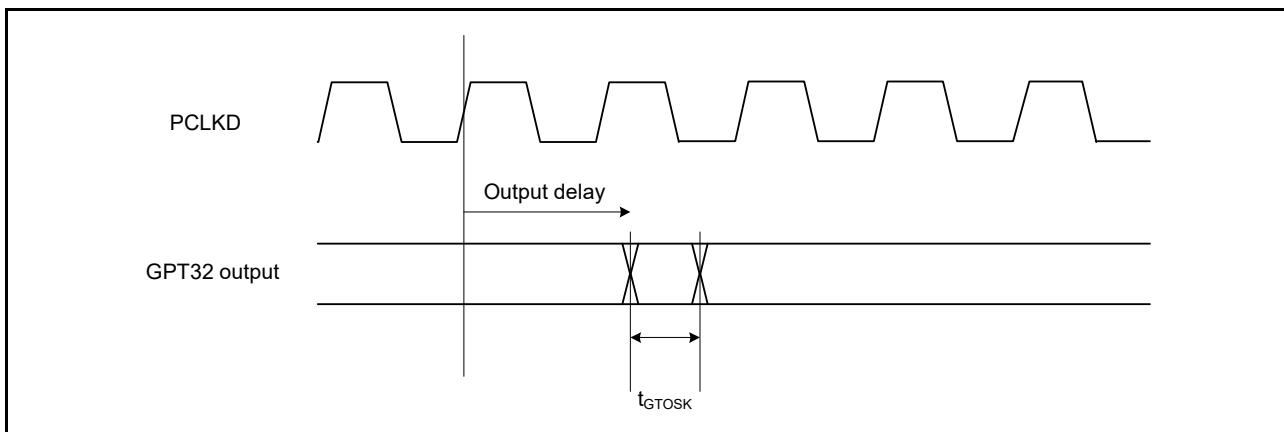


Figure 2.38 GPT32 output delay skew for OPS

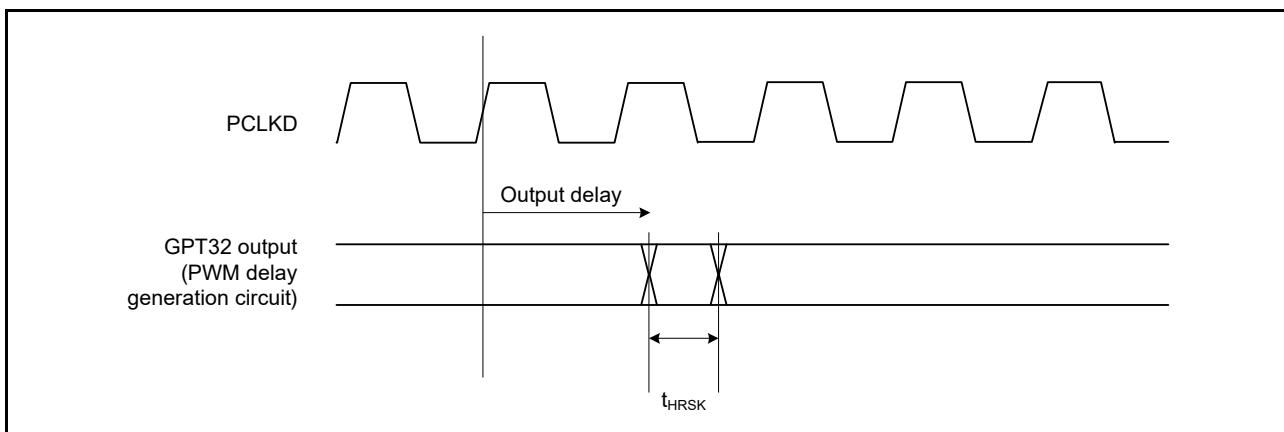


Figure 2.39 GPT32 (PWM Delay Generation Circuit) output delay skew

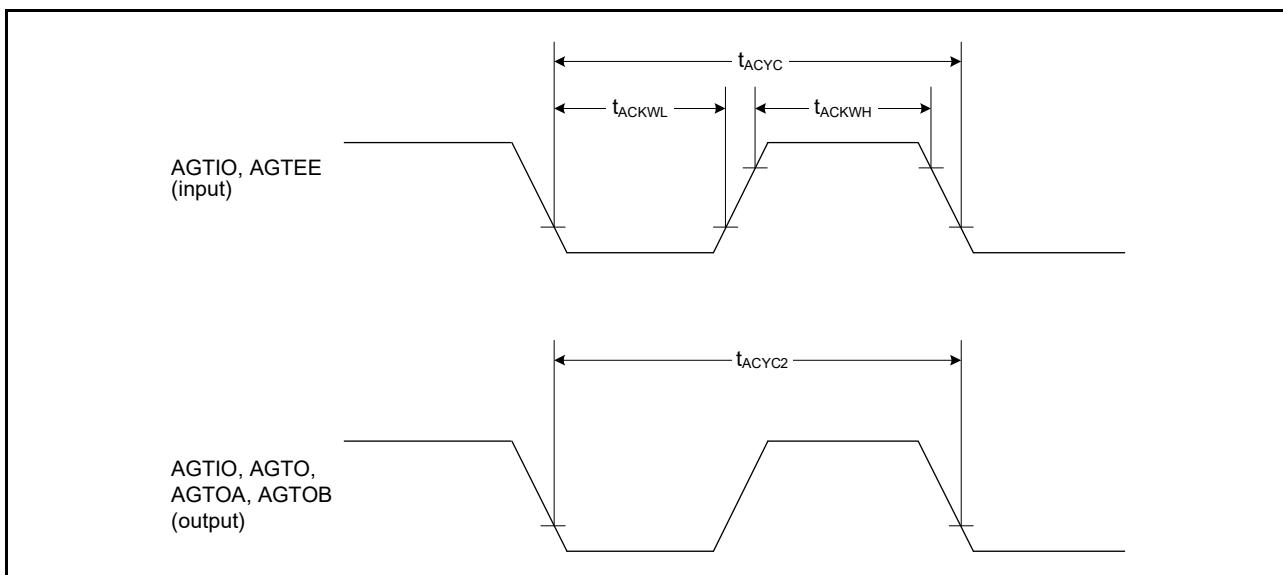


Figure 2.40 AGT input/output timing

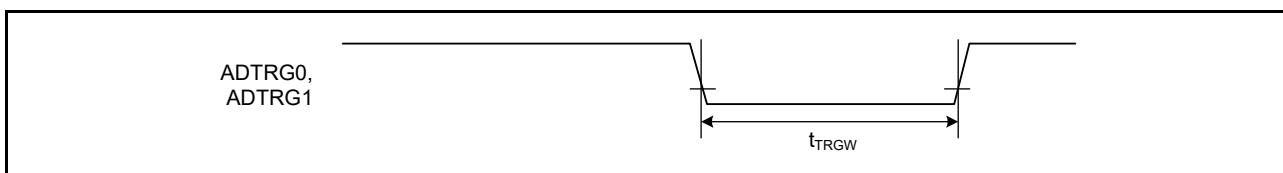


Figure 2.41 ADC12 trigger input timing

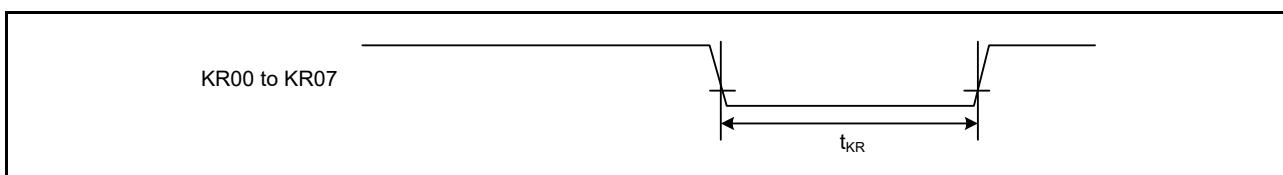


Figure 2.42 Key interrupt input timing

2.3.8 PWM Delay Generation Circuit Timing

Table 2.20 PWM Delay Generation Circuit timing

Parameter	Min	Typ	Max	Unit	Test conditions
Operation frequency	80	-	120	MHz	-
Resolution	-	260	-	ps	PCLKD = 120 MHz
DNL*1	-	± 2.0	-	LSB	-

Note 1. This value normalizes the differences between lines in 1-LSB resolution.

2.3.9 CAC Timing

Table 2.21 CAC timing

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
CAC	CACREF input pulse width $t_{PBcyc} \leq t_{cac}^*$	t_{CACREF}	$4.5 \times t_{cac} + 3 \times t_{PBcyc}$	-	-	ns	-
	$t_{PBcyc} > t_{cac}^*$		$5 \times t_{cac} + 6.5 \times t_{PBcyc}$	-	-	ns	

Note 1. t_{PBcyc} : PCLKB cycle.

Note 2. t_{cac} : CAC count clock source cycle.

2.3.10 SCI Timing

Table 2.22 SCI timing (1)

Conditions: High drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SCK0 to SCK9. For other pins, middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter			Symbol	Min	Max	Unit ^{*1}	Test conditions	
SCI	Input clock cycle	Asynchronous	t_{Scyc}	4	-	t_{Pcyc}	Figure 2.43	
		Clock synchronous		6	-			
	Input clock pulse width		t_{SCKW}	0.4	0.6	t_{Scyc}		
	Input clock rise time		t_{SCKr}	-	5	ns		
	Input clock fall time		t_{SCKf}	-	5	ns		
	Output clock cycle	Asynchronous	t_{Scyc}	6	-	t_{Pcyc}		
		Clock synchronous		4	-			
	Output clock pulse width		t_{SCKW}	0.4	0.6	t_{Scyc}		
	Output clock rise time		t_{SCKr}	-	5	ns		
	Output clock fall time		t_{SCKf}	-	5	ns		
	Transmit data delay	Clock synchronous	t_{TXD}	-	25	ns	Figure 2.44	
	Receive data setup time	Clock synchronous	t_{RXS}	15	-	ns		
	Receive data hold time	Clock synchronous	t_{RXH}	5	-	ns		

Note 1. t_{Pcyc} : PCLKA cycle.

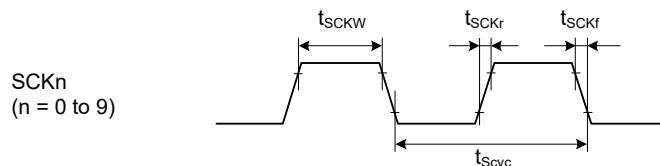
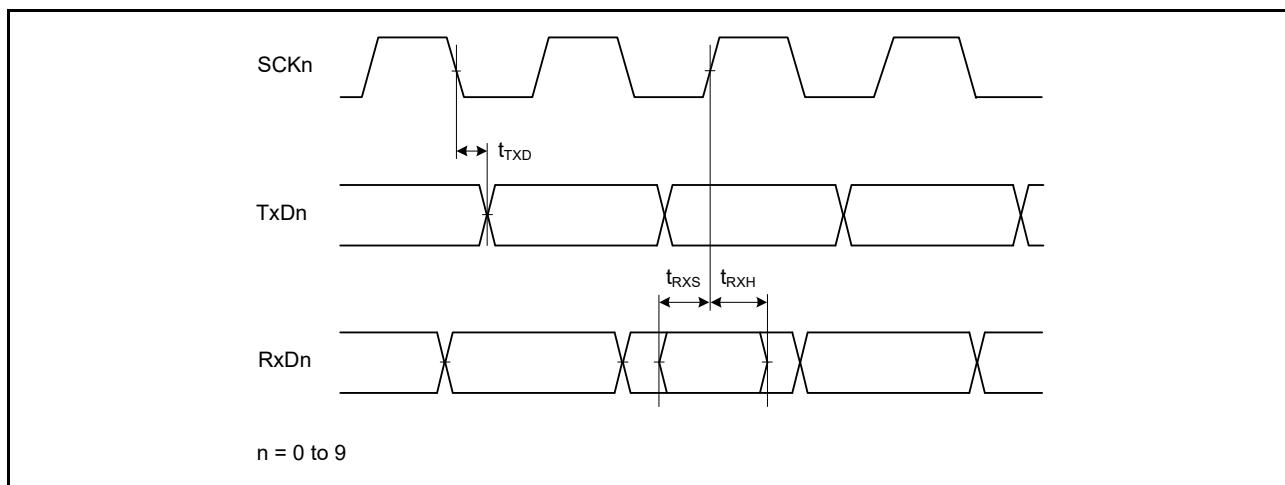


Figure 2.43 SCK clock input/output timing

**Figure 2.44** SCI input/output timing in clock synchronous mode**Table 2.23** SCI timing (2)

Conditions: High drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SCK0 to SCK9. For other pins, middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Max	Unit	Test conditions
Simple SPI	SCK clock cycle output (master)	t_{SPCyc}	4 (PCLKA \leq 60 MHz) 8 (PCLKA > 60 MHz)	65536	Figure 2.45 Figure 2.46 to Figure 2.49 Figure 2.49
	SCK clock cycle input (slave)	-	6 (PCLKA \leq 60 MHz) 12 (PCLKA > 60 MHz)	65536	
	SCK clock high pulse width	t_{SPCKWH}	0.4	0.6	
	SCK clock low pulse width	t_{SPCKWL}	0.4	0.6	
	SCK clock rise and fall time	t_{SPCKR}, t_{SPCKF}	-	20	
	Data input setup time	t_{SU}	33.3	-	
	Data input hold time	t_H	33.3	-	
	SS input setup time	t_{LEAD}	1	-	
	SS input hold time	t_{LAG}	1	-	
	Data output delay	t_{OD}	-	33.3	
	Data output hold time	t_{OH}	-10	-	
	Data rise and fall time	t_{DR}, t_{DF}	-	16.6	
	SS input rise and fall time	t_{SSLR}, t_{SSLf}	-	16.6	
	Slave access time	t_{SA}	-	4 (PCLKA \leq 60 MHz) 8 (PCLKA > 60 MHz)	Figure 2.49
	Slave output release time	t_{REL}	-	5 (PCLKA \leq 60 MHz) 10 (PCLKA > 60 MHz)	

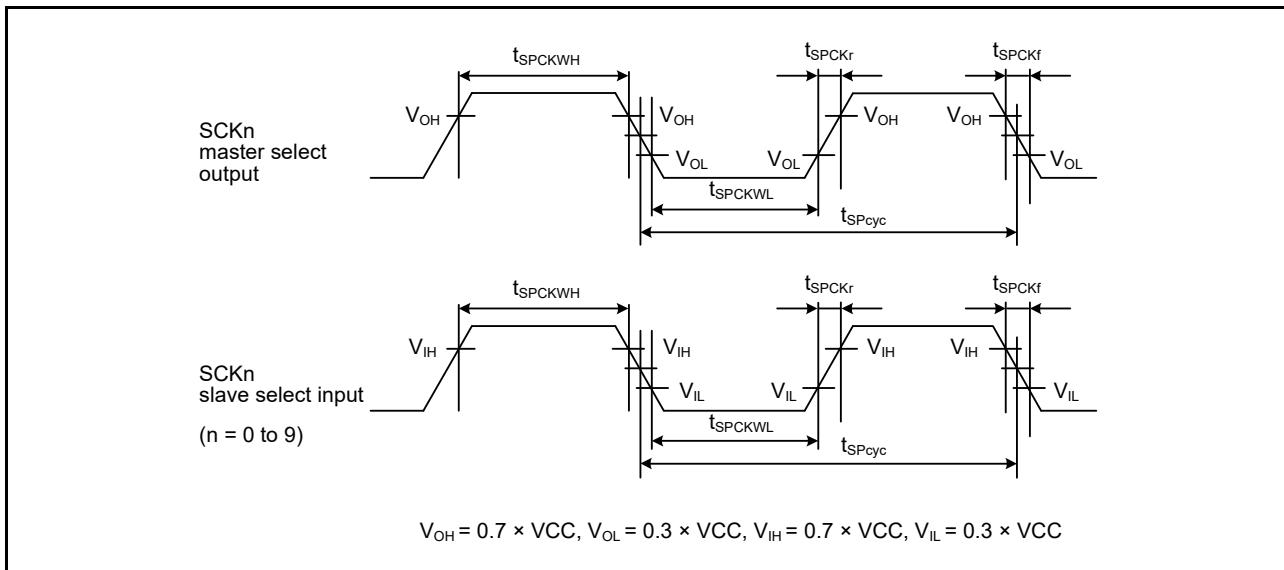


Figure 2.45 SCI simple SPI mode clock timing

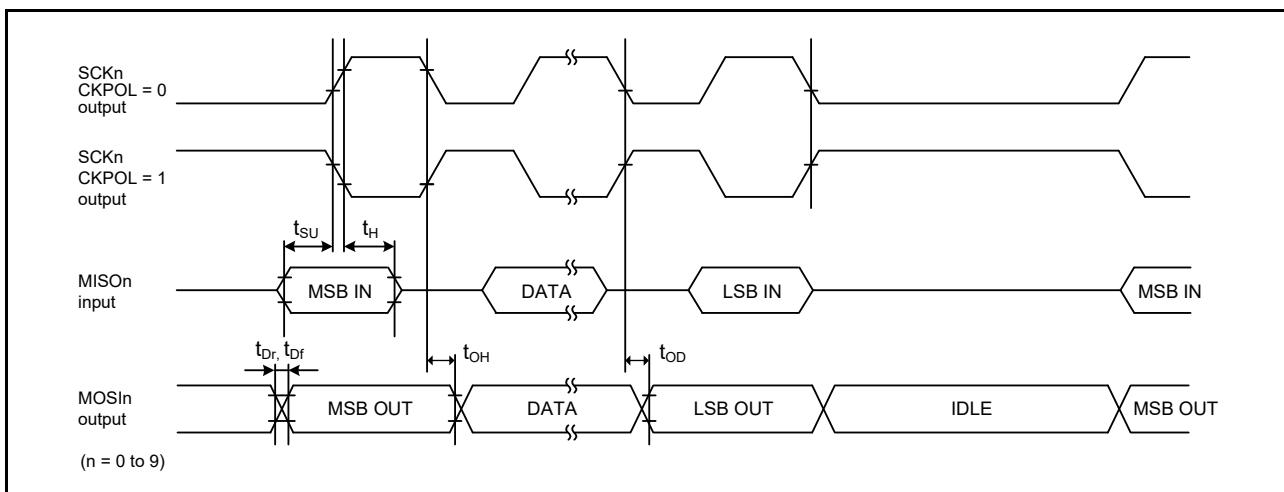


Figure 2.46 SCI simple SPI mode timing for master when CKPH = 1

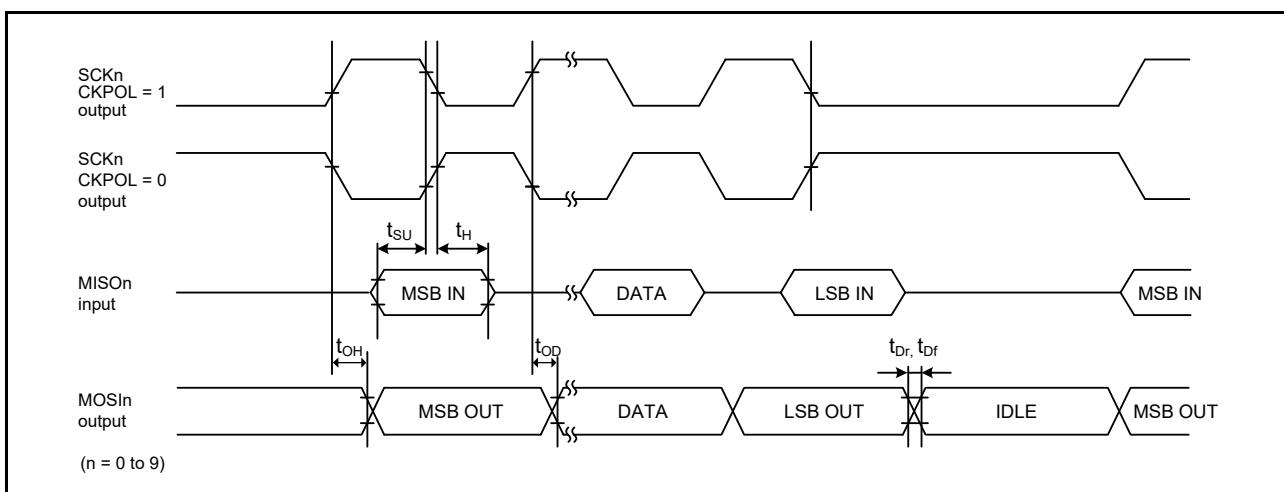


Figure 2.47 SCI simple SPI mode timing for master when CKPH = 0

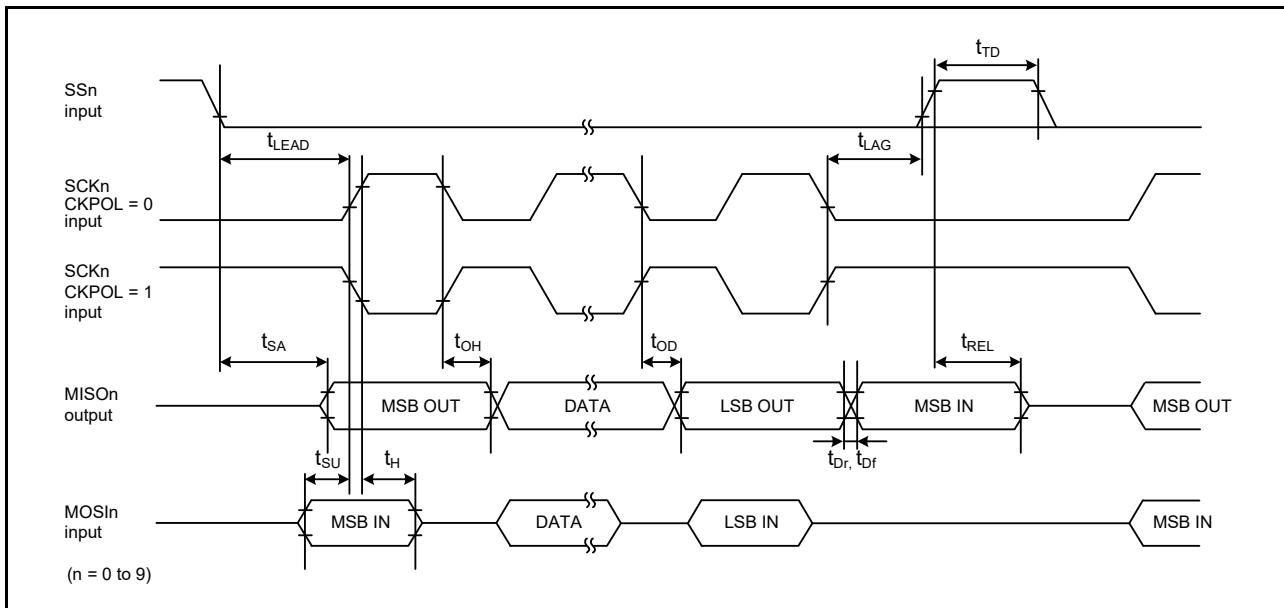


Figure 2.48 SCI simple SPI mode timing for slave when CKPH = 1

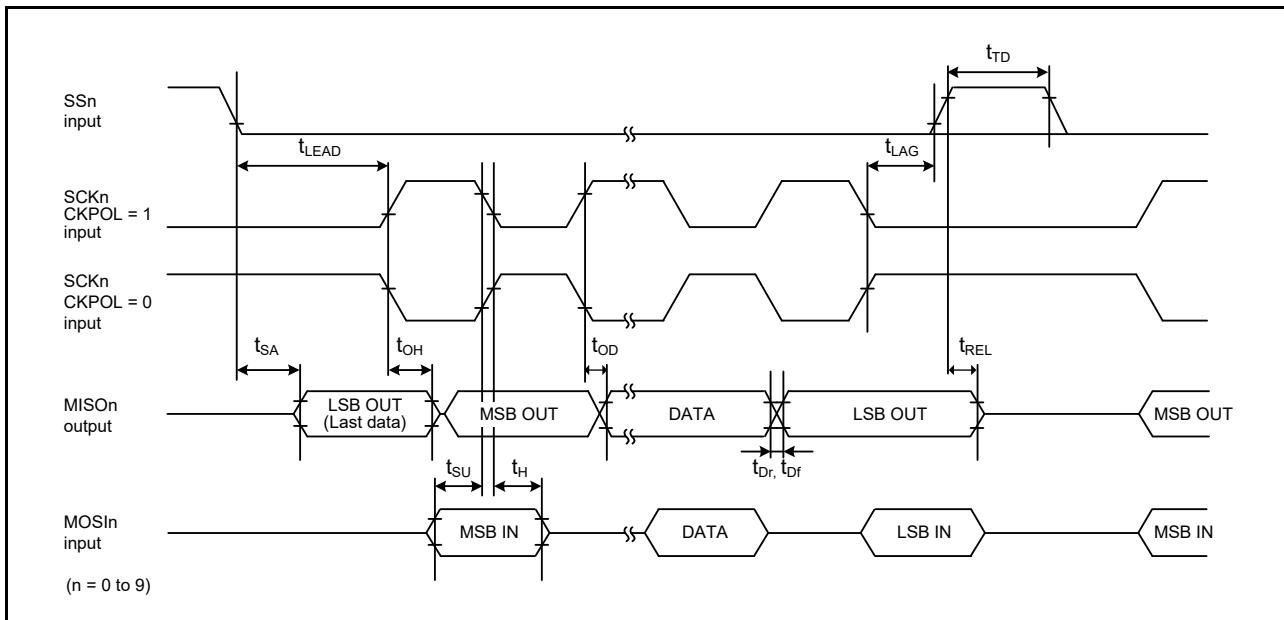


Figure 2.49 SCI simple SPI mode timing for slave when CKPH = 0

Table 2.24 SCI timing (3) (1 of 2)

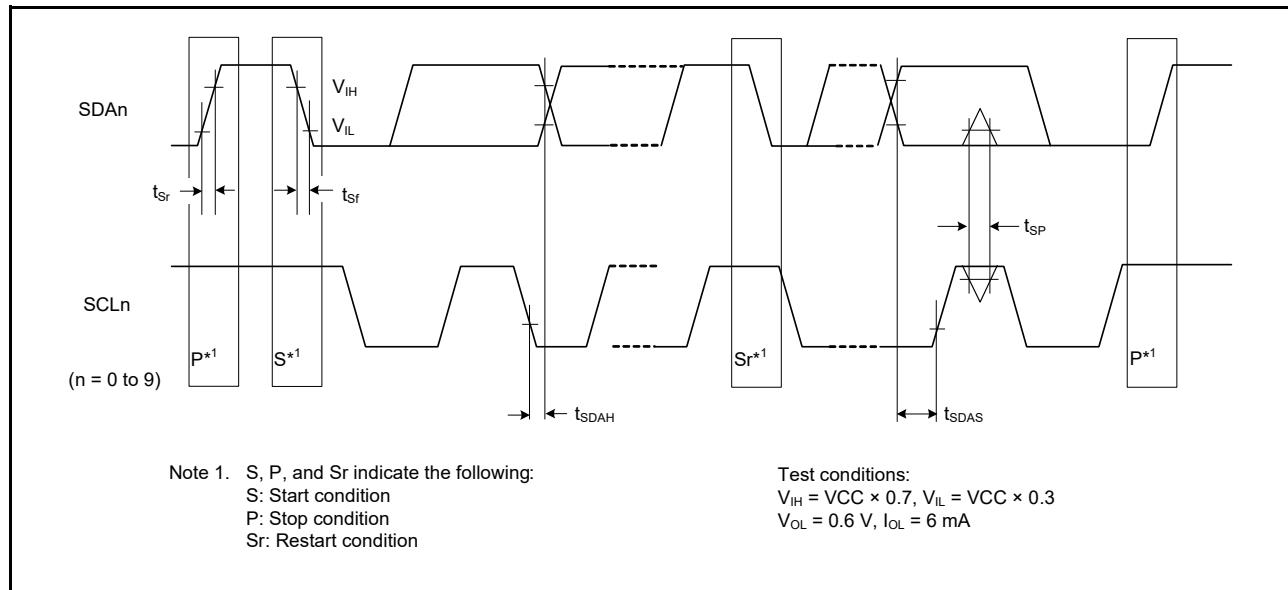
Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Max	Unit	Test conditions
Simple IIC (Standard mode)	SDA input rise time	t_{Sr}	-	1000	Figure 2.50
	SDA input fall time	t_{Sf}	-	300	
	SDA input spike pulse removal time	t_{SP}	0	$4 \times t_{IICcyc}$	
	Data input setup time	t_{SDAS}	250	-	
	Data input hold time	t_{SDAH}	0	-	
	SCL, SDA capacitive load	C_b^*	-	400	

Table 2.24 SCI timing (3) (2 of 2)

Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Max	Unit	Test conditions
Simple IIC (Fast mode)	SDA input rise time	t_{Sr}	-	300	ns
	SDA input fall time	t_{Sf}	-	300	ns
	SDA input spike pulse removal time	t_{SP}	0	$4 \times t_{IICcyc}$	ns
	Data input setup time	t_{SDAS}	100	-	ns
	Data input hold time	t_{SDAH}	0	-	ns
	SCL, SDA capacitive load	$C_b^*{}^1$	-	400	pF

Note: t_{IICcyc} : IIC internal reference clock (IIC ϕ) cycle.Note 1. C_b indicates the total capacity of the bus line.**Figure 2.50 SCI simple IIC mode timing**

2.3.11 SPI Timing

Table 2.25 SPI timing

Conditions:

For RSPCKA and RSPCKB pins, high drive output is selected with the port drive capability bit in the PmnPFS register.

For other pins, middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min	Max	Unit ^{*1}	Test conditions ^{*2}
SPI	RSPCK clock cycle	Master	t_{SPCyc}	2 (PCLKA \leq 60 MHz) 4 (PCLKA > 60 MHz)	4096	Figure 2.51 $C = 30 \text{ pF}$
		Slave		4	4096	
	RSPCK clock high pulse width	Master	t_{SPCKWH}	$(t_{SPCyc} - t_{SPCKr} - t_{SPCKf}) / 2 - 3$	-	
		Slave		$2 \times t_{Pcyc}$	-	
	RSPCK clock low pulse width	Master	t_{SPCKWL}	$(t_{SPCyc} - t_{SPCKr} - t_{SPCKf}) / 2 - 3$	-	
		Slave		$2 \times t_{Pcyc}$	-	
	RSPCK clock rise and fall time	Master	t_{SPCKr}, t_{SPCKf}	-	5	
		Slave		-	1	μs
	Data input setup time	Master	t_{SU}	4	-	
		Slave		5	-	
	Data input hold time	Master (PCLKA division ratio set to 1/2)	t_{HF}	0	-	Figure 2.52 to Figure 2.57 $C = 30 \text{ pF}$
		Master (PCLKA division ratio set to a value other than 1/2)	t_H	t_{Pcyc}	-	
		Slave	t_H	20	-	
	SSL setup time	Master	t_{LEAD}	$N \times t_{SPCyc} - 10^{*3}$	$N \times t_{SPCyc} + 100^{*3}$	
		Slave		$6 \times t_{Pcyc}$	-	
	SSL hold time	Master	t_{LAG}	$N \times t_{SPCyc} - 10^{*4}$	$N \times t_{SPCyc} + 100^{*4}$	
		Slave		$6 \times t_{Pcyc}$	-	
	Data output delay	Master	t_{OD}	-	6.3	
		Slave		-	20	
	Data output hold time	Master	t_{OH}	0	-	
		Slave		0	-	
	Successive transmission delay	Master	t_{TD}	$t_{SPCyc} + 2 \times t_{Pcyc}$	$8 \times t_{SPCyc} + 2 \times t_{Pcyc}$	Figure 2.56 and Figure 2.57 $C = 30 \text{ pF}$
		Slave		$6 \times t_{Pcyc}$		
	MOSI and MISO rise and fall time	Output	t_{Dr}, t_{Df}	-	5	
		Input		-	1	μs
	SSL rise and fall time	Output	t_{SSLr}, t_{SSLf}	-	5	
		Input		-	1	μs
	Slave access time	t_{SA}	-		$2 \times t_{Pcyc} + 28$	
	Slave output release time	t_{REL}	-		$2 \times t_{Pcyc} + 28$	

Note 1. t_{Pcyc} : PCLKA cycle.

- Note 2. Must use pins that have a letter ("_A", "_B") to indicate group membership appended to their name as groups. For the SPI interface, the AC portion of the electrical characteristics is measured for each group.
- Note 3. N is set to an integer from 1 to 8 by the SPCKD register.
- Note 4. N is set to an integer from 1 to 8 by the SSLND register.

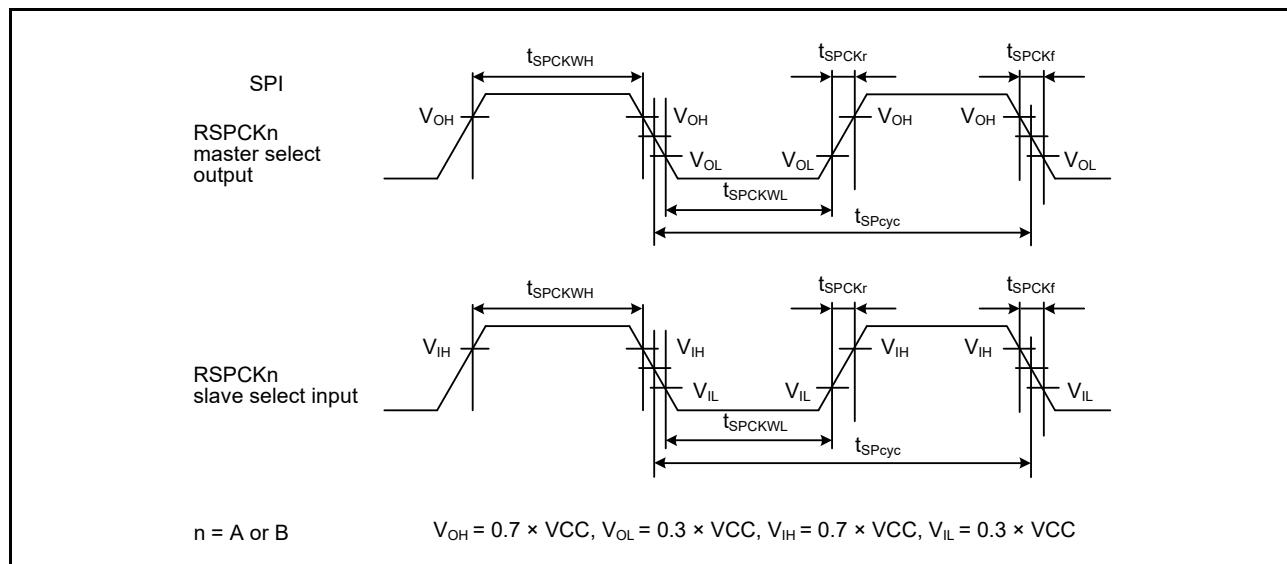


Figure 2.51 SPI clock timing

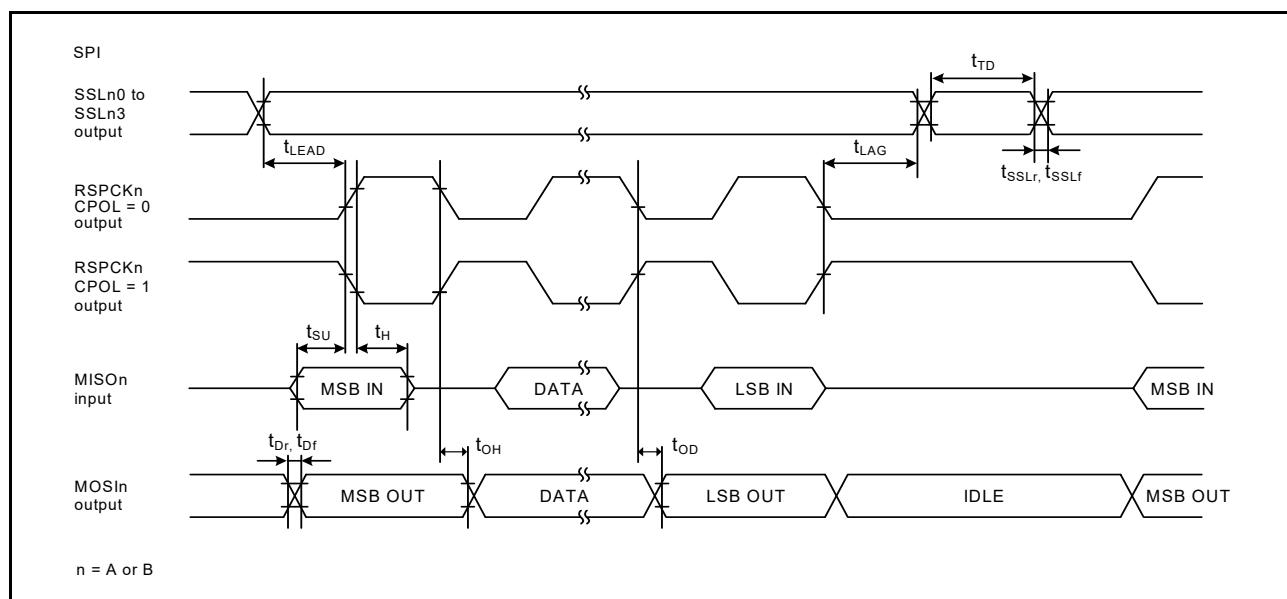


Figure 2.52 SPI timing for master when CPHA = 0

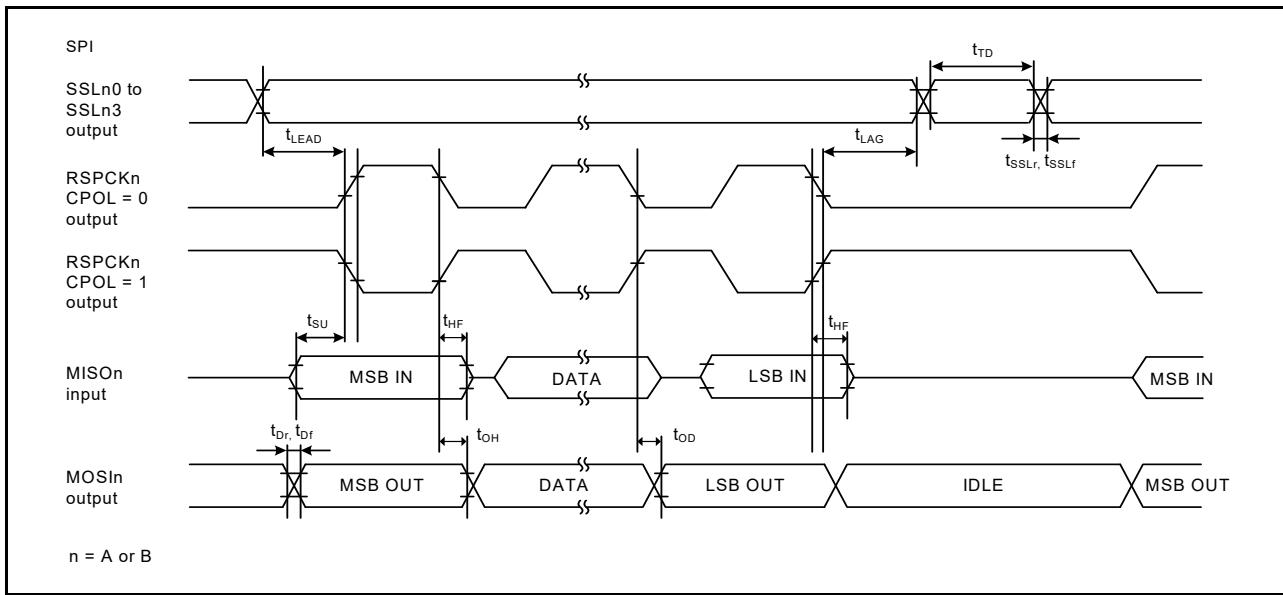


Figure 2.53 SPI timing for master when $\text{CPHA} = 0$ and the bit rate is set to $\text{PCLKA}/2$

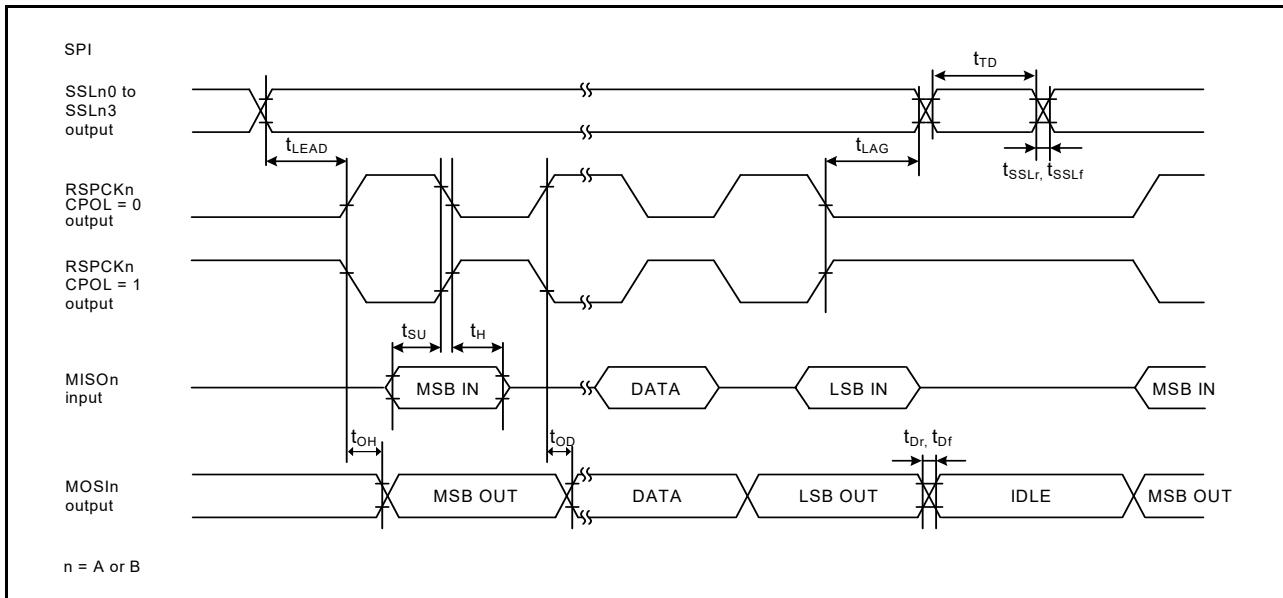


Figure 2.54 SPI timing for master when $\text{CPHA} = 1$

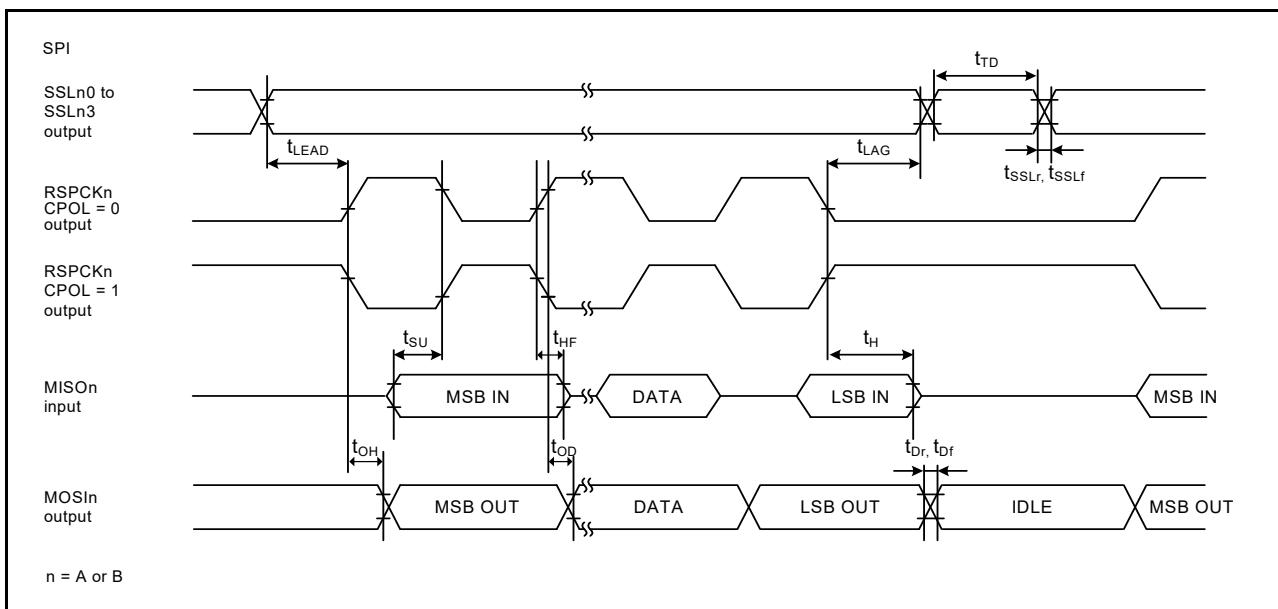


Figure 2.55 RSPI timing for master when CPHA = 1 and the bit rate is set to PCLKA/2

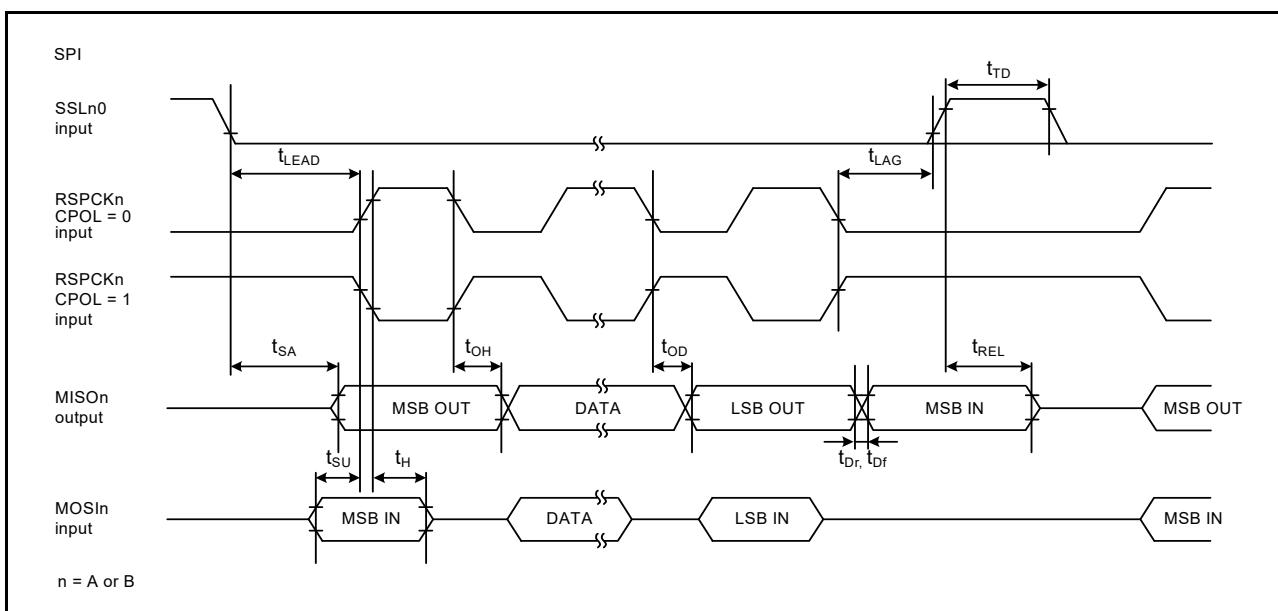


Figure 2.56 SPI timing for slave when CPHA = 0

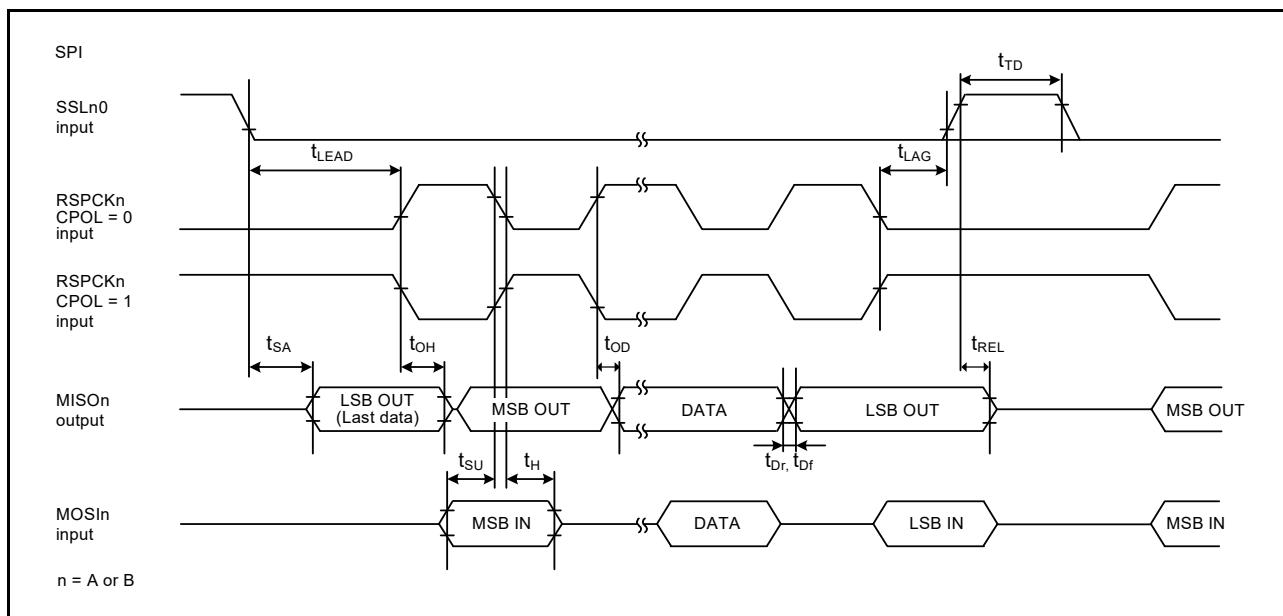


Figure 2.57 SPI timing for slave when CPHA = 1

2.3.12 QSPI Timing

Table 2.26 QSPI timing

Conditions: High drive output is selected in the port drive capability bit in the PrmnPFS register.

Parameter	Symbol	Min	Max	Unit ^{*1}	Test conditions
QSPI	QSPCK clock cycle	t_{QScyc}	2	48	t_{Pcyc}
	QSPCK clock high pulse width	t_{QSWH}	$t_{QScyc} \times 0.4$	-	ns
	QSPCK clock low pulse width	t_{QSWL}	$t_{QScyc} \times 0.4$	-	ns
	Data input setup time	t_{Su}	8	-	ns
	Data input hold time	t_{IH}	0	-	ns
	QSSL setup time	t_{LEAD}	$(N+0.5) \times t_{QScyc} - 5$ *2	$(N+0.5) \times t_{QScyc} + 100$ *2	ns
	QSSL hold time	t_{LAG}	$(N+0.5) \times t_{QScyc} - 5$ *3	$(N+0.5) \times t_{QScyc} + 100$ *3	ns
	Data output delay	t_{OD}	-	4	ns
	Data output hold time	t_{OH}	-3.3	-	ns
Successive transmission delay		t_{TD}	1	16	t_{QScyc}

Note 1. t_{Pcyc} : PCLKA cycle.

Note 2. N is set to 0 or 1 in SFMSLD.

Note 3. N is set to 0 or 1 in SFMSHD.

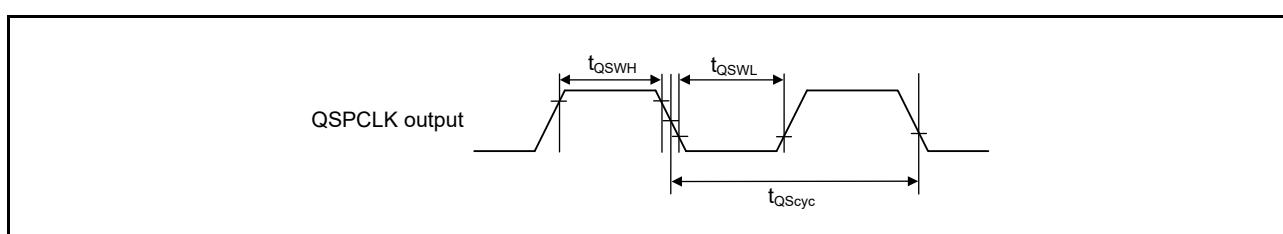


Figure 2.58 QSPI clock timing

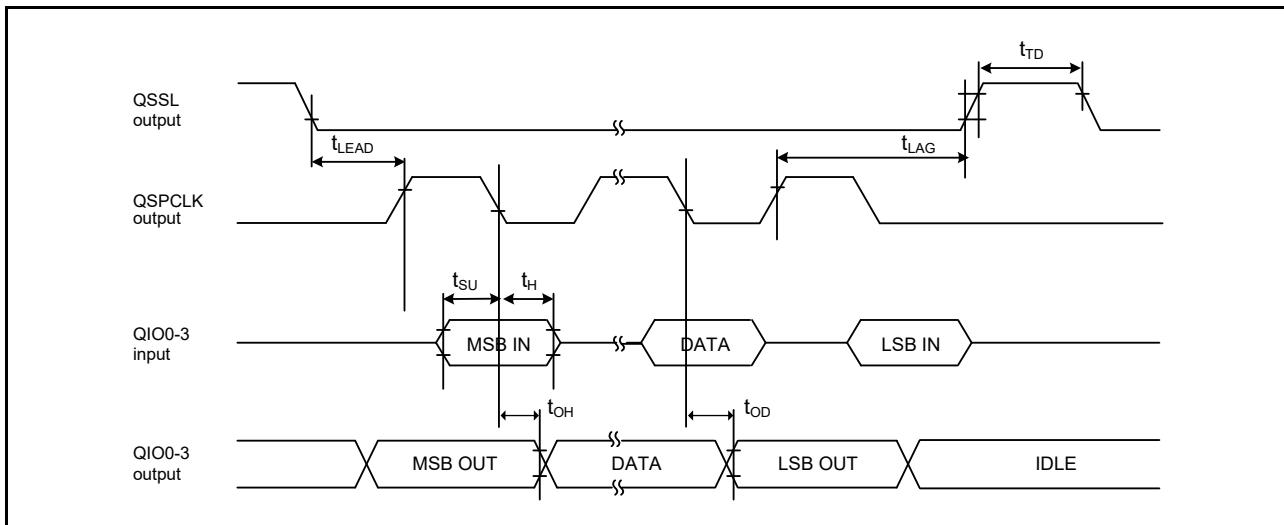


Figure 2.59 Transmit and receive timing

2.3.13 IIC Timing

Table 2.27 IIC timing (1) (1 of 2)

- (1) Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SDA0_B, SCL0_B, SDA1_A, SCL1_A, SDA1_B, SCL1_B.
 (2) The following pins do not require setting: SCL0_A, SDA0_A, SCL2, SDA2.
 (3) Use pins that have a letter appended to their names, for instance “_A” or “_B”, to indicate group membership. For the IIC interface, the AC portion of the electrical characteristics is measured for each group.

Parameter	Symbol	Min*1	Max	Unit	Test conditions*3
IIC (Standard mode, SMBus) ICFER.FMPE = 0	t _{SCL}	$6(12) \times t_{IICcyc} + 1300$	-	ns	Figure 2.60
	t _{SCLH}	$3(6) \times t_{IICcyc} + 300$	-	ns	
	t _{SCLL}	$3(6) \times t_{IICcyc} + 300$	-	ns	
	t _{Sr}	-	1000	ns	
	t _{Sf}	-	300	ns	
	t _{SP}	0	$1(4) \times t_{IICcyc}$	ns	
	t _{BUF}	$3(6) \times t_{IICcyc} + 300$	-	ns	
	t _{BUF}	$3(6) \times t_{IICcyc} + 4 \times t_{Pcyc} + 300$	-	ns	
	t _{STAH}	$t_{IICcyc} + 300$	-	ns	
	t _{STAH}	$1(5) \times t_{IICcyc} + t_{Pcyc} + 300$	-	ns	
	t _{STAS}	1000	-	ns	
	t _{STOS}	1000	-	ns	
	t _{SDAS}	$t_{IICcyc} + 50$	-	ns	
	t _{SDAH}	0	-	ns	
SCL, SDA capacitive load		C _b	400	pF	

Table 2.27 IIC timing (1) (2 of 2)

- (1) Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SDA0_B, SCL0_B, SDA1_A, SCL1_A, SDA1_B, SCL1_B.
- (2) The following pins do not require setting: SCL0_A, SDA0_A, SCL2, SDA2.
- (3) Use pins that have a letter appended to their names, for instance “_A” or “_B”, to indicate group membership. For the IIC interface, the AC portion of the electrical characteristics is measured for each group.

Parameter	Symbol	Min*1	Max	Unit	Test conditions*3
IIC (Fast mode)	SCL input cycle time	t_{SCL}	$6(12) \times t_{IICcyc} + 600$	-	ns
	SCL input high pulse width	t_{SCLH}	$3(6) \times t_{IICcyc} + 300$	-	ns
	SCL input low pulse width	t_{SCLL}	$3(6) \times t_{IICcyc} + 300$	-	ns
	SCL, SDA input rise time	t_{Sr}	$20 \times (\text{external pullup voltage}/5.5V)^{*2}$	300	ns
	SCL, SDA input fall time	t_{Sf}	$20 \times (\text{external pullup voltage}/5.5V)^{*2}$	300	ns
	SCL, SDA input spike pulse removal time	t_{SP}	0	$1(4) \times t_{IICcyc}$	ns
	SDA input bus free time when wakeup function is disabled	t_{BUF}	$3(6) \times t_{IICcyc} + 300$	-	ns
	SDA input bus free time when wakeup function is enabled	t_{BUF}	$3(6) \times t_{IICcyc} + 4 \times t_{Pcyc} + 300$	-	ns
	START condition input hold time when wakeup function is disabled	t_{STAH}	$t_{IICcyc} + 300$	-	ns
	START condition input hold time when wakeup function is enabled	t_{STAH}	$1(5) \times t_{IICcyc} + t_{Pcyc} + 300$	-	ns
	Repeated START condition input setup time	t_{STAS}	300	-	ns
	STOP condition input setup time	t_{STOS}	300	-	ns
	Data input setup time	t_{SDAS}	$t_{IICcyc} + 50$	-	ns
	Data input hold time	t_{SDAH}	0	-	ns
	SCL, SDA capacitive load	C_b	-	400	pF

Note: t_{IICcyc} : IIC internal reference clock (IIC ϕ) cycle, t_{Pcyc} : PCLKB cycle.

Note 1. Values in parentheses apply when ICMR3.NF[1:0] is set to 11b while the digital filter is enabled with ICFER.NFE set to 1.

Note 2. Only supported for SCL0_A, SDA0_A, SCL2, and SDA2.

Note 3. Must use pins that have a letter (“_A”, “_B”) to indicate group membership appended to their name as groups. For the IIC interface, the AC portion of the electrical characteristics is measured for each group.

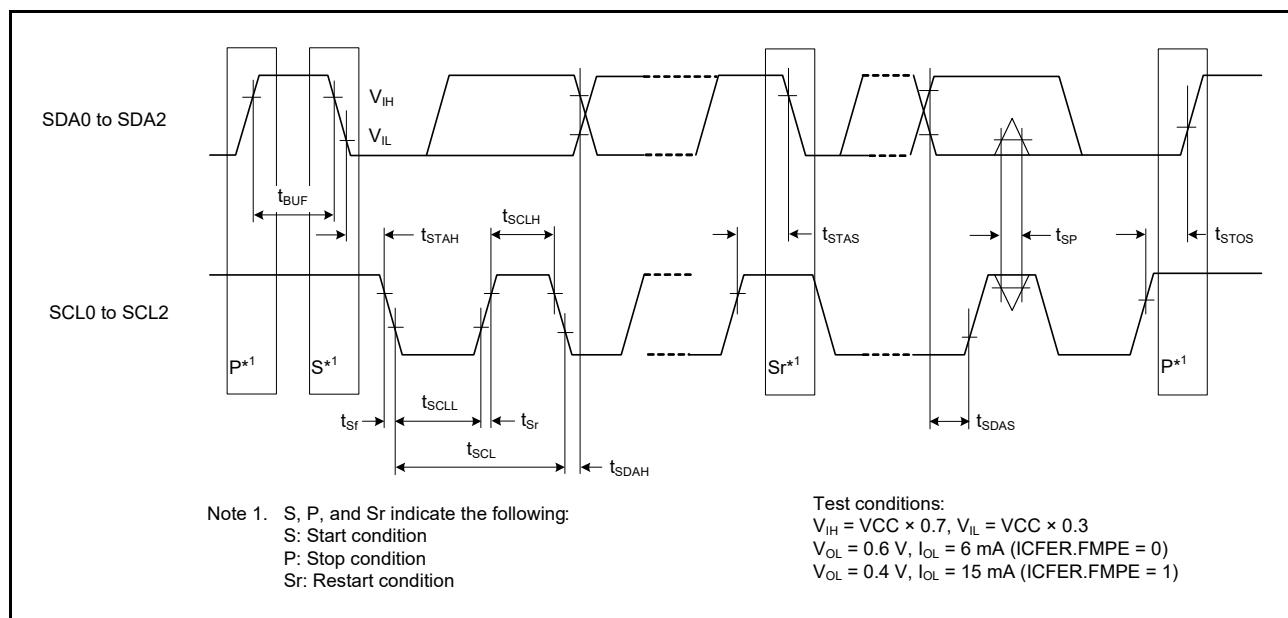
Table 2.28 IIC timing (2)

Setting of the SCL0_A, SDA0_A pins is not required with the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min*1,*2	Max	Unit	Test conditions
IIC (Fast-mode+) ICFER.FMPE = 1	SCL input cycle time	t_{SCL}	$6(12) \times t_{IICcyc} + 240$	-	ns
	SCL input high pulse width	t_{SCLH}	$3(6) \times t_{IICcyc} + 120$	-	ns
	SCL input low pulse width	t_{SCLL}	$3(6) \times t_{IICcyc} + 120$	-	ns
	SCL, SDA input rise time	t_{Sr}	-	120	ns
	SCL, SDA input fall time	t_{Sf}	-	120	ns
	SCL, SDA input spike pulse removal time	t_{SP}	0	$1(4) \times t_{IICcyc}$	ns
	SDA input bus free time when wakeup function is disabled	t_{BUF}	$3(6) \times t_{IICcyc} + 120$	-	ns
	SDA input bus free time when wakeup function is enabled	t_{BUF}	$3(6) \times t_{IICcyc} + 4 \times t_{Pcyc} + 120$	-	ns
	Start condition input hold time when wakeup function is disabled	t_{STAH}	$t_{IICcyc} + 120$	-	ns
	START condition input hold time when wakeup function is enabled	t_{STAH}	$1(5) \times t_{IICcyc} + t_{Pcyc} + 120$	-	ns
	Restart condition input setup time	t_{STAS}	120	-	ns
	Stop condition input setup time	t_{STOS}	120	-	ns
	Data input setup time	t_{SDAS}	$t_{IICcyc} + 30$	-	ns
	Data input hold time	t_{SDAH}	0	-	ns
	SCL, SDA capacitive load	C_b	-	550	pF

Note: t_{IICcyc} : IIC internal reference clock (IIC ϕ) cycle, t_{Pcyc} : PCLKB cycle.

Note 1. Values in parentheses apply when ICMR3.NF[1:0] is set to 11b while the digital filter is enabled with ICFER.NFE set to 1.

Note 2. C_b indicates the total capacity of the bus line.**Figure 2.60 I²C bus interface input/output timing**

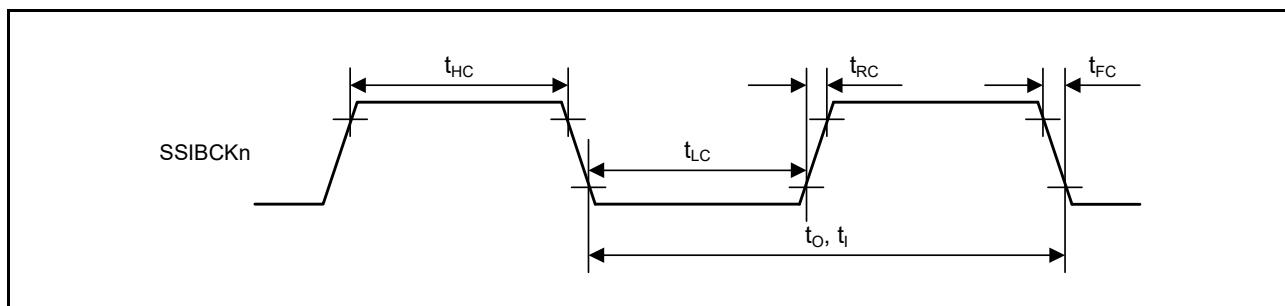
2.3.14 SSIE Timing

Table 2.29 SSIE timing

- (1) High drive output is selected with the port drive capability bit in the PmnPFS register.
 (2) Use pins that have a letter appended to their names, for instance “_A” or “_B” to indicate group membership. For the SSIE interface, the AC portion of the electrical characteristics is measured for each group.

Parameter		Symbol	Target specification		Unit	Comments
			Min.	Max.		
SSIBCK	Cycle	Master	t_O	80	-	ns
		Slave	t_I	80	-	ns
	High level/ low level	Master	t_{HC}/t_{LC}	0.35	-	t_O
		Slave		0.35	-	t_I
	Rising time/falling time	Master	t_{RC}/t_{FC}	-	0.15	t_O / t_I
		Slave		-	0.15	t_O / t_I
	Input set up time	Master	t_{SR}	12	-	ns
		Slave		12	-	ns
	Input hold time	Master	t_{HR}	8	-	ns
		Slave		15	-	ns
SSILRCK/SSIIFS, SSITXD0, SSIRXD0, SSIDATA1	Output delay time	Master	t_{DTR}	-10	5	ns
		Slave		0	20	ns
	Output delay time from SSILRCK/SSIIFS change	Slave	t_{DTRW}	-	20	ns
	Cycle		t_{EXcyc}	20	-	ns
	High level/ low level		$t_{EXL}/$ t_{EXH}	0.4	0.6	t_{EXcyc}
GTIOC1A, AUDIO_CLK						Figure 2.62

Note 1. For slave-mode transmission, SSIE has a path, through which the signal input from the SSILRCK/SSIIFS pin is used to generate transmit data, and the transmit data is logically output to the SSITXD0 or SSIDATA1 pin.

**Figure 2.61 SSIE clock input/output timing**

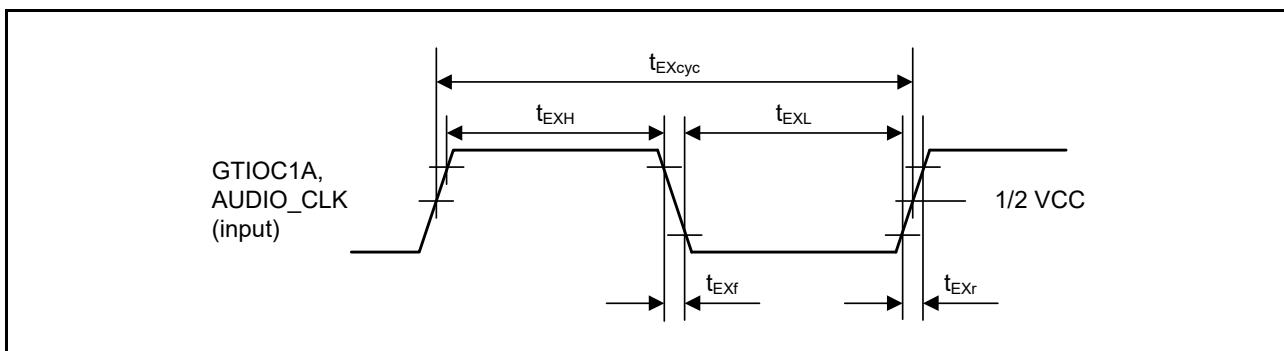


Figure 2.62 Clock input timing

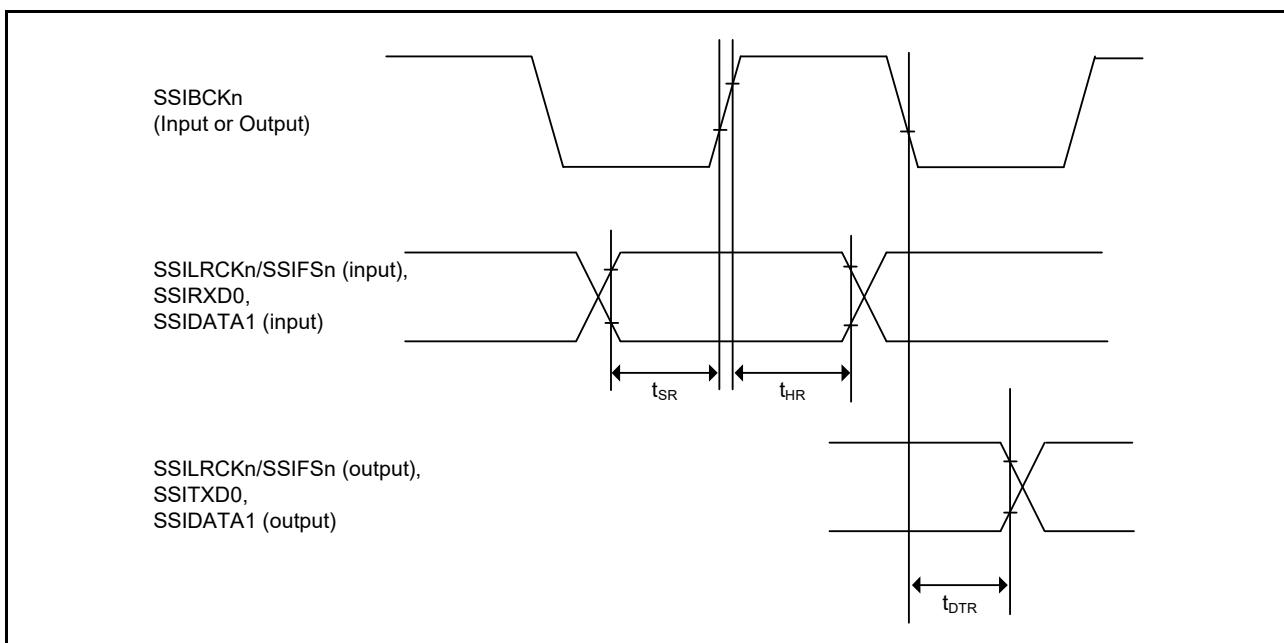


Figure 2.63 SSIE data transmit and receive timing when SSICR.BCKP = 0

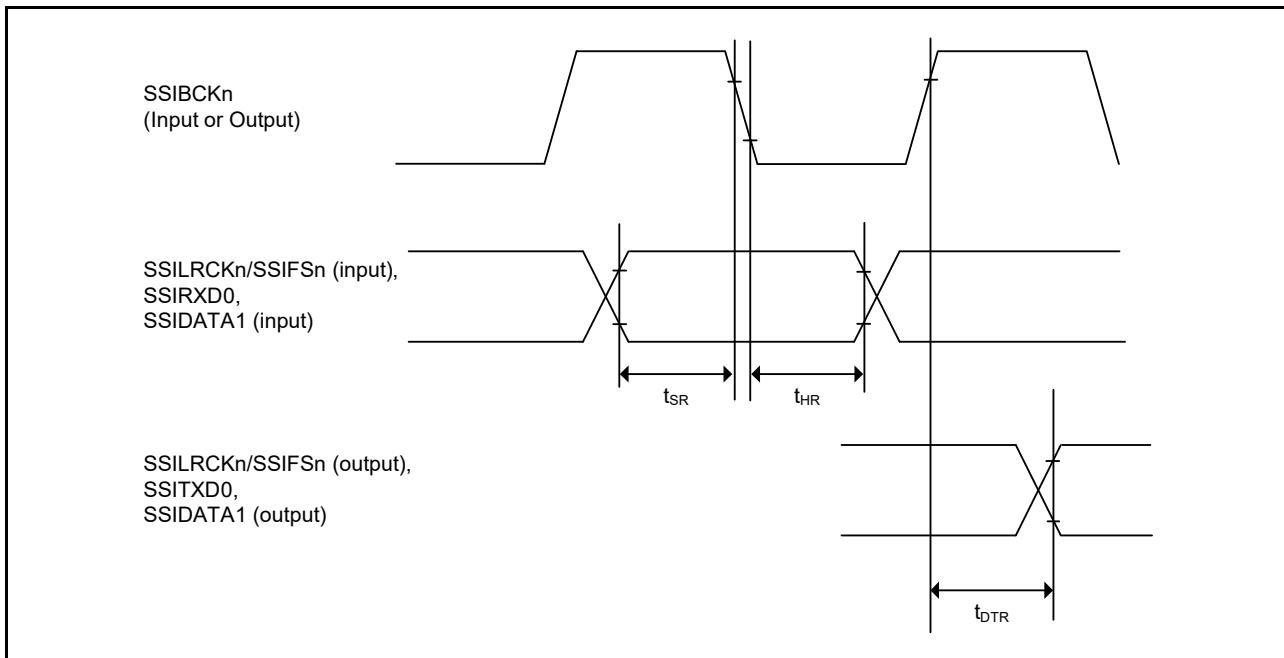


Figure 2.64 SSIE data transmit and receive timing when SSICR.BCKP = 1

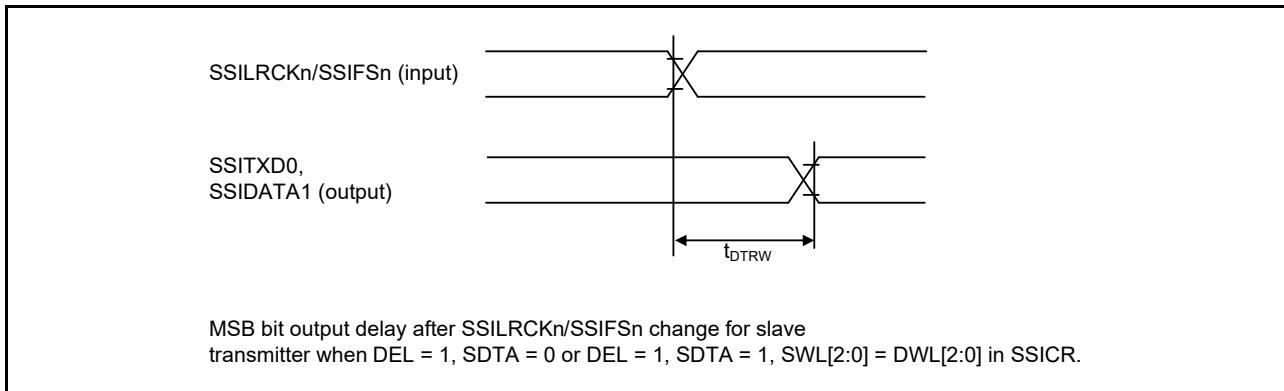


Figure 2.65 SSIE data output delay after SSILRCKn/SSIFSn change

2.3.15 SD/MMC Host Interface Timing

Table 2.30 SD/MMC Host Interface signal timing

Conditions: High drive output is selected in the port drive capability bit in the PmnPFS register.
Clock duty ratio is 50%.

Parameter	Symbol	Min	Max	Unit	Test conditions*1
SDCLK clock cycle	T _{SDCYC}	20	-	ns	Figure 2.66
SDCLK clock high pulse width	T _{SDWH}	6.5	-	ns	
SDCLK clock low pulse width	T _{SDWL}	6.5	-	ns	
SDCLK clock rise time	T _{SDLH}	-	3	ns	
SDCLK clock fall time	T _{SDHL}	-	3	ns	
SDCMD/SDDAT output data delay	T _{SDODLY}	-6	5	ns	
SDCMD/SDDAT input data setup	T _{SDIS}	4	-	ns	
SDCMD/SDDAT input data hold	T _{SDIH}	2	-	ns	

Note 1. Must use pins that have a letter ("_A", "_B") to indicate group membership appended to their name as groups. For

the SD/MMC Host interface, the AC portion of the electrical characteristics is measured for each group.

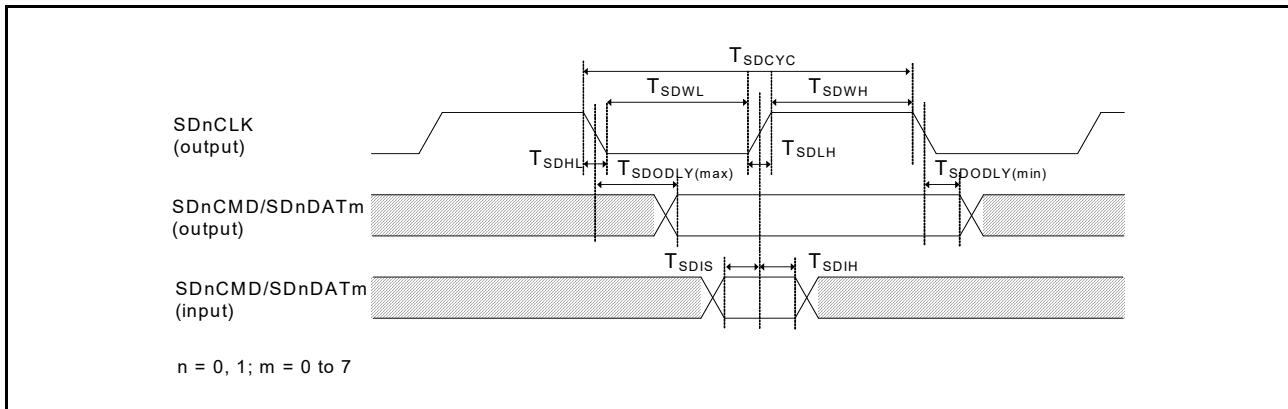


Figure 2.66 SD/MMC Host Interface signal timing

2.3.16 ETHERC Timing

Table 2.31 ETHERC timing

Conditions: ETHERC (RMII): Middle drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: ET0_MDC, ET0_MDIO.

For other pins, high drive output is selected in the port drive capability bit in the PmnPFS register.

ETHERC (MII): Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Max	Unit	Test conditions ^{*3}
ETHERC (RMII)	T _{ck}	20	-	ns	Figure 2.67 to Figure 2.70
	REF50CK frequency, typical 50 MHz	-	50 + 100 ppm	MHz	
	REF50CK duty	35	65	%	
	T _{ckr/ckf}	0.5	3.5	ns	
	RMII0_xxxx ^{*1} output delay	T _{co}	2.5	12.0	
	RMII0_xxxx ^{*2} setup time	T _{su}	3	-	
	RMII0_xxxx ^{*2} hold time	T _{hd}	1	-	
	RMII0_xxxx ^{*1, *2} rise/fall time	T _{r/T_f}	0.5	4	
	ET0_WOL output delay	t _{WOLd}	1	23.5	
ETHERC (MII)	ET0_TX_CLK cycle time	t _{Tcyc}	40	-	Figure 2.72
	ET0_TX_EN output delay	t _{TEND}	1	20	
	ET0_ETXD0 to ET0_ETXD3 output delay	t _{MTDd}	1	20	
	ET0_CRS setup time	t _{CRSs}	10	-	
	ET0_CRS hold time	t _{CRSh}	10	-	
	ET0_COL setup time	t _{COLs}	10	-	
	ET0_COL hold time	t _{COLh}	10	-	
	ET0_RX_CLK cycle time	t _{TRcyc}	40	-	Figure 2.74
	ET0_RX_DV setup time	t _{RDVs}	10	-	
	ET0_RX_DV hold time	t _{RDVh}	10	-	
	ET0_ERXD0 to ET0_ERXD3 setup time	t _{MRDs}	10	-	
	ET0_ERXD0 to ET0_ERXD3 hold time	t _{MRDh}	10	-	
	ET0_RX_ER setup time	t _{RERs}	10	-	Figure 2.75
	ET0_RX_ER hold time	t _{RESh}	10	-	
	ET0_WOL output delay	t _{WOLd}	1	23.5	Figure 2.76

Note 1. RMII0_TXD_EN, RMII0_TXD1, RMII0_TXD0.

Note 2. RMII0_CRS_DV, RMII0_RXD1, RMII0_RXD0, RMII0_RX_ER.

Note 3. The following pins, must use pins that have a letter ("_A", "_B") to indicate group membership appended to their name as groups. For the ETHERC (RMII) Host interface, the AC portion of the electrical characteristics is measured for each group.
REF50CK0_A, REF50CK0_B, RMII0_xxxx_A, RMII0_xxxx_B

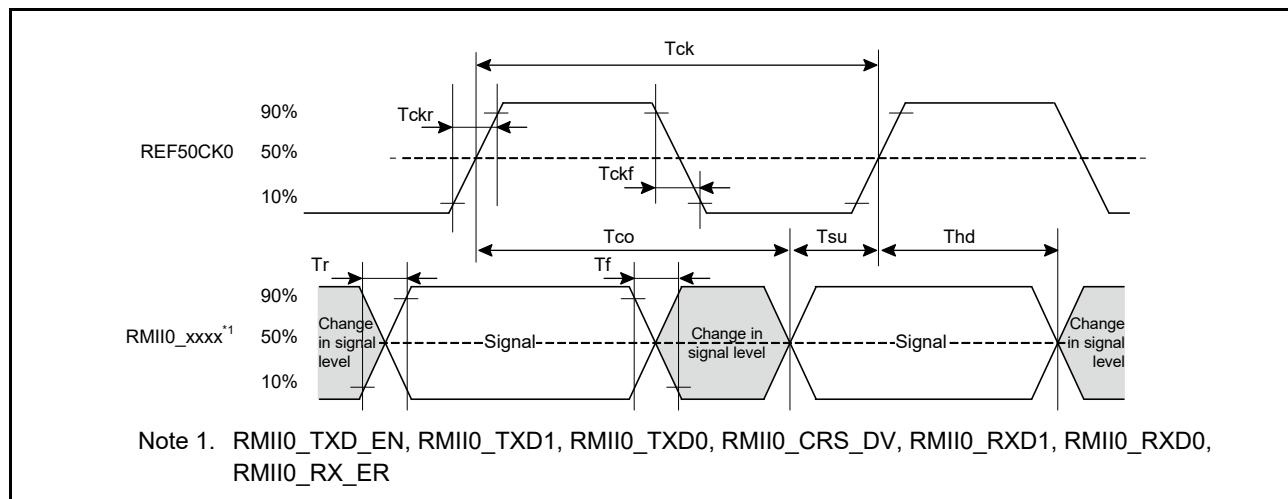


Figure 2.67 REF50CK0 and RMII signal timing

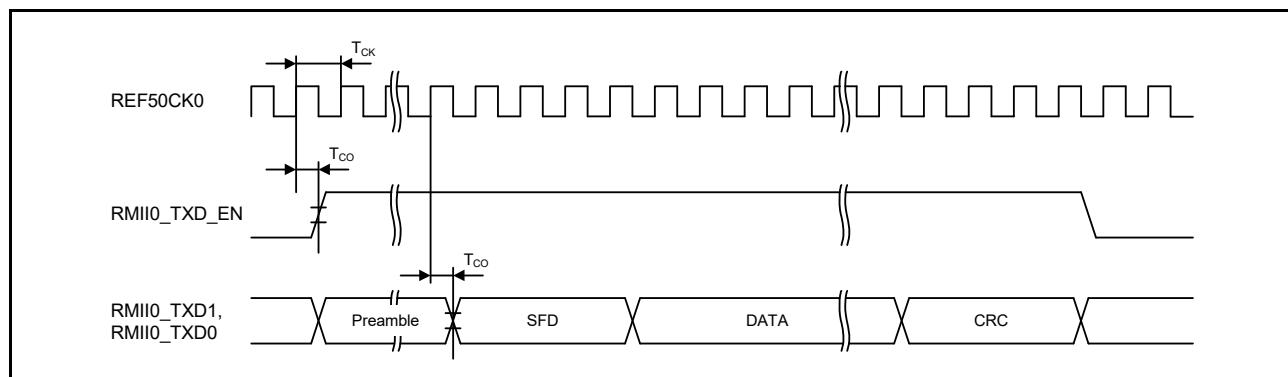


Figure 2.68 RMII transmission timing

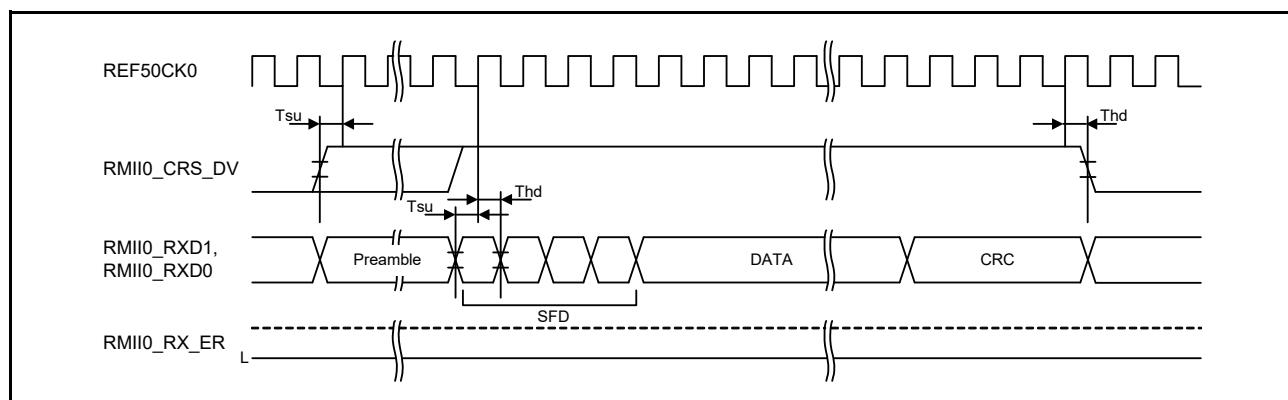


Figure 2.69 RMII reception timing in normal operation

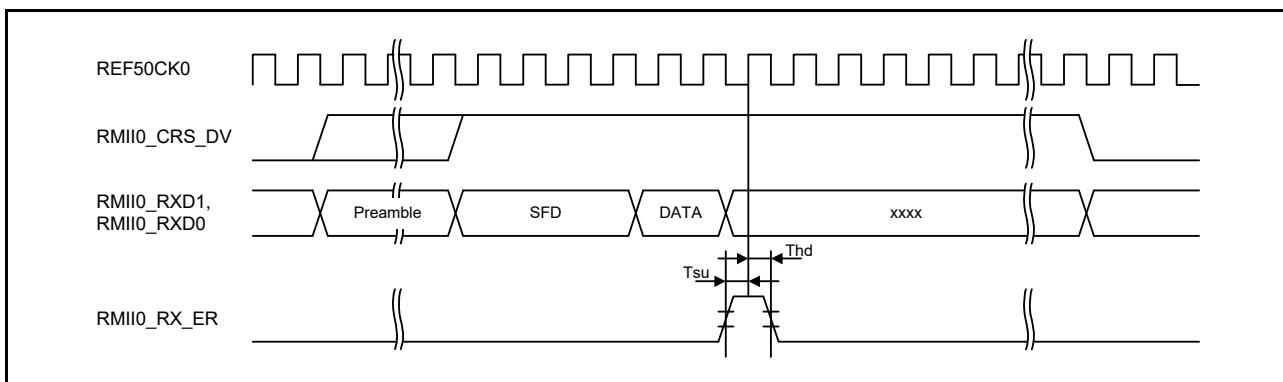


Figure 2.70 RMII reception timing when an error occurs

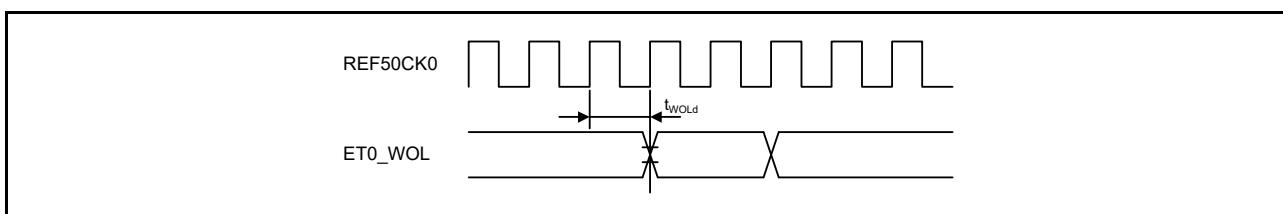


Figure 2.71 WOL output timing for RMII

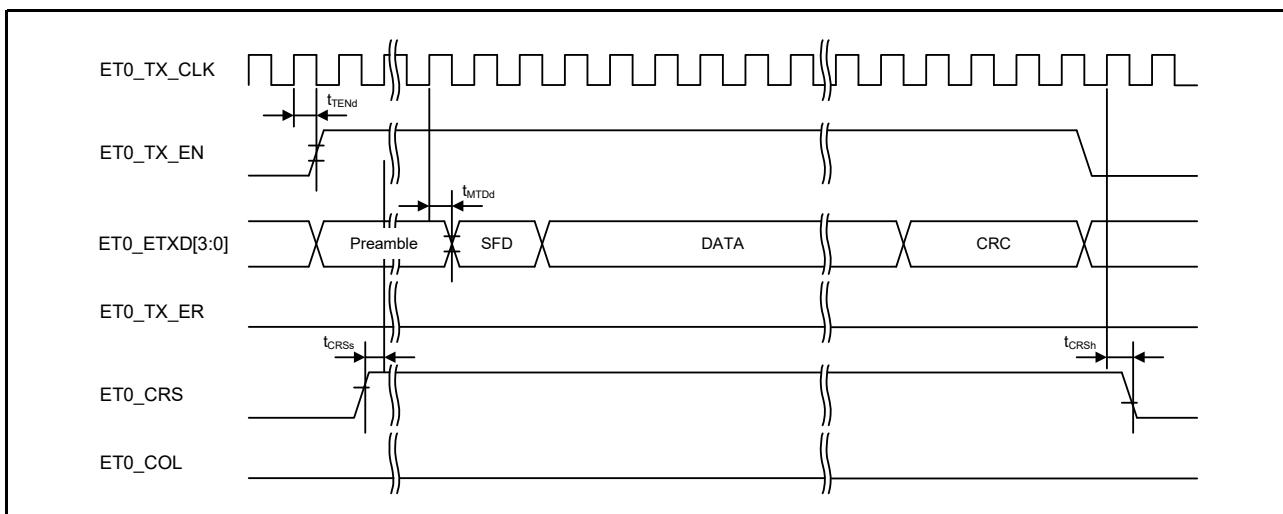


Figure 2.72 MII transmission timing in normal operation

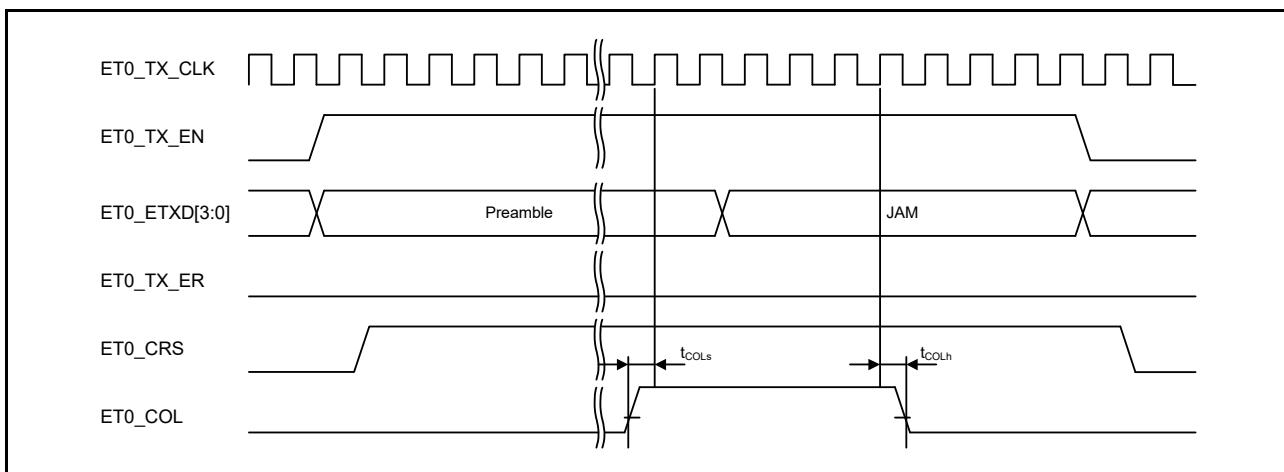


Figure 2.73 MII transmission timing when a conflict occurs

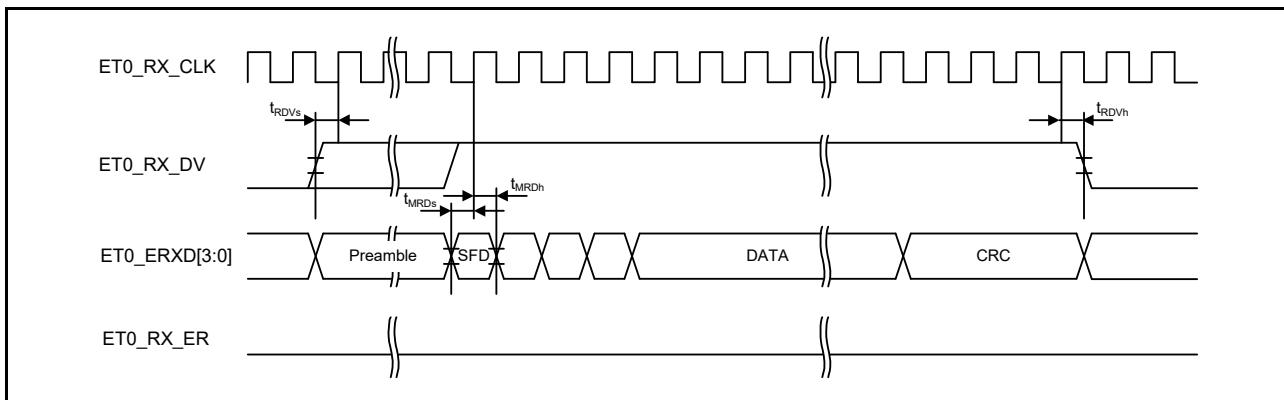


Figure 2.74 MII reception timing in normal operation

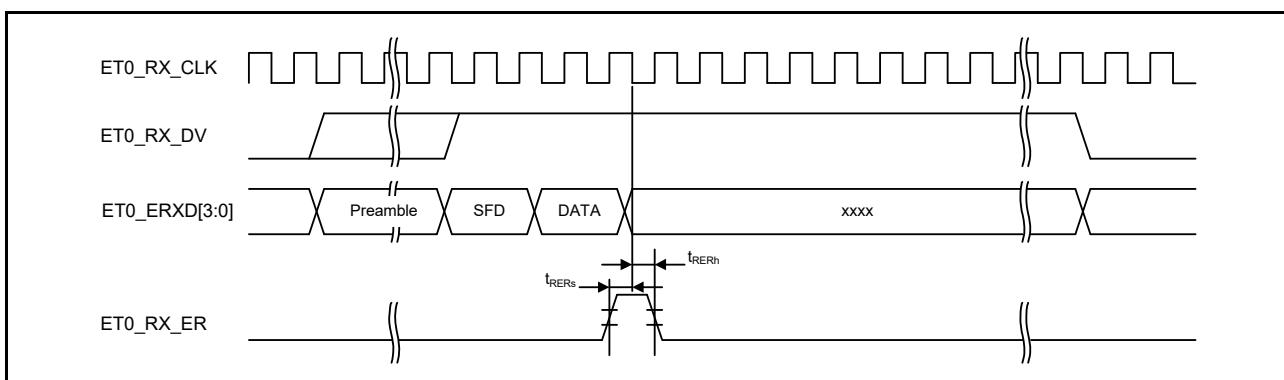


Figure 2.75 MII reception timing when an error occurs

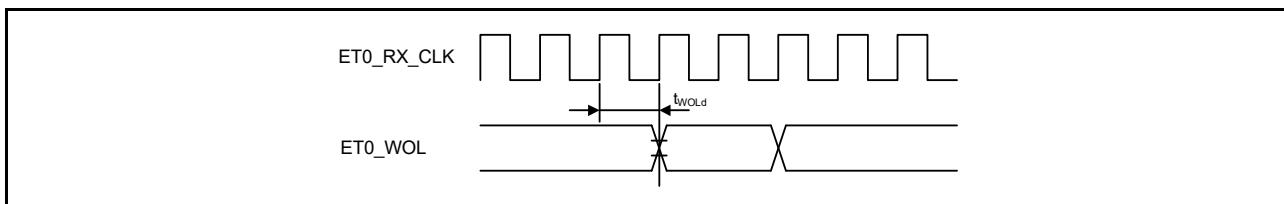


Figure 2.76 WOL output timing for MII

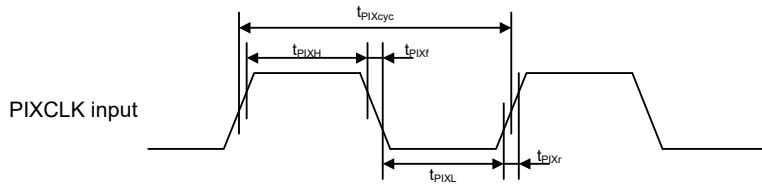
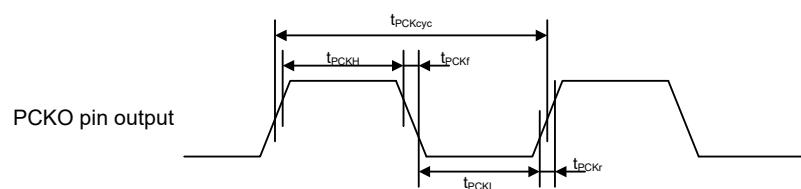
2.3.17 PDC Timing

Table 2.32 PDC timing

Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Output load conditions: $V_{OH} = VCC \times 0.5$, $V_{OL} = VCC \times 0.5$, $C = 30 \text{ pF}$

Parameter	Symbol	Min	Max	Unit	Test conditions
PDC	PIXCLK input cycle time	t_{PIXcyc}	37	-	Figure 2.77
	PIXCLK input high pulse width	t_{PIXH}	10	-	
	PIXCLK input low pulse width	t_{PIXL}	10	-	
	PIXCLK rise time	t_{PIXr}	-	5	
	PIXCLK fall time	t_{PIXf}	-	5	
	PCKO output cycle time	t_{PCKcyc}	$2 \times t_{PBcyc}$	-	
	PCKO output high pulse width	t_{PCKH}	$(t_{PCKcyc} - t_{PCKr} - t_{PCKf})/2 - 3$	-	
	PCKO output low pulse width	t_{PCKL}	$(t_{PCKcyc} - t_{PCKr} - t_{PCKf})/2 - 3$	-	
	PCKO rise time	t_{PCKr}	-	5	
	PCKO fall time	t_{PCKf}	-	5	
VSYNV/HSYNC input	VSYNV/HSYNC input setup time	t_{SYNCS}	10	-	Figure 2.79
	VSYNV/HSYNC input hold time	t_{SYNCH}	5	-	
	PIXD input setup time	t_{PIXDS}	10	-	
	PIXD input hold time	t_{PIXDH}	5	-	

Note 1. t_{PBcyc} : PCLKB cycle.**Figure 2.77 PDC input clock timing****Figure 2.78 PDC output clock timing**

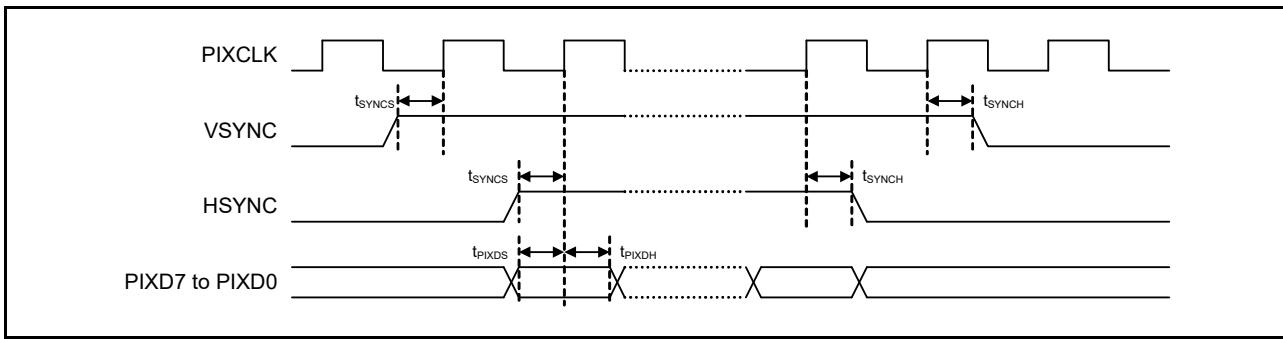


Figure 2.79 PDC AC timing

2.3.18 GLCDC Timing

Table 2.33 GLCDC timing

Conditions:

LCD_CLK: High drive output is selected in the port drive capability bit in the PmnPFS register.

LCD_DATA: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
LCD_EXTCLK input clock frequency	t_{Ecyc}	-	-	$60^{\ast 1}$	MHz	Figure 2.80
LCD_EXTCLK input clock low pulse width	t_{WL}	0.45	-	0.55	t_{Ecyc}	
LCD_EXTCLK input clock high pulse width	t_{WH}	0.45	-	0.55		
LCD_CLK output clock frequency	t_{Lcyc}	-	-	$60^{\ast 1}$	MHz	Figure 2.81
LCD_CLK output clock low pulse width	t_{LOL}	0.4	-	0.6	t_{Lcyc}	Figure 2.81
LCD_CLK output clock high pulse width	t_{LOH}	0.4	-	0.6	t_{Lcyc}	Figure 2.81
LCD data output delay timing	t_{DD}	-3.5	-	4	ns	Figure 2.82
_A or _B combinations ^{*2}				-5.0		
_A and _B combinations ^{*3}				5.5		

Note 1. Parallel RGB888, 666,565: Maximum 54 MHz
Serial RGB888: Maximum 60 MHz (4x speed)

Note 2. Use pins that have a letter appended to their names, for instance, “_A” or “_B”, to indicate

Note 3. Pins of group “_A” and “_B” combinations are used.

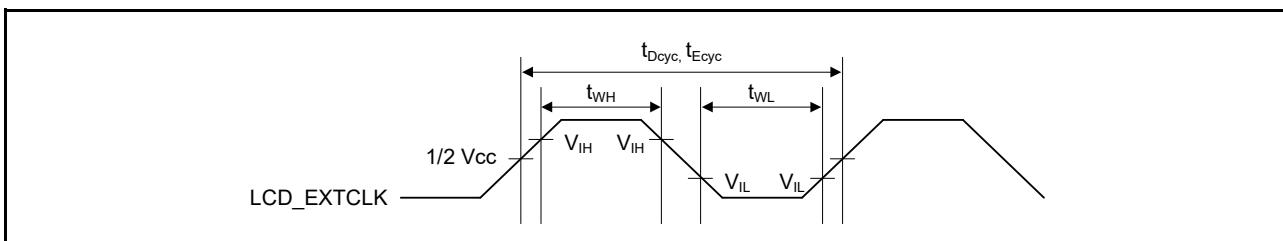


Figure 2.80 LCD_EXTCLK clock input timing

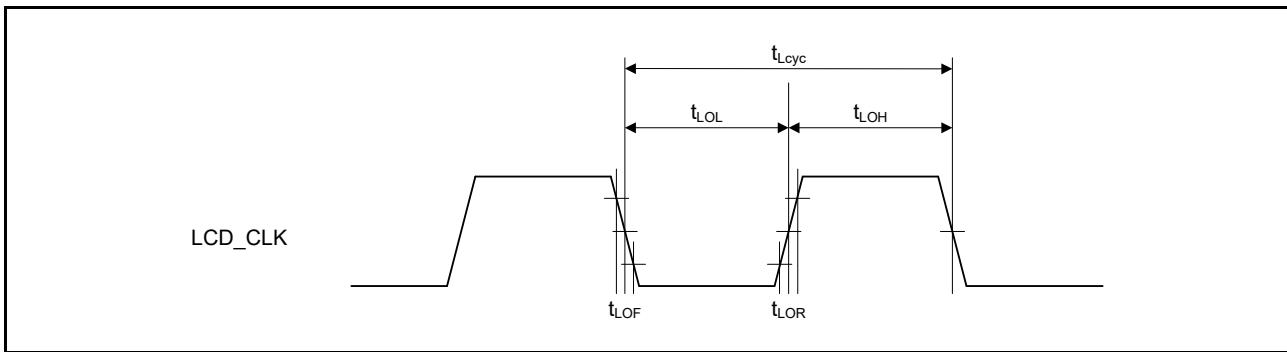


Figure 2.81 LCD_CLK clock output timing

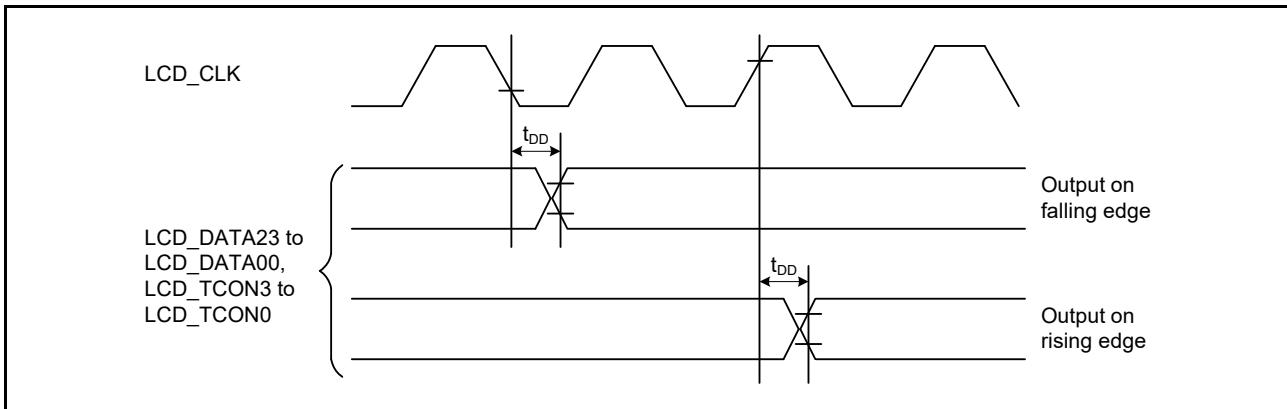


Figure 2.82 Display output timing

2.4 USB Characteristics

2.4.1 USBHS Timing

Table 2.34 USBHS low-speed characteristics for host only (USBHS_DP and USBHS_DM pin characteristics)
Conditions: USBHS_RREF = 2.2 kΩ ± 1%, USBMCLK = 12/20/24 MHz, UCLK = 48 MHz

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
Input characteristics	V _{IH}	2.0	-	-	V	-	-
	V _{IL}	-	-	0.8	V	-	-
	V _{DI}	0.2	-	-	V	USBHS_DP - USBHS_DM	-
	V _{CM}	0.8	-	2.5	V	-	-
Output characteristics	V _{OH}	2.8	-	3.6	V	I _{OH} = -200 μA	-
	V _{OL}	0.0	-	0.3	V	I _{OL} = 2 mA	-
	V _{CRS}	1.3	-	2.0	V	-	Figure 2.83, Figure 2.84
	t _{LR}	75	-	300	ns	-	
	t _{LF}	75	-	300	ns	-	
	t _{LR} / t _{LF}	80	-	125	%	t _{LR} / t _{LF}	-
Pull-up, Pull-down characteristics	R _{pd}	14.25	-	24.80	kΩ	-	-

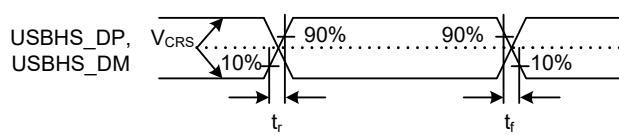


Figure 2.83 USBHS_DP and USBHS_DM output timing in low-speed mode

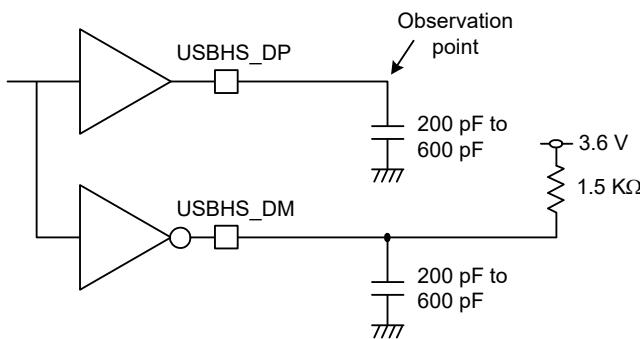


Figure 2.84 Test circuit in low-speed mode

Table 2.35 USBHS full-speed characteristics (USBHS_DP and USBHS_DM pin characteristics)
Conditions: USBHS_RREF = 2.2 kΩ ± 1%, USBMCLK = 12/20/24 MHz, UCLK = 48 MHz

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Input characteristics	Input high voltage	V _{IH}	2.0	-	-	V	-
	Input low voltage	V _{IL}	-	-	0.8	V	-
	Differential input sensitivity	V _{DI}	0.2	-	-	V	USBHS_DP - USBHS_DM
	Differential common-mode range	V _{CM}	0.8	-	2.5	V	-
Output characteristics	Output high voltage	V _{OH}	2.8	-	3.6	V	I _{OH} = -200 μA
	Output low voltage	V _{OL}	0.0	-	0.3	V	I _{OL} = 2 mA
	Cross-over voltage	V _{CRS}	1.3	-	2.0	V	Figure 2.85, Figure 2.86
	Rise time	t _{LR}	4	-	20	ns	
	Fall time	t _{LF}	4	-	20	ns	
	Rise/fall time ratio	t _{LR} / t _{LF}	90	-	111.11	%	t _{FR} / t _{FF}
	Output resistance	Z _{DRV}	40.5	-	49.5	Ω	Rs Not used (PHYSET.REPSEL[1:0] = 01b and PHYSET.HSEB = 0)
DC characteristics	USBHS_DM pull-up resistor (device)	R _{pu}	0.900	-	1.575	kΩ	During idle state
			1.425	-	3.090	kΩ	During transmission and reception
	USBHS_DP/USBHS_DM pull-down resistor (host)	R _{pd}	14.25	-	24.80	kΩ	-

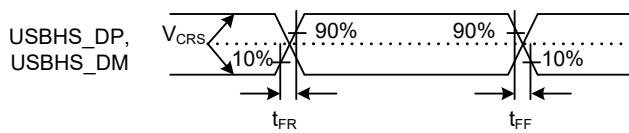


Figure 2.85 USBHS_DP and USBHS_DM output timing in full-speed mode

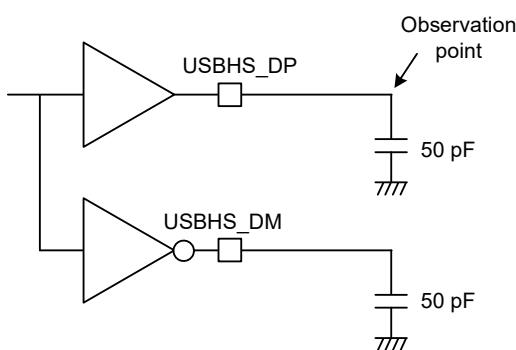


Figure 2.86 Test circuit in full-speed mode

Table 2.36 USBHS high-speed characteristics (USBHS_DP and USBHS_DM pin characteristics)
Conditions: $V_{HSSQ} = 2.2 \text{ k}\Omega \pm 1\%$, $V_{HSDSC} = 525 \text{ mV}$, $V_{HSREF} = 2.2 \text{ k}\Omega$, $V_{HSDR} = 40.5 \text{ }\Omega$, $V_{HSDV} = 49.5 \text{ }\Omega$, $V_{HSDC} = 625 \text{ mV}$, $V_{HSCM} = 500 \text{ mV}$, $V_{HSOI} = 10 \text{ mV}$, $V_{HSOH} = 440 \text{ mV}$, $V_{HSOL} = 10 \text{ mV}$, $V_{CHIRPJ} = 1100 \text{ mV}$, $V_{CHIRPK} = -500 \text{ mV}$, $V_{HSR} = 500 \text{ ps}$, $V_{HSF} = 500 \text{ ps}$, $V_{HSSQ} = 150 \text{ mV}$, $V_{HSDSC} = 625 \text{ mV}$, $t_{HSDR} = 40.5 \text{ }\Omega$, $t_{HSDC} = 625 \text{ mV}$, $t_{HSCM} = 500 \text{ mV}$, $t_{HSOI} = 10 \text{ mV}$, $t_{HSOH} = 440 \text{ mV}$, $t_{HSOL} = 10 \text{ mV}$, $t_{CHIRPJ} = 1100 \text{ mV}$, $t_{CHIRPK} = -500 \text{ mV}$, $t_{HSR} = 500 \text{ ps}$, $t_{HSF} = 500 \text{ ps}$

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input characteristics	Squelch detect sensitivity	V_{HSSQ}	100	-	150	mV
	Disconnect detect sensitivity	V_{HSDSC}	525	-	625	mV
	Common-mode voltage	V_{HSCM}	-50	-	500	mV
Output characteristics	Idle state	V_{HSOI}	-10.0	-	10	mV
	Output high voltage	V_{HSOH}	360	-	440	mV
	Output low voltage	V_{HSOL}	-10.0	-	10	mV
	Chirp J output voltage (difference)	V_{CHIRPJ}	700	-	1100	mV
	Chirp K output voltage (difference)	V_{CHIRPK}	-900	-	-500	mV
AC characteristics	Rise time	t_{HSR}	500	-	-	ps
	Fall time	t_{HSF}	500	-	-	ps
	Output resistance	Z_{HSDR}	40.5	-	49.5	Ω

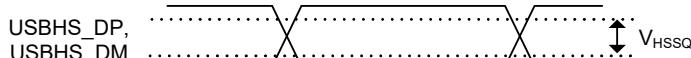


Figure 2.87 USBHS_DP and USBHS_DM squelch detect sensitivity in high-speed mode

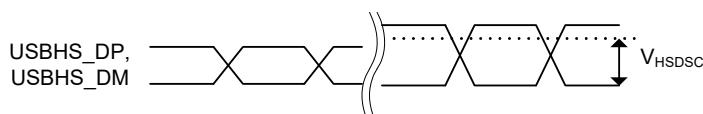


Figure 2.88 USBHS_DP and USBHS_DM disconnect detect sensitivity in high-speed mode

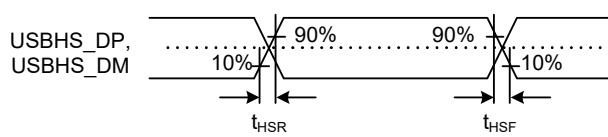


Figure 2.89 USBHS_DP and USBHS_DM output timing in high-speed mode

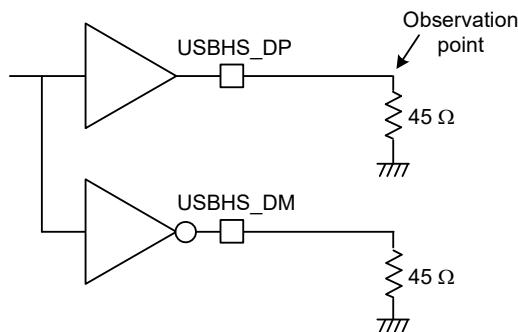


Figure 2.90 Test circuit in high-speed mode

Table 2.37 USBHS high-speed characteristics (USBHS_DP and USBHS_DM pin characteristics)
Conditions: USBHS_RREF = 2.2 kΩ ± 1%, USBMCLK = 12/20/24 MHz

Parameter	Symbol	Min	Max	Unit	Test conditions
Battery Charging Specification	I _{DP_SINK}	25	175	µA	-
	I _{DM_SINK}	25	175	µA	-
	I _{DP_SRC}	7	13	µA	-
	V _{DAT_REF}	0.25	0.4	V	-
	V _{DP_SRC}	0.5	0.7	V	Output current = 250 µA
	V _{DM_SRC}	0.5	0.7	V	Output current = 250 µA

2.4.2 USBFS Timing

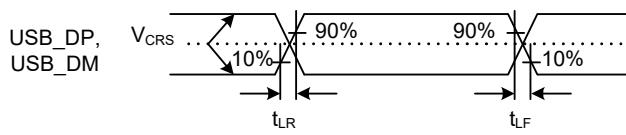
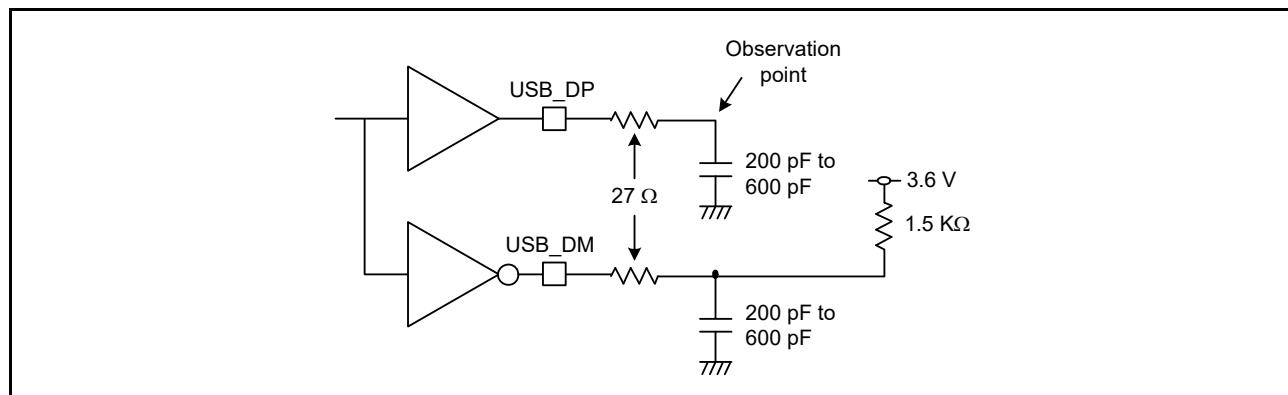
Table 2.38 USBFS low-speed characteristics for host only (USB_DP and USB_DM pin characteristics) (1 of 2)
Conditions: VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6V, 2.7 ≤ VREFH0/VREFH ≤ AVCC0, VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V, UCLK = 48 MHz

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input characteristics	V _{IH}	2.0	-	-	V	-
	V _{IL}	-	-	0.8	V	-
	V _{DI}	0.2	-	-	V	USB_DP - USB_DM
	V _{CM}	0.8	-	2.5	V	-
Output characteristics	V _{OH}	2.8	-	3.6	V	I _{OH} = -200 µA
	V _{OL}	0.0	-	0.3	V	I _{OL} = 2 mA
	V _{CRS}	1.3	-	2.0	V	Figure 2.91
	t _{LR}	75	-	300	ns	
	t _{LF}	75	-	300	ns	
	t _{LR} / t _{LF}	80	-	125	%	t _{LR} / t _{LF}

Table 2.38 USBFS low-speed characteristics for host only (USB_DP and USB_DM pin characteristics) (2 of 2)

Conditions: VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6V, $2.7 \leq VREFH0/VREFH \leq AVCC0$, VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V, UCLK = 48 MHz

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Pull-up and pull-down characteristics	R_{pd}	14.25	-	24.80	kΩ	-

**Figure 2.91 USB_DP and USB_DM output timing in low-speed mode****Figure 2.92 Test circuit in low-speed mode****Table 2.39 USBFS full-speed characteristics (USB_DP and USB_DM pin characteristics)**

Conditions: VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6V, $2.7 \leq VREFH0/VREFH \leq AVCC0$, VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V, UCLK = 48 MHz

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input characteristics	Input high voltage	V_{IH}	2.0	-	-	V
	Input low voltage	V_{IL}	-	-	0.8	V
	Differential input sensitivity	V_{DI}	0.2	-	-	V
	Differential common-mode range	V_{CM}	0.8	-	2.5	V
Output characteristics	Output high voltage	V_{OH}	2.8	-	3.6	V
	Output low voltage	V_{OL}	0.0	-	0.3	V
	Cross-over voltage	V_{CRS}	1.3	-	2.0	V
	Rise time	t_{LR}	4	-	20	ns
	Fall time	t_{LF}	4	-	20	ns
	Rise/fall time ratio	t_{LR} / t_{LF}	90	-	111.11	%
	Output resistance	Z_{DRV}	28	-	44	Ω
Pull-up and pull-down characteristics	DM pull-up resistance in device controller mode	R_{pu}	0.900	-	1.575	kΩ
			1.425	-	3.090	kΩ
	USB_DP and USB_DM pull-down resistance in host controller mode	R_{pd}	14.25	-	24.80	kΩ

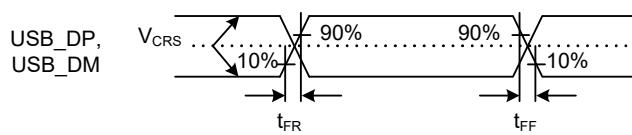


Figure 2.93 USB_DP and USB_DM output timing in full-speed mode

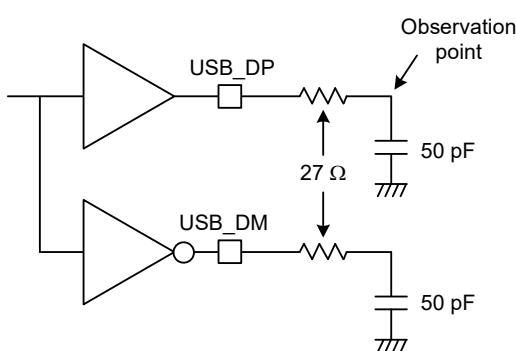


Figure 2.94 Test circuit in full-speed mode

2.5 ADC12 Characteristics

Table 2.40 A/D conversion characteristics for unit 0 (1 of 2)

Conditions: PCLKC = 1 to 60 MHz

Parameter	Min	Typ	Max	Unit	Test conditions
Frequency	1	-	60	MHz	-
Analog input capacitance	-	-	30	pF	-
Quantization error	-	± 0.5	-	LSB	-
Resolution	-	-	12	Bits	-
Channel-dedicated sample-and-hold circuits in use (AN000 to AN002)	Conversion time* ¹ (operation at PCLKC = 60 MHz) Max. = 1 kΩ	1.06 (0.4 + 0.25)* ²	-	μs	<ul style="list-style-type: none"> Sampling of channel-dedicated sample-and-hold circuits in 24 states Sampling in 15 states
	Offset error	-	± 1.5	± 3.5	LSB
	Full-scale error	-	± 1.5	± 3.5	LSB
	Absolute accuracy	-	± 2.5	± 5.5	LSB
	DNL differential nonlinearity error	-	± 1.0	± 2.0	LSB
	INL integral nonlinearity error	-	± 1.5	± 3.0	LSB
	Holding characteristics of sample-and hold circuits	-	-	20	μs
	Dynamic range	0.25	-	VREFH 0 - 0.25	V
Channel-dedicated sample-and-hold circuits not in use (AN000 to AN002)	Conversion time* ¹ (operation at PCLKC = 60 MHz) Max. = 1 kΩ	0.48 (0.267)* ²	-	-	Sampling in 16 states
	Offset error	-	± 1.0	± 2.5	LSB
	Full-scale error	-	± 1.0	± 2.5	LSB
	Absolute accuracy	-	± 2.0	± 4.5	LSB
	DNL differential nonlinearity error	-	± 0.5	± 1.5	LSB
	INL integral nonlinearity error	-	± 1.0	± 2.5	LSB

Table 2.40 A/D conversion characteristics for unit 0 (2 of 2)

Conditions: PCLKC = 1 to 60 MHz

Parameter			Min	Typ	Max	Unit	Test conditions
High-precision channels (AN003 to AN007)	Conversion time ^{*1} (operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.48 (0.267) ^{*2}	-	-	μs	Sampling in 16 states
		Max. = 400 Ω	0.40 (0.183) ^{*2}	-	-	μs	Sampling in 11 states VCC = AVCC0 = 3.0 to 3.6 V 3.0 V ≤ VREFH0 ≤ AVCC0
	Offset error		-	±1.0	±2.5	LSB	-
	Full-scale error		-	±1.0	±2.5	LSB	-
	Absolute accuracy		-	±2.0	±4.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±1.5	LSB	-
INL integral nonlinearity error		-	±1.0	±2.5	LSB	-	
Normal-precision channels (AN016 to AN020)	Conversion time ^{*1} (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.88 (0.667) ^{*2}	-	-	μs	Sampling in 40 states
		Offset error	-	±1.0	±5.5	LSB	-
	Full-scale error		-	±1.0	±5.5	LSB	-
	Absolute accuracy		-	±2.0	±7.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±4.5	LSB	-
	INL integral nonlinearity error		-	±1.0	±5.5	LSB	-

Note: These specification values apply when there is no access to the external bus during A/D conversion. If access occurs during A/D conversion, values might not fall within the indicated ranges.

The use of ports 0 as digital outputs is not allowed when the 12-Bit A/D converter is used.

The characteristics apply when AVCC0, AVSS0, VREFH0, VREFH, VREFL0, VREFL, and 12-bit A/D converter input voltage is stable.

Note 1. The conversion time includes the sampling and comparison times. The number of sampling states is indicated for the test conditions.

Note 2. Values in parentheses indicate the sampling time.

Table 2.41 A/D conversion characteristics for unit 1 (1 of 2)

Conditions: PCLKC = 1 to 60 MHz

Parameter			Min	Typ	Max	Unit	Test conditions
Frequency			1	-	60	MHz	-
Analog input capacitance			-	-	30	pF	-
Quantization error			-	±0.5	-	LSB	-
Resolution			-	-	12	Bits	-
Channel-dedicated sample-and-hold circuits in use (AN100 to AN102)	Conversion time ^{*1} (operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	1.06 (0.4 + 0.25) ^{*2}	-	-	μs	<ul style="list-style-type: none"> Sampling of channel-dedicated sample-and-hold circuits in 24 states Sampling in 15 states
		Offset error	-	±1.5	±3.5	LSB	AN100 to AN102 = 0.25 V
	Full-scale error		-	±1.5	±3.5	LSB	AN100 to AN102 = VREFH - 0.25 V
	Absolute accuracy		-	±2.5	±5.5	LSB	-
	DNL differential nonlinearity error		-	±1.0	±2.0	LSB	-
	INL integral nonlinearity error		-	±1.5	±3.0	LSB	-
	Holding characteristics of sample-and hold circuits		-	-	20	μs	-
	Dynamic range		0.25	-	VREFH - 0.25	V	-

Table 2.41 A/D conversion characteristics for unit 1 (2 of 2)

Conditions: PCLKC = 1 to 60 MHz

Parameter			Min	Typ	Max	Unit	Test conditions
Channel-dedicated sample-and-hold circuits not in use (AN100 to AN102)	Conversion time ^{*1} (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.48 (0.267) ^{*2}	-	-	μs	Sampling in 16 states
	Offset error		-	±1.0	±2.5	LSB	-
	Full-scale error		-	±1.0	±2.5	LSB	-
	Absolute accuracy		-	±2.0	±4.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±1.5	LSB	-
	INL integral nonlinearity error		-	±1.0	±2.5	LSB	-
High-precision channels (AN103, AN105 to AN107)	Conversion time ^{*1} (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.48 (0.267) ^{*2}	-	-	μs	Sampling in 16 states
		Max. = 400 Ω	0.40 (0.183) ^{*2}	-	-	μs	Sampling in 11 states VCC = AVCC0 = 3.0 to 3.6 V 3.0 V ≤ VREFH ≤ AVCC0
	Offset error		-	±1.0	±2.5	LSB	-
	Full-scale error		-	±1.0	±2.5	LSB	-
	Absolute accuracy		-	±2.0	±4.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±1.5	LSB	-
Normal-precision channels (AN116 to AN119)	Conversion time ^{*1} (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.88 (0.667) ^{*2}	-	-	μs	Sampling in 40 states
		Offset error	-	±1.0	±5.5	LSB	-
	Full-scale error		-	±1.0	±5.5	LSB	-
	Absolute accuracy		-	±2.0	±7.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±4.5	LSB	-
	INL integral nonlinearity error		-	±1.0	±5.5	LSB	-

Note: These specification values apply when there is no access to the external bus during A/D conversion. If access occurs during A/D conversion, values might not fall within the indicated ranges.

The use of ports 0 as digital outputs is not allowed when the 12-Bit A/D converter is used.

The characteristics apply when AVCC0, AVSS0, VREFH0, VREFL0, VREFL, and 12-bit A/D converter input voltage is stable.

Note 1. The conversion time includes the sampling and comparison times. The number of sampling states is indicated for the test conditions.

Note 2. Values in parentheses indicate the sampling time.

Table 2.42 A/D conversion characteristics for simultaneous using of channel-dedicated sample-and-hold circuits in unit0 and unit1

Conditions: PCLKC = 30/60 MHz

Parameter		Min	Typ	Max	Test conditions
Channel-dedicated sample-and-hold circuits in use with continuous sampling function enabled (AN000 to AN002)	Offset error	-	±1.5	±5.0	• PCLKC = 60 MHz • Sampling in 15 states
	Full-scale error	-	±2.5	±5.0	
	Absolute accuracy	-	±4.0	±8.0	
Channel-dedicated sample-and-hold circuits in use with continuous sampling function enabled (AN100 to AN102)	Offset error	-	±1.5	±5.0	• PCLKC = 30 MHz • Sampling in 7 states
	Full-scale error	-	±2.5	±5.0	
	Absolute accuracy	-	±4.0	±8.0	
Channel-dedicated sample-and-hold circuits in use with continuous sampling function enabled (AN000 to AN002)	Offset error	-	±1.5	±3.5	• PCLKC = 30 MHz • Sampling in 7 states
	Full-scale error	-	±1.5	±3.5	
	Absolute accuracy	-	±3.0	±5.5	
Channel-dedicated sample-and-hold circuits in use with continuous sampling function enabled (AN100 to AN102)	Offset error	-	±1.5	±3.5	
	Full-scale error	-	±1.5	±3.5	
	Absolute accuracy	-	±3.0	±5.5	

Note: When simultaneously using channel-dedicated sample-and-hold circuits in unit0 and unit1, setting the ADSHMSR.SHMD bit to 1 is recommended.

Table 2.43 A/D internal reference voltage characteristics

Parameter	Min	Typ	Max	Unit	Test conditions
A/D internal reference voltage	1.13	1.18	1.23	V	-
Sampling time	4.15	-	-	μs	-

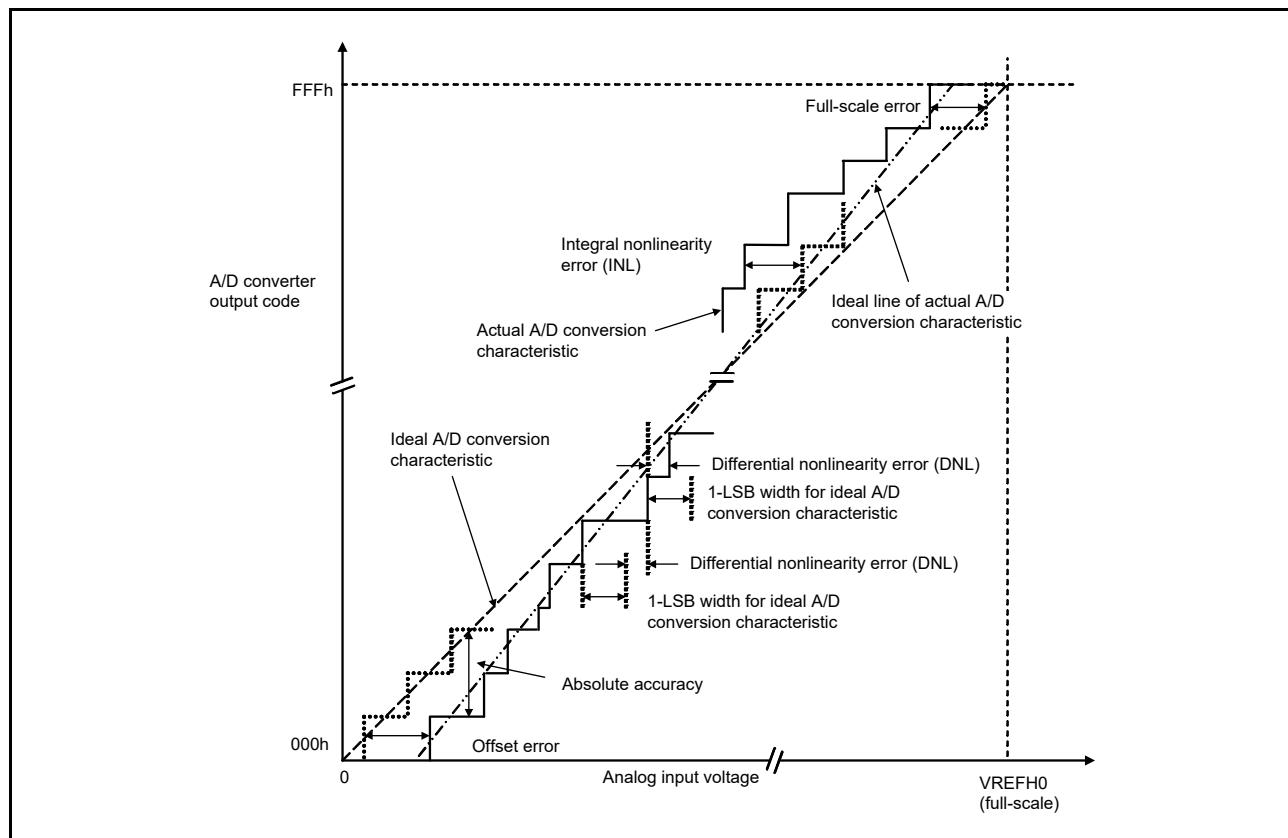


Figure 2.95 Illustration of ADC12 characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of the analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as an analog input voltage. For example, if 12-bit resolution is used and the reference voltage $VREFH0 = 3.072$ V, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, and 1.5 mV are used as the analog input voltages. If the analog input voltage is 6 mV, an absolute accuracy of ± 5 LSB means that the actual A/D conversion result is in the range of 003h to 00Dh, though an output code of 008h can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between the 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.

Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.

2.6 DAC12 Characteristics

Table 2.44 D/A conversion characteristics

Parameter	Min	Typ	Max	Unit	Test conditions
Resolution	-	-	12	Bits	-
Without output amplifier					
Absolute accuracy	-	-	± 24	LSB	Resistive load 2 MΩ
INL	-	± 2.0	± 8.0	LSB	Resistive load 2 MΩ
DNL	-	± 1.0	± 2.0	LSB	-
Output impedance	-	8.5	-	kΩ	-
Conversion time	-	-	3.0	μs	Resistive load 2 MΩ, Capacitive load 20 pF
Output voltage range	0	-	VREFH	V	-
With output amplifier					
INL	-	± 2.0	± 4.0	LSB	-
DNL	-	± 1.0	± 2.0	LSB	-
Conversion time	-	-	4.0	μs	-
Resistive load	5	-	-	kΩ	-
Capacitive load	-	-	50	pF	-
Output voltage range	0.2	-	VREFH - 0.2	V	-

2.7 TSN Characteristics

Table 2.45 TSN characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Relative accuracy	-	-	± 1.0	-	°C	-
Temperature slope	-	-	4.0	-	mV/°C	-
Output voltage (at 25°C)	-	-	1.24	-	V	-
Temperature sensor start time	t _{START}	-	-	30	μs	-
Sampling time	-	4.15	-	-	μs	-

2.8 OSC Stop Detect Characteristics

Table 2.46 Oscillation stop detection circuit characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Detection time	t _{dr}	-	-	1	ms	Figure 2.96

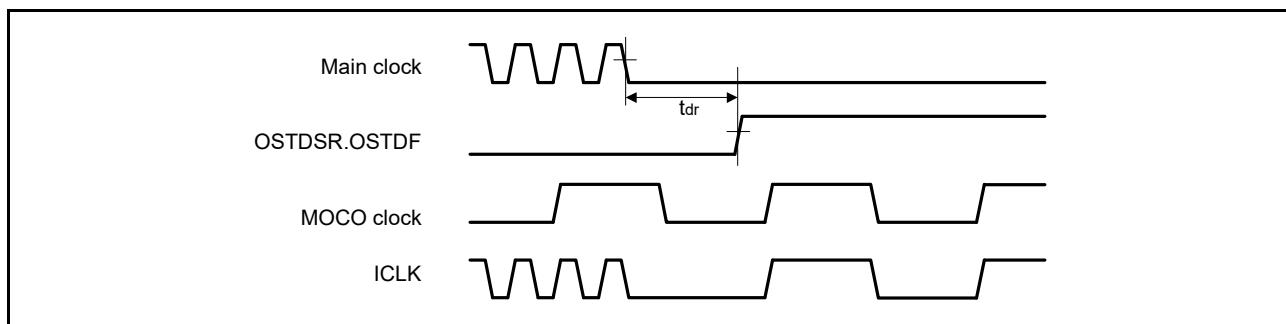


Figure 2.96 Oscillation stop detection timing

2.9 POR and LVD Characteristics

Table 2.47 Power-on reset circuit and voltage detection circuit characteristics

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions		
Voltage detection level	Power-on reset (POR)	Module-stop function disabled* ²	V _{POR}	2.5	2.6	2.7	V	Figure 2.97		
		Module-stop function enabled* ³		1.8	2.25	2.7				
	Voltage detection circuit (LVD0)		V _{det0_1}	2.84	2.94	3.04		Figure 2.98		
			V _{det0_2}	2.77	2.87	2.97				
			V _{det0_3}	2.70	2.80	2.90				
	Voltage detection circuit (LVD1)		V _{det1_1}	2.89	2.99	3.09		Figure 2.99		
			V _{det1_2}	2.82	2.92	3.02				
			V _{det1_3}	2.75	2.85	2.95				
	Voltage detection circuit (LVD2)		V _{det2_1}	2.89	2.99	3.09		Figure 2.100		
			V _{det2_2}	2.82	2.92	3.02				
			V _{det2_3}	2.75	2.85	2.95				
Internal reset time	Power-on reset time		t _{POR}	-	4.5	-	ms	Figure 2.97		
	LVD0 reset time		t _{LVD0}	-	0.51	-		Figure 2.98		
	LVD1 reset time		t _{LVD1}	-	0.38	-		Figure 2.99		
	LVD2 reset time		t _{LVD2}	-	0.38	-		Figure 2.100		
Minimum VCC down time* ¹			t _{VOFF}	200	-	-	μs	Figure 2.97, Figure 2.98		
Response delay			t _{det}	-	-	200	μs	Figure 2.97 to Figure 2.100		
LVD operation stabilization time (after LVD is enabled)			t _{d(E-A)}	-	-	10	μs	Figure 2.99, Figure 2.100		
Hysteresis width (LVD1 and LVD2)			V _{LVH}	-	70	-	mV			

Note 1. The minimum VCC down time indicates the time when VCC is below the minimum value of voltage detection levels V_{POR}, V_{det1}, and V_{det2} for POR and LVD.

Note 2. The low-power function is disabled and DEEPCUT[1:0] = 00b or 01b.

Note 3. The low-power function is enabled and DEEPCUT[1:0] = 11b.

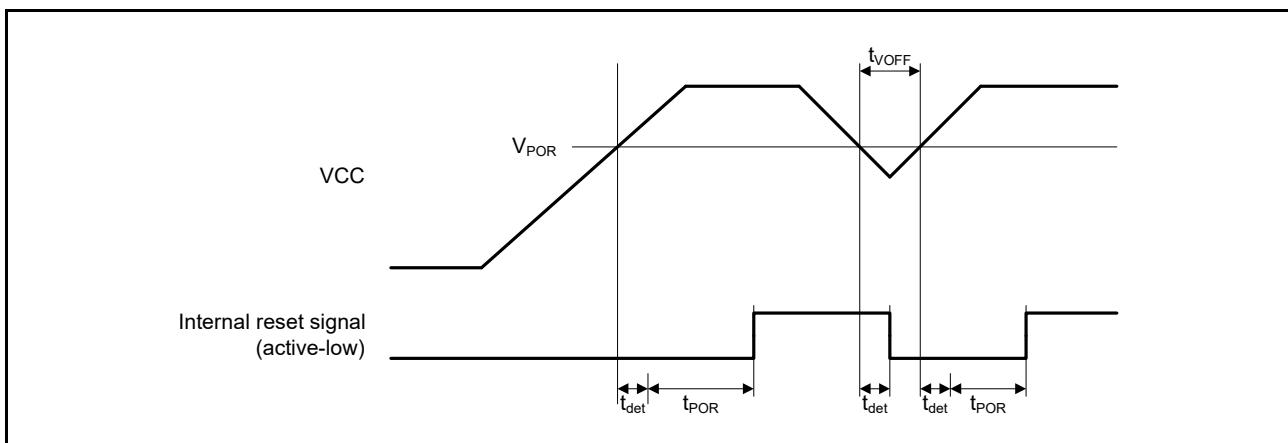


Figure 2.97 Power-on reset timing

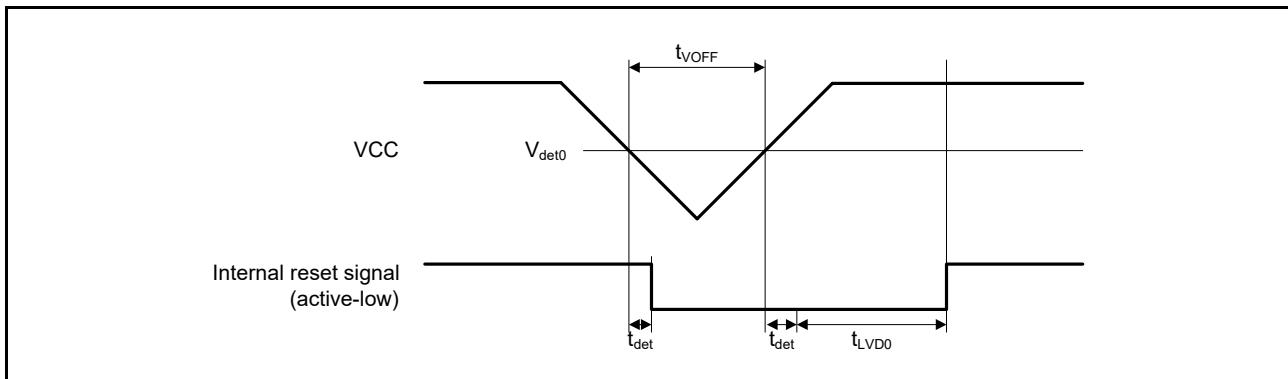
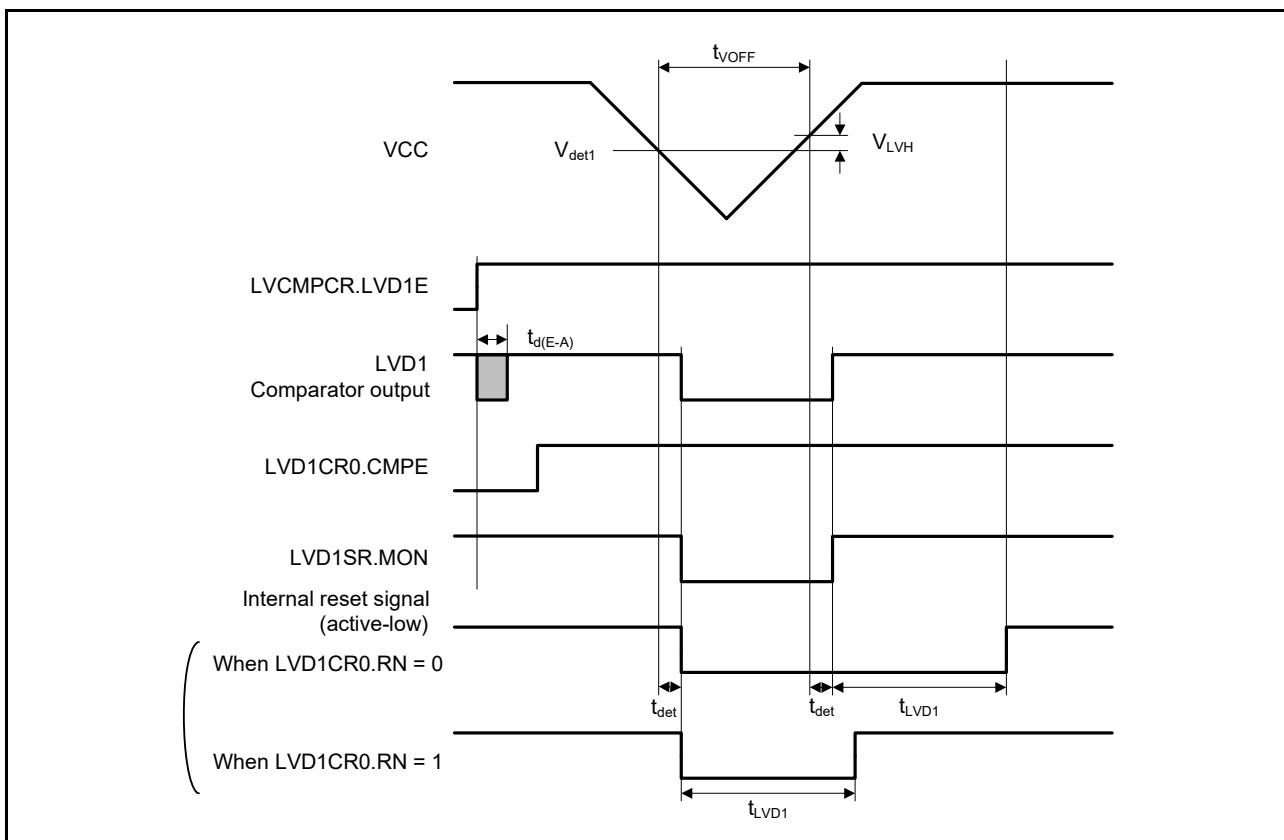
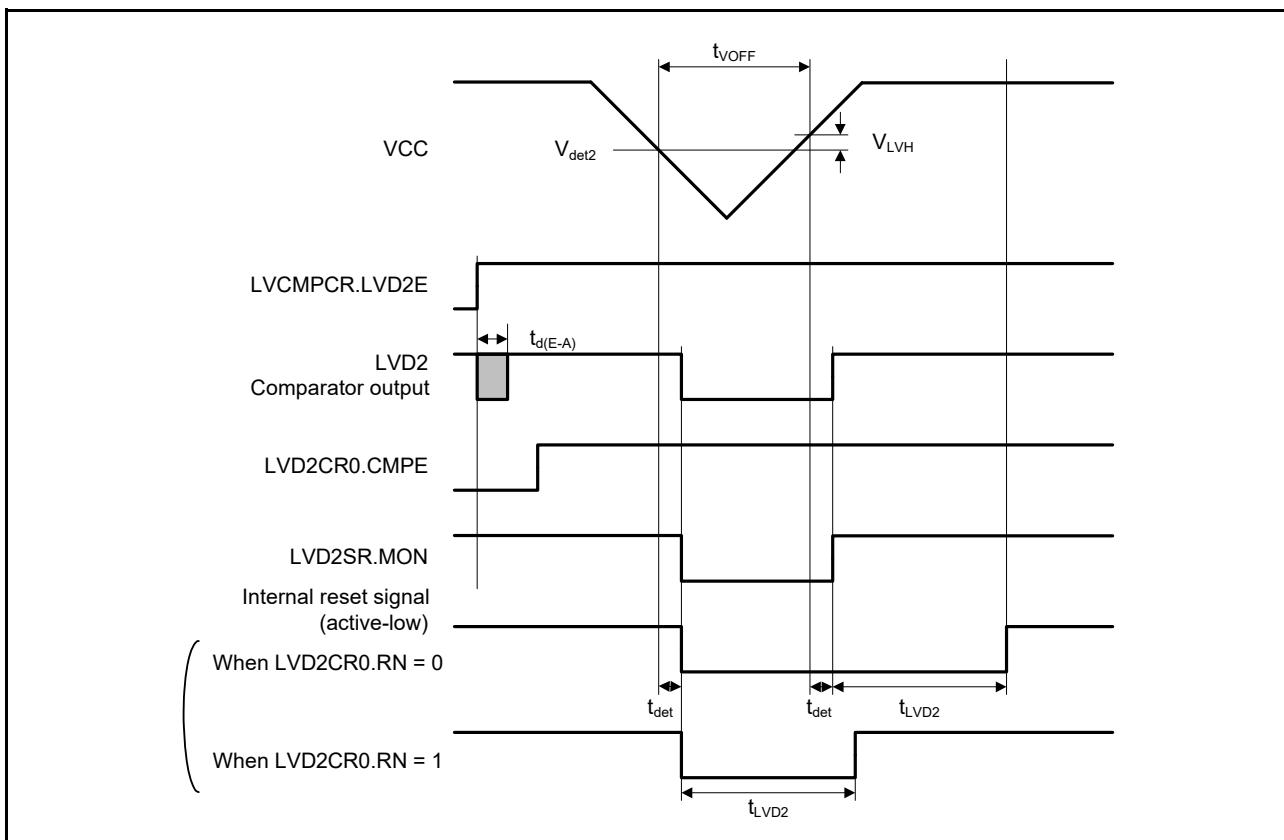


Figure 2.98 Voltage detection circuit timing (V_{det0})

Figure 2.99 Voltage detection circuit timing (V_{det1})Figure 2.100 Voltage detection circuit timing (V_{det2})

2.10 VBATT Characteristics

Table 2.48 Battery backup function characteristics

Conditions: VCC = AVCC0 = VCC_USB = 2.7 to 3.6 V, 2.7 ≤ VREFH0/VREFH ≤ AVCC0, VBATT = 1.8 to 3.6 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Voltage level for switching to battery backup	$V_{DETBATT}$	2.50	2.60	2.70	V	Figure 2.101
Lower-limit VBATT voltage for power supply switching caused by VCC voltage drop	V_{BATTSW}	2.70	-	-	V	
VCC-off period for starting power supply switching	$t_{VOFFBATT}$	200	-	-	μs	

Note: The VCC-off period for starting power supply switching indicates the period in which VCC is below the minimum value of the voltage level for switching to battery backup ($V_{DETBATT}$).

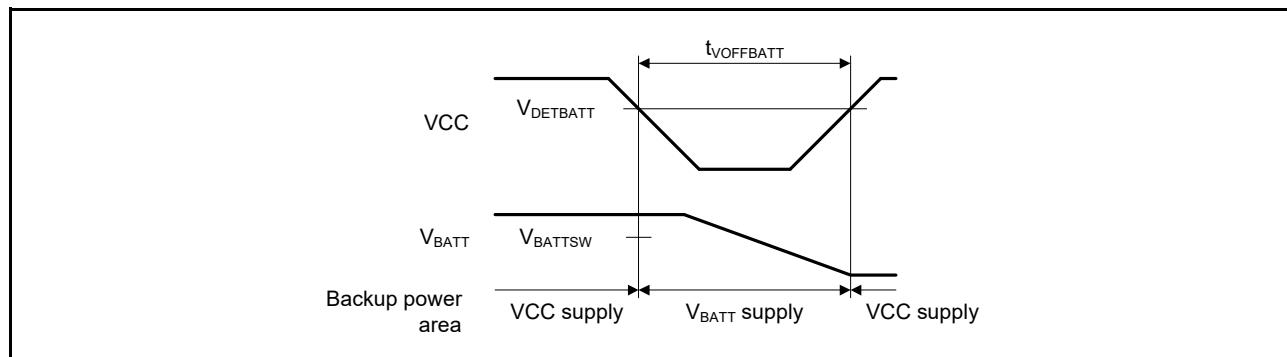


Figure 2.101 Battery backup function characteristics

2.11 CTSU Characteristics

Table 2.49 CTSU characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
External capacitance connected to TSCAP pin	C_{tscap}	9	10	11	nF	-
TS pin capacitive load	C_{base}	-	-	50	pF	-
Permissible output high current	Σ_{IOH}	-	-	-40	mA	When the mutual capacitance method is applied

2.12 ACMPHS Characteristics

Table 2.50 ACMPHS characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Reference voltage range	V_{REF}	0	-	AVCC0	V	-
Input voltage range	V_I	0	-	AVCC0	V	-
Output delay*1	T_d	-	50	100	ns	$V_I = V_{REF} \pm 100 \text{ mV}$
Internal reference voltage	V_{ref}	1.13	1.18	1.23	V	-

Note 1. This value is the internal propagation delay.

2.13 PGA Characteristics

Table 2.51 PGA characteristics in single mode

Parameter	Symbol	Min	Typ	Max	Unit
PGAVSS input voltage range	PGAVSS	0	-	0	V
	AIN0 (G = 2.000)	$0.050 \times AVCC_0$	-	$0.45 \times AVCC_0$	V
	AIN1 (G = 2.500)	$0.047 \times AVCC_0$	-	$0.360 \times AVCC_0$	V
	AIN2 (G = 2.667)	$0.046 \times AVCC_0$	-	$0.337 \times AVCC_0$	V
	AIN3 (G = 2.857)	$0.046 \times AVCC_0$	-	$0.32 \times AVCC_0$	V
	AIN4 (G = 3.077)	$0.045 \times AVCC_0$	-	$0.292 \times AVCC_0$	V
	AIN5 (G = 3.333)	$0.044 \times AVCC_0$	-	$0.265 \times AVCC_0$	V
	AIN6 (G = 3.636)	$0.042 \times AVCC_0$	-	$0.247 \times AVCC_0$	V
	AIN7 (G = 4.000)	$0.040 \times AVCC_0$	-	$0.212 \times AVCC_0$	V
	AIN8 (G = 4.444)	$0.036 \times AVCC_0$	-	$0.191 \times AVCC_0$	V
	AIN9 (G = 5.000)	$0.033 \times AVCC_0$	-	$0.17 \times AVCC_0$	V
	AIN10 (G = 5.714)	$0.031 \times AVCC_0$	-	$0.148 \times AVCC_0$	V
	AIN11 (G = 6.667)	$0.029 \times AVCC_0$	-	$0.127 \times AVCC_0$	V
	AIN12 (G = 8.000)	$0.027 \times AVCC_0$	-	$0.09 \times AVCC_0$	V
	AIN13 (G = 10.000)	$0.025 \times AVCC_0$	-	$0.08 \times AVCC_0$	V
	AIN14 (G = 13.333)	$0.023 \times AVCC_0$	-	$0.06 \times AVCC_0$	V
Gain error	Gerr0 (G = 2.000)	-1.0	-	1.0	%
	Gerr1 (G = 2.500)	-1.0	-	1.0	%
	Gerr2 (G = 2.667)	-1.0	-	1.0	%
	Gerr3 (G = 2.857)	-1.0	-	1.0	%
	Gerr4 (G = 3.077)	-1.0	-	1.0	%
	Gerr5 (G = 3.333)	-1.5	-	1.5	%
	Gerr6 (G = 3.636)	-1.5	-	1.5	%
	Gerr7 (G = 4.000)	-1.5	-	1.5	%
	Gerr8 (G = 4.444)	-2.0	-	2.0	%
	Gerr9 (G = 5.000)	-2.0	-	2.0	%
	Gerr10 (G = 5.714)	-2.0	-	2.0	%
	Gerr11 (G = 6.667)	-2.0	-	2.0	%
	Gerr12 (G = 8.000)	-2.0	-	2.0	%
	Gerr13 (G = 10.000)	-2.0	-	2.0	%
	Gerr14 (G = 13.333)	-2.0	-	2.0	%
Offset error	Voff	-8	-	8	mV

Table 2.52 PGA characteristics in differential mode (1 of 2)

Parameter	Symbol	Min	Typ	Max	Unit
PGAVSS input voltage range	PGAVSS	-0.5	-	0.3	V
Differential input voltage range	G = 1.500	AIN-PGAVSS	-0.5	-	0.5
	G = 2.333		-0.4	-	0.4
	G = 4.000		-0.2	-	0.2
	G = 5.667		-0.15	-	0.15

Table 2.52 PGA characteristics in differential mode (2 of 2)

Parameter	Symbol	Min	Typ	Max	Unit
Gain error	G = 1.500	Gerr	-1.0	-	1.0
	G = 2.333		-1.0	-	1.0
	G = 4.000		-1.0	-	1.0
	G = 5.667		-1.0	-	1.0

2.14 Flash Memory Characteristics

2.14.1 Code Flash Memory Characteristics

Table 2.53 Code flash memory characteristics

Conditions: Program or erase: FCLK = 4 to 60 MHz

Read: FCLK ≤ 60 MHz

Parameter	Symbol	FCLK = 4 MHz			20 MHz ≤ FCLK ≤ 60 MHz			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Programming time N _{PEC} ≤ 100 times	t _{P128}	-	0.75	13.2	-	0.34	6.0	ms	
	t _{P8K}	-	49	176	-	22	80	ms	
	t _{P32K}	-	194	704	-	88	320	ms	
Programming time N _{PEC} > 100 times	t _{P128}	-	0.91	15.8	-	0.41	7.2	ms	
	t _{P8K}	-	60	212	-	27	96	ms	
	t _{P32K}	-	234	848	-	106	384	ms	
Erasure time N _{PEC} ≤ 100 times	t _{E8K}	-	78	216	-	43	120	ms	
	t _{E32K}	-	283	864	-	157	480	ms	
Erasure time N _{PEC} > 100 times	t _{E8K}	-	94	260	-	52	144	ms	
	t _{E32K}	-	341	1040	-	189	576	ms	
Reprogramming/erasure cycle*Note:	N _{PEC}	10000*1	-	-	10000*1	-	-	Times	
Suspend delay during programming	t _{SPD}	-	-	264	-	-	120	μs	
First suspend delay during erasure in suspend priority mode	t _{SESD1}	-	-	216	-	-	120	μs	
Second suspend delay during erasure in suspend priority mode	t _{SESD2}	-	-	1.7	-	-	1.7	ms	
Suspend delay during erasure in erasure priority mode	t _{SEED}	-	-	1.7	-	-	1.7	ms	
Forced stop command	t _{FD}	-	-	32	-	-	20	μs	
Data hold time*2	t _{DRP}	10*2, *3	-	-	10*2, *3	-	-	Years	
		30*2, *3	-	-	30*2, *3	-	-		Ta = +85°C

Note: The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 10,000), erasing can be performed n times for each block. For example, when 128-byte programming is performed 64 times for different addresses in 8-KB blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address several times as one erasure is not enabled. (Overwriting is prohibited.)

Note 1. This is the minimum number of times to guarantee all the characteristics after reprogramming. The guaranteed range is from 1 to the minimum value.

Note 2. This indicates the minimum value of the characteristic when reprogramming is performed within the specified range.

Note 3. This result is obtained from reliability testing.

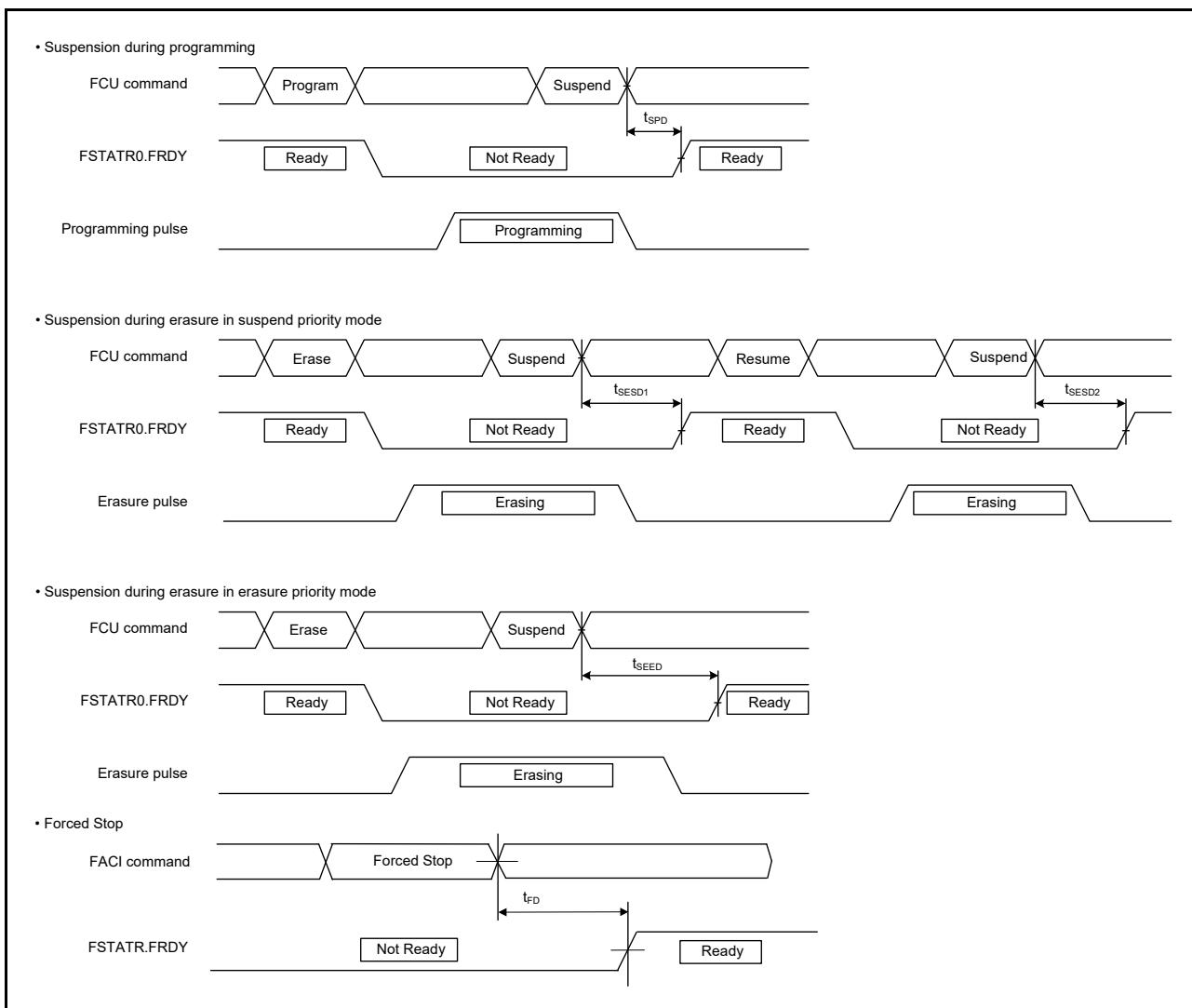


Figure 2.102 Suspension and forced stop timing for flash memory programming and erasure

2.14.2 Data Flash Memory Characteristics

Table 2.54 Data flash memory characteristics (1 of 2)Conditions: Program or erase: $FCLK = 4$ to 60 MHzRead: $FCLK \leq 60$ MHz

Parameter	Symbol	FCLK = 4 MHz			20 MHz \leq FCLK \leq 60 MHz			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Programming time	4-byte	t_{DP4}	-	0.36	3.8	-	0.16	1.7	ms
	8-byte	t_{DP8}	-	0.38	4.0	-	0.17	1.8	
	16-byte	t_{DP16}	-	0.42	4.5	-	0.19	2.0	
Erasure time	64-byte	t_{DE64}	-	3.1	18	-	1.7	10	ms
	128-byte	t_{DE128}	-	4.7	27	-	2.6	15	
	256-byte	t_{DE256}	-	8.9	50	-	4.9	28	
Blank check time	4-byte	t_{DBC4}	-	-	84	-	-	30	μs
Reprogramming/erasure cycle*1		N_{DPEC}	125000 *2	-	-	125000 *2	-	-	

Table 2.54 Data flash memory characteristics (2 of 2)

Conditions: Program or erase: FCLK = 4 to 60 MHz

Read: FCLK ≤ 60 MHz

Parameter	Symbol	FCLK = 4 MHz			20 MHz ≤ FCLK ≤ 60 MHz			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Suspend delay during programming	t _{DSPD}	-	-	264	-	-	120	μs	
		-	-	264	-	-	120		
		-	-	264	-	-	120		
First suspend delay during erasure in suspend priority mode	t _{DSESD1}	-	-	216	-	-	120	μs	
		-	-	216	-	-	120		
		-	-	216	-	-	120		
Second suspend delay during erasure in suspend priority mode	t _{DSESD2}	-	-	300	-	-	300	μs	
		-	-	390	-	-	390		
		-	-	570	-	-	570		
Suspend delay during erasing in erasure priority mode	t _{DSEED}	-	-	300	-	-	300	μs	
		-	-	390	-	-	390		
		-	-	570	-	-	570		
Forced stop command	t _{FD}	-	-	32	-	-	20	μs	
Data hold time ^{*3}	t _{DRP}	10 ^{*3,*4}	-	-	10 ^{*3,*4}	-	-	Year	
		30 ^{*3,*4}	-	-	30 ^{*3,*4}	-	-		Ta = +85°C

Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 125,000), erasing can be performed n times for each block. For example, when 4-byte programming is performed 16 times for different addresses in 64-byte blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address several times as one erasure is not enabled. (Overwriting is prohibited.)

Note 2. This is the minimum number of times to guarantee all the characteristics after reprogramming. The guaranteed range is from 1 to the minimum value.

Note 3. This indicates the minimum value of the characteristic when reprogramming is performed within the specified range.

Note 4. This result is obtained from reliability testing.

2.15 Boundary Scan

Table 2.55 Boundary scan characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
TCK clock cycle time	t _{TCKcyc}	100	-	-	ns	Figure 2.103
TCK clock high pulse width	t _{TCKH}	45	-	-	ns	
TCK clock low pulse width	t _{TCKL}	45	-	-	ns	
TCK clock rise time	t _{TCKr}	-	-	5	ns	
TCK clock fall time	t _{TCKf}	-	-	5	ns	
TMS setup time	t _{TMSS}	20	-	-	ns	Figure 2.104
TMS hold time	t _{TMSH}	20	-	-	ns	
TDI setup time	t _{TDIS}	20	-	-	ns	
TDI hold time	t _{TDIH}	20	-	-	ns	
TDO data delay	t _{TDOD}	-	-	40	ns	
Boundary scan circuit startup time ^{*1}	T _{BSSTUP}	t _{RESWP}	-	-	-	Figure 2.105

Note 1. Boundary scan does not function until the power-on reset becomes negative.

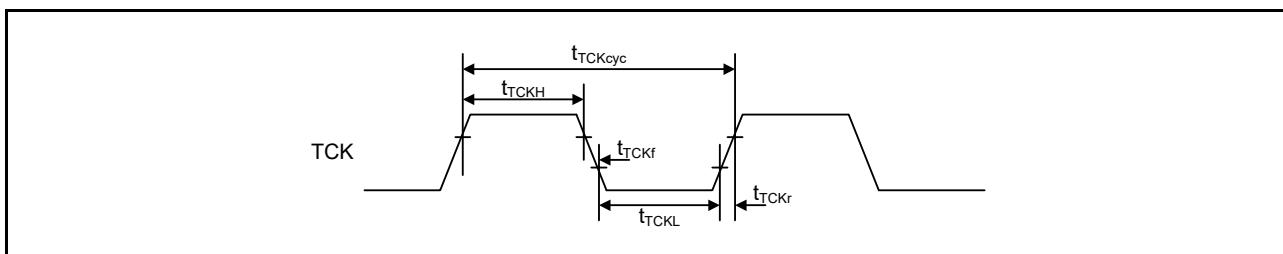


Figure 2.103 Boundary scan TCK timing

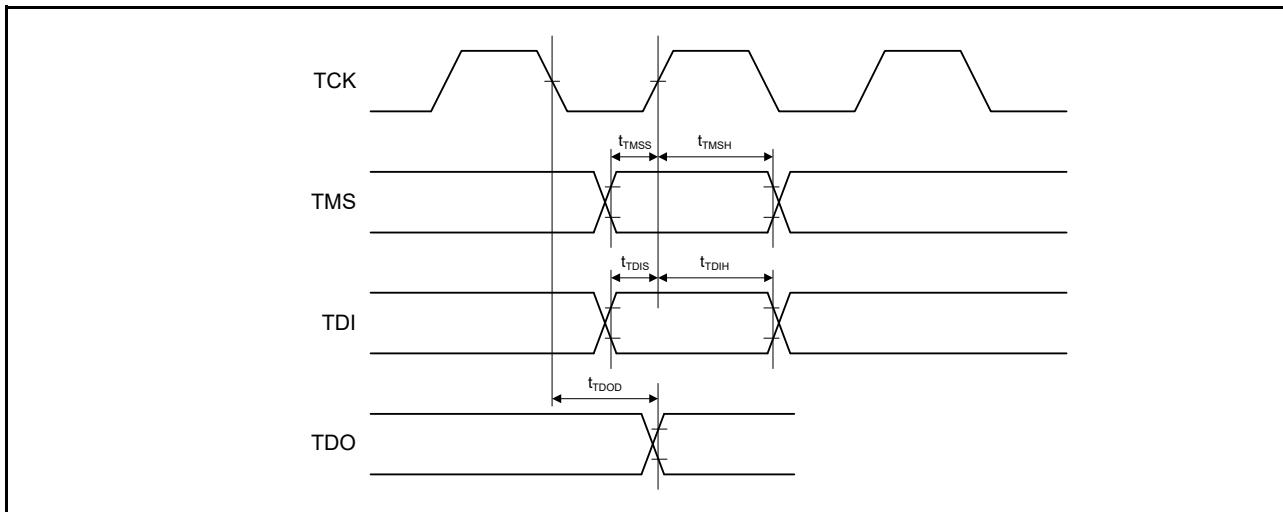


Figure 2.104 Boundary scan input/output timing

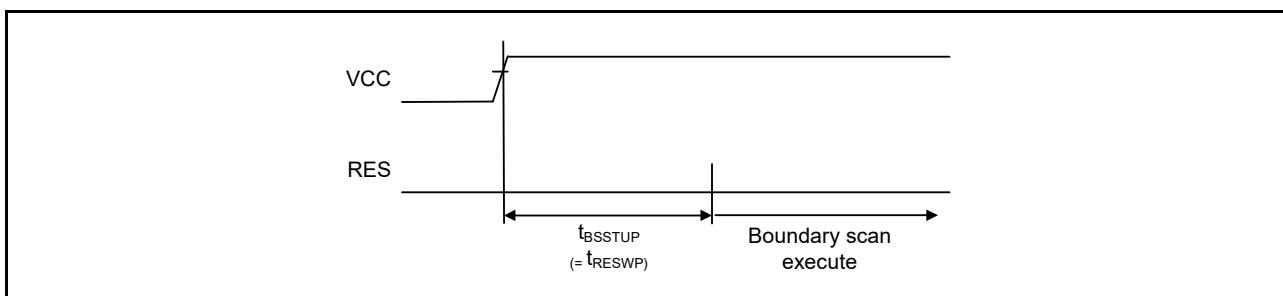


Figure 2.105 Boundary scan circuit startup timing

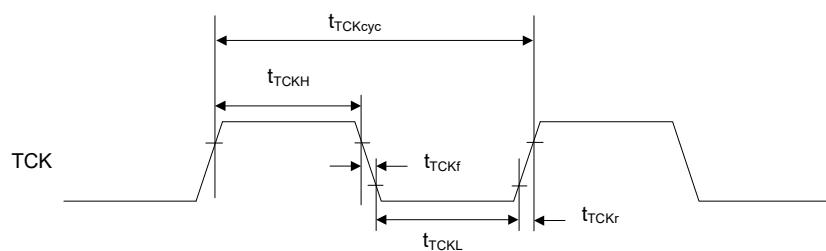
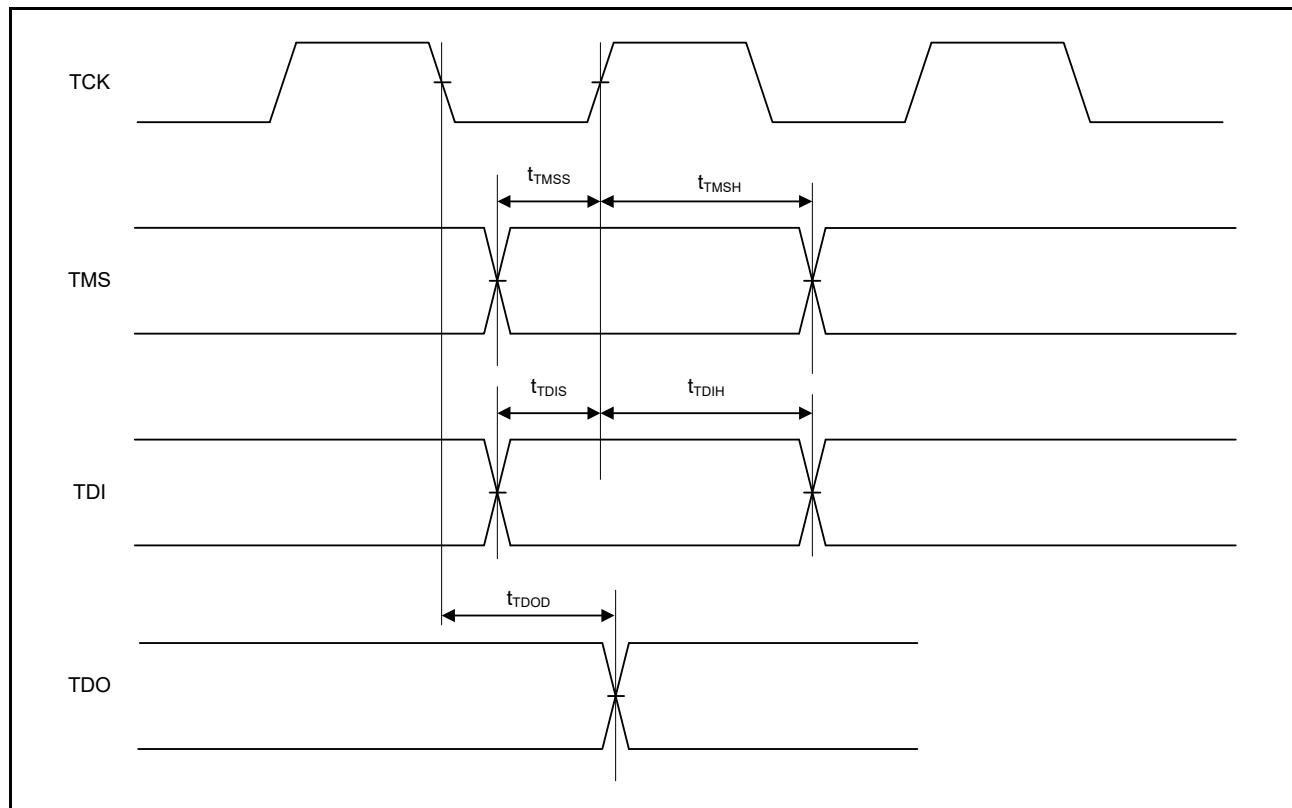
2.16 Joint Test Action Group (JTAG)

Table 2.56 JTAG

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
TCK clock cycle time	t_{TCKcyc}	40	-	-	ns	Figure 2.103
TCK clock high pulse width	t_{TCKH}	15	-	-	ns	
TCK clock low pulse width	t_{TCKL}	15	-	-	ns	
TCK clock rise time	t_{TCKr}	-	-	5	ns	
TCK clock fall time	t_{TCKf}	-	-	5	ns	

Table 2.56 JTAG

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
TMS setup time	t_{TMSS}	8	-	-	ns	Figure 2.104
TMS hold time	t_{TMSH}	8	-	-	ns	
TDI setup time	t_{TDIS}	8	-	-	ns	
TDI hold time	t_{TDIH}	8	-	-	ns	
TDO data delay time	t_{TDOD}	-	-	20	ns	

**Figure 2.106 JTAG TCK timing****Figure 2.107 JTAG input/output timing**

2.17 Serial Wire Debug (SWD)

Table 2.57 SWD

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
SWCLK clock cycle time	$t_{SWCKcyc}$	40	-	-	ns	Figure 2.108
SWCLK clock high pulse width	t_{SWCKH}	15	-	-	ns	
SWCLK clock low pulse width	t_{SWCKL}	15	-	-	ns	
SWCLK clock rise time	t_{SWCKr}	-	-	5	ns	
SWCLK clock fall time	t_{SWCKf}	-	-	5	ns	
SWDIO setup time	t_{SWDS}	8	-	-	ns	Figure 2.109
SWDIO hold time	t_{SWDH}	8	-	-	ns	
SWDIO data delay time	t_{SWDD}	2	-	28	ns	

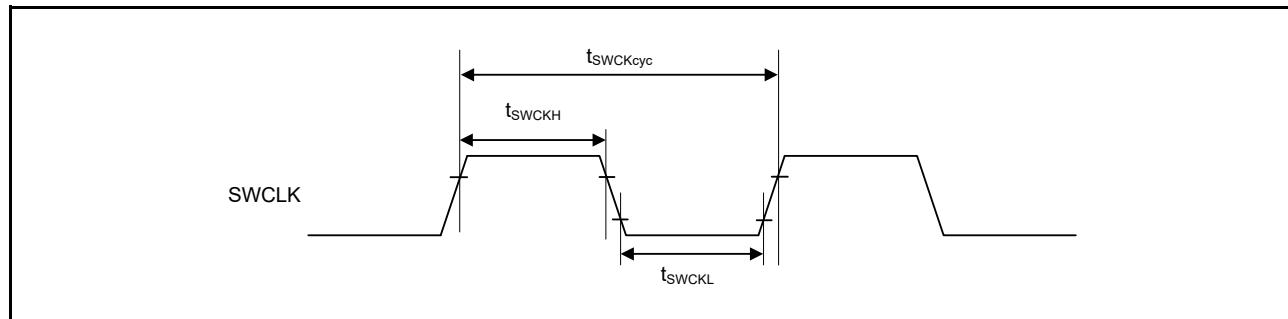


Figure 2.108 SWD SWCLK timing

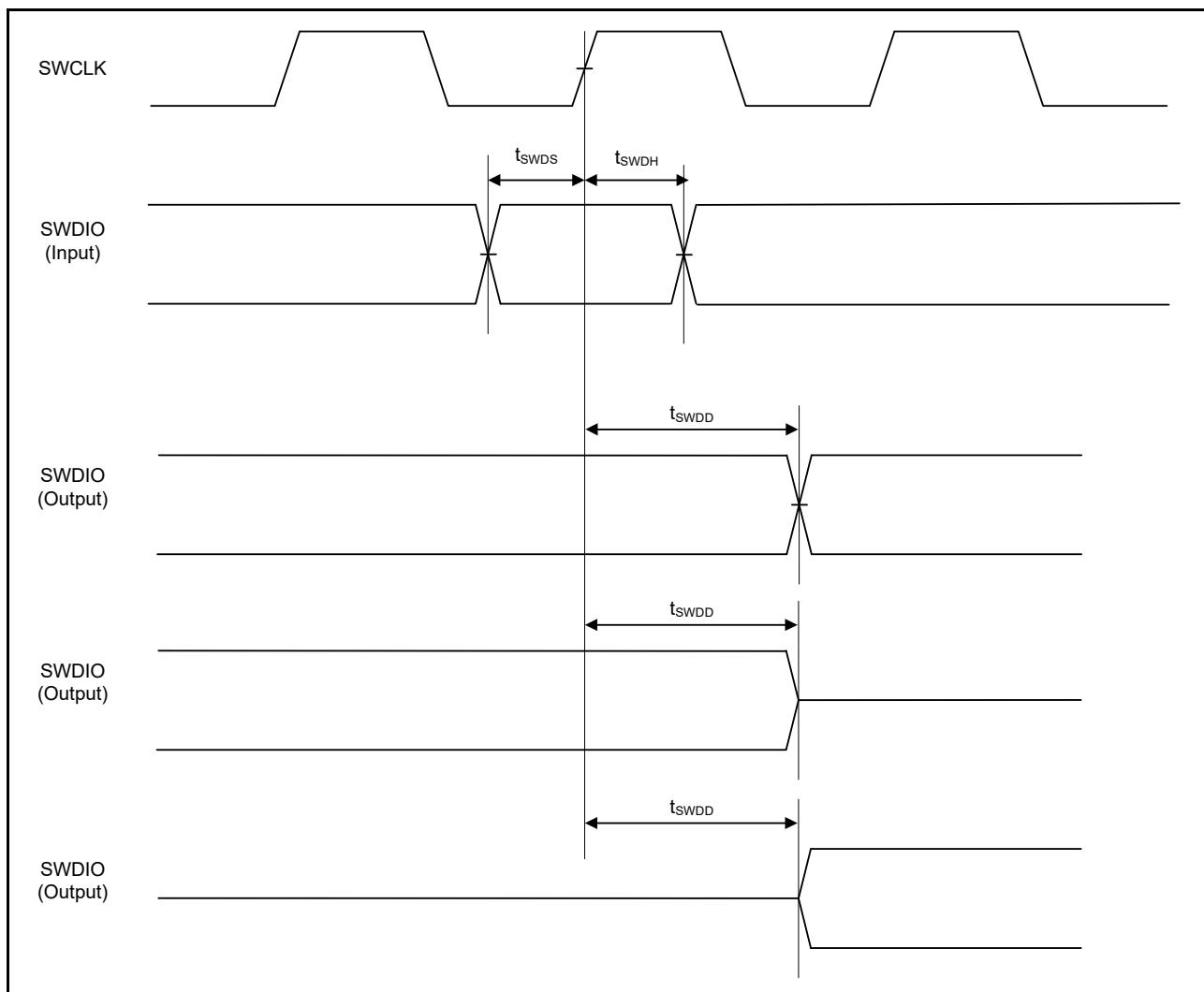


Figure 2.109 SWD input/output timing

2.18 Embedded Trace Macro Interface (ETM)

Table 2.58 ETM

Conditions: High drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
TCLK clock cycle time	t_TCLKcyc	33.3	-	-	ns	Figure 2.110
TCLK clock high pulse width	t_TCLKH	13.6	-	-	ns	
TCLK clock low pulse width	t_TCLKL	13.6	-	-	ns	
TCLK clock rise time	t_TCLKr	-	-	3	ns	
TCLK clock fall time	t_TCLKf	-	-	3	ns	
TDATA[3:0] output setup time	t_TRDS	3.5	-	-	ns	
TDATA[3:0] output hold time	t_TRDH	2.5	-	-	ns	

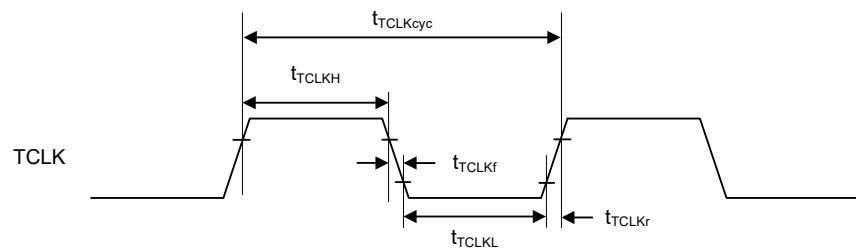


Figure 2.110 ETM TCLK timing

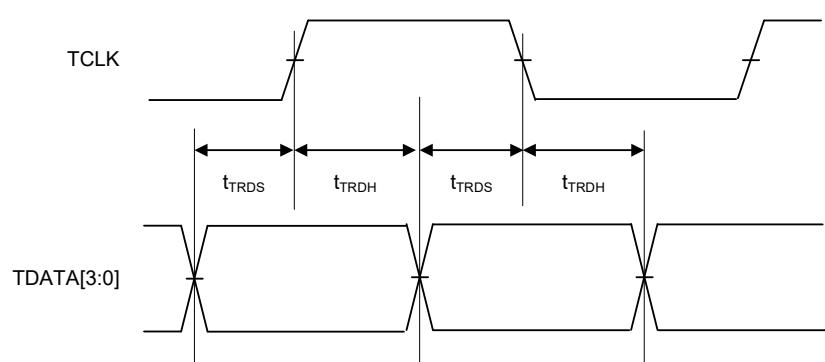


Figure 2.111 ETM output timing

Appendix 1.Package Dimensions

For information on the latest version of the package dimensions or mountings, go to “Packages” on the Renesas Electronics Corporation website.

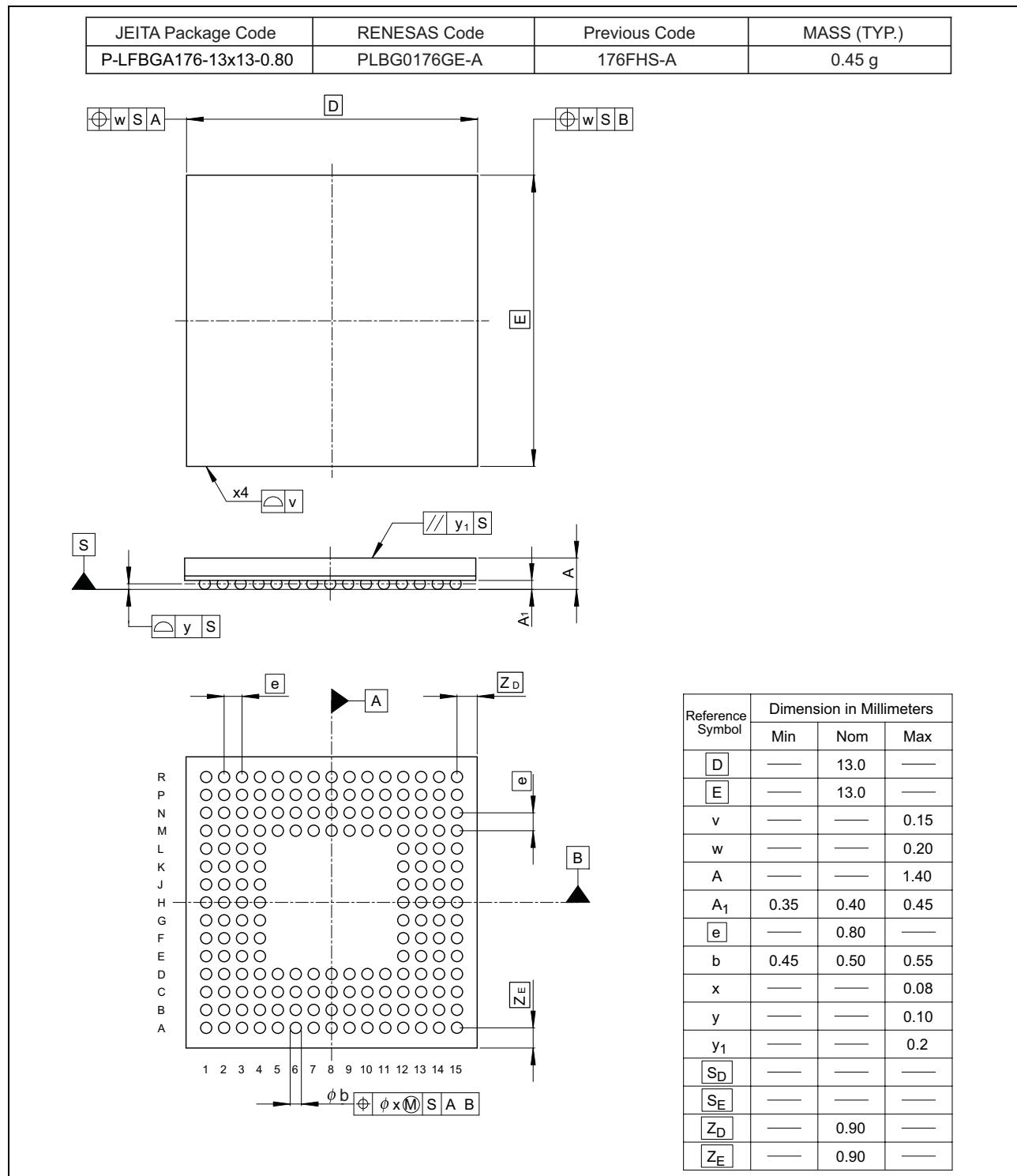


Figure 1.1 176-pin BGA

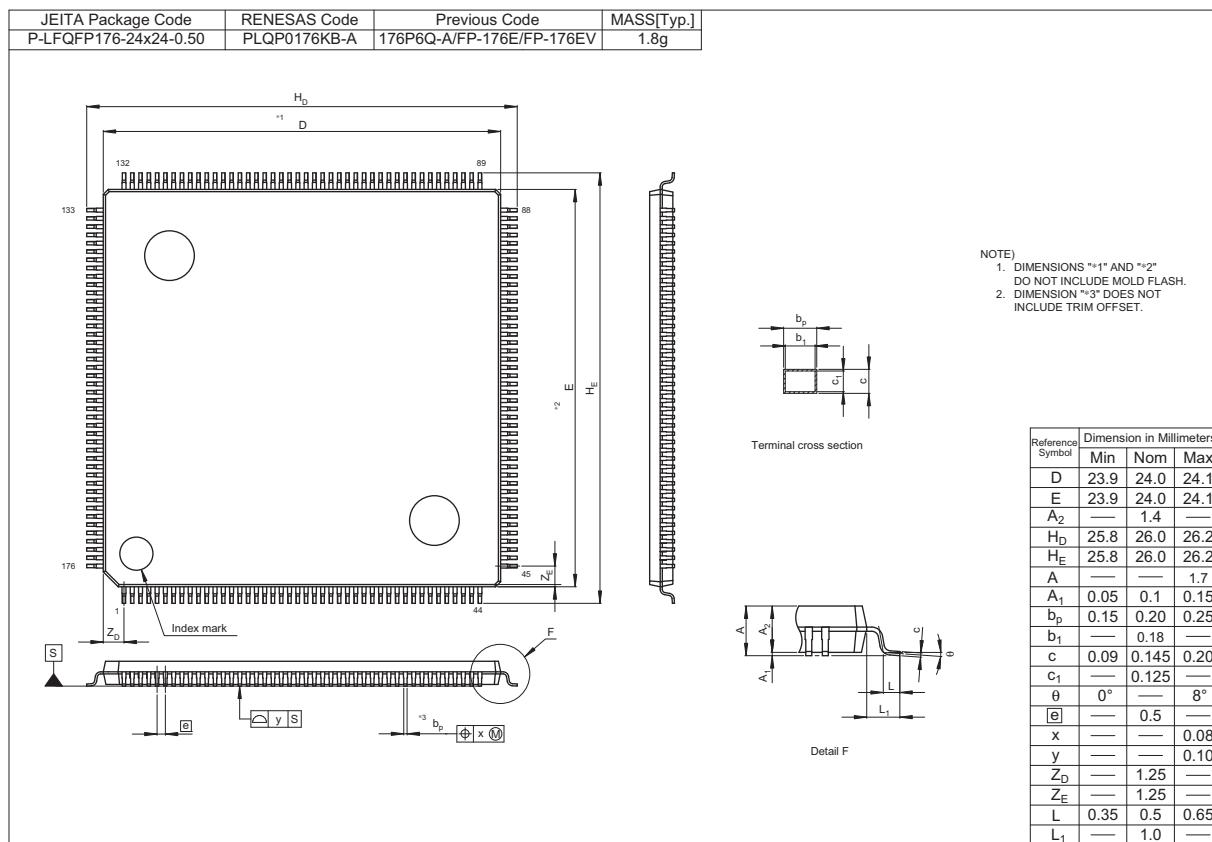


Figure 1.2 176-pin LQFP

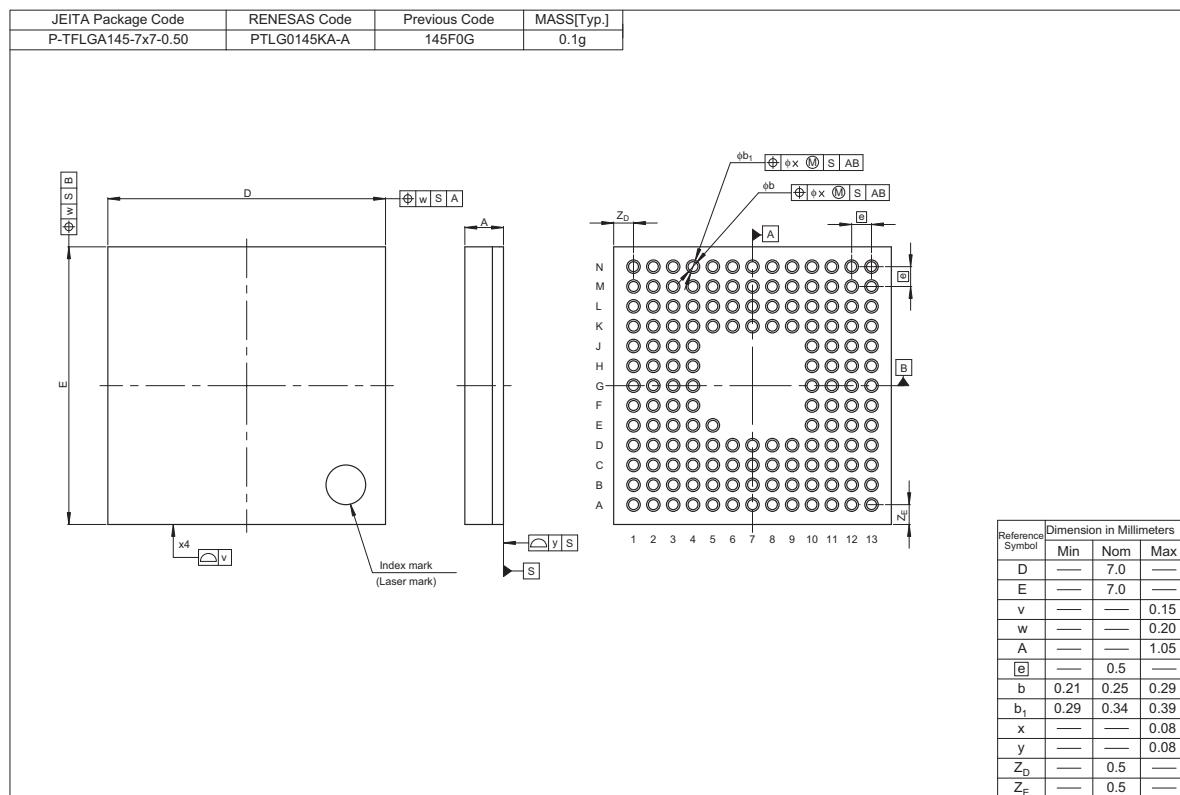
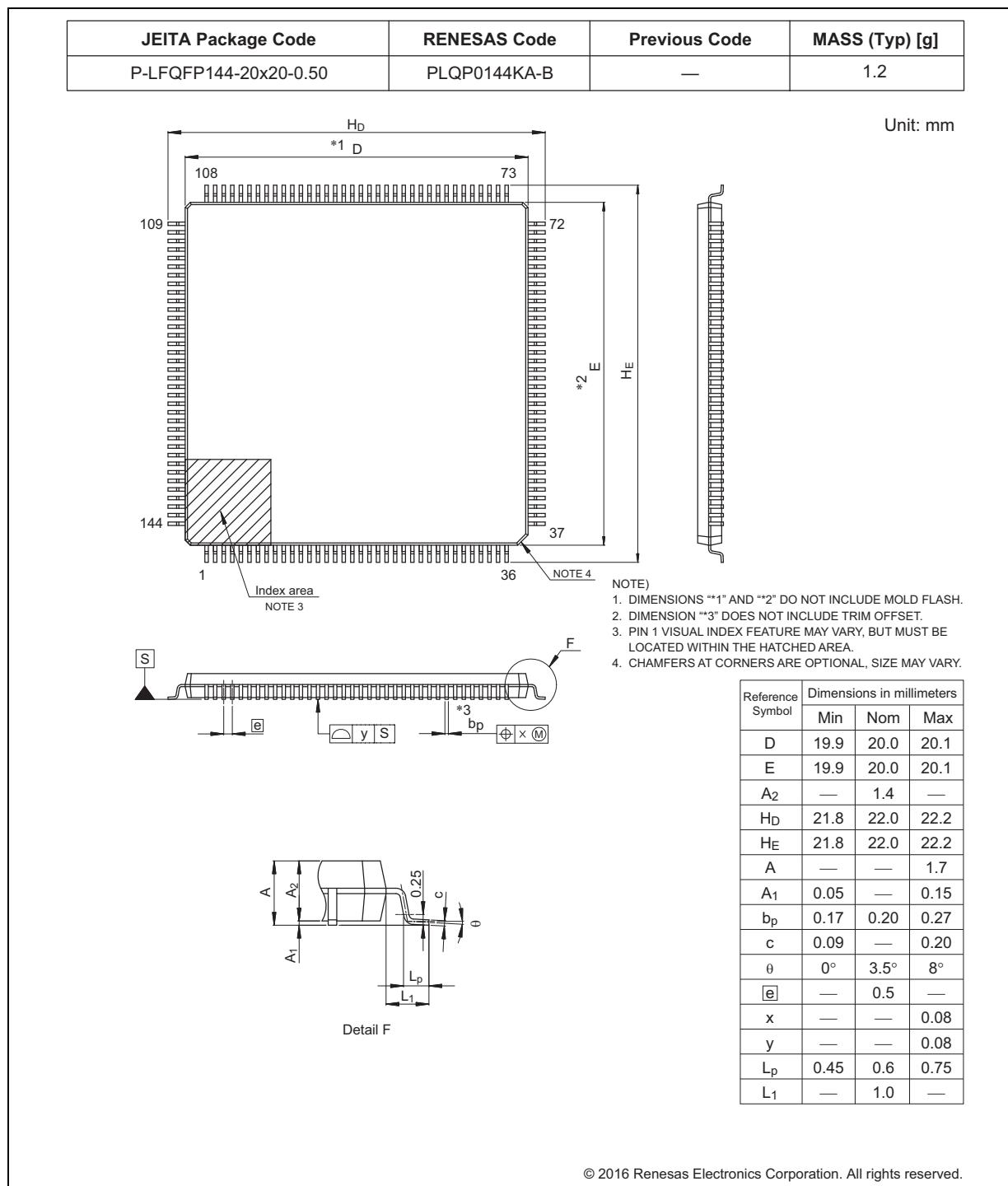
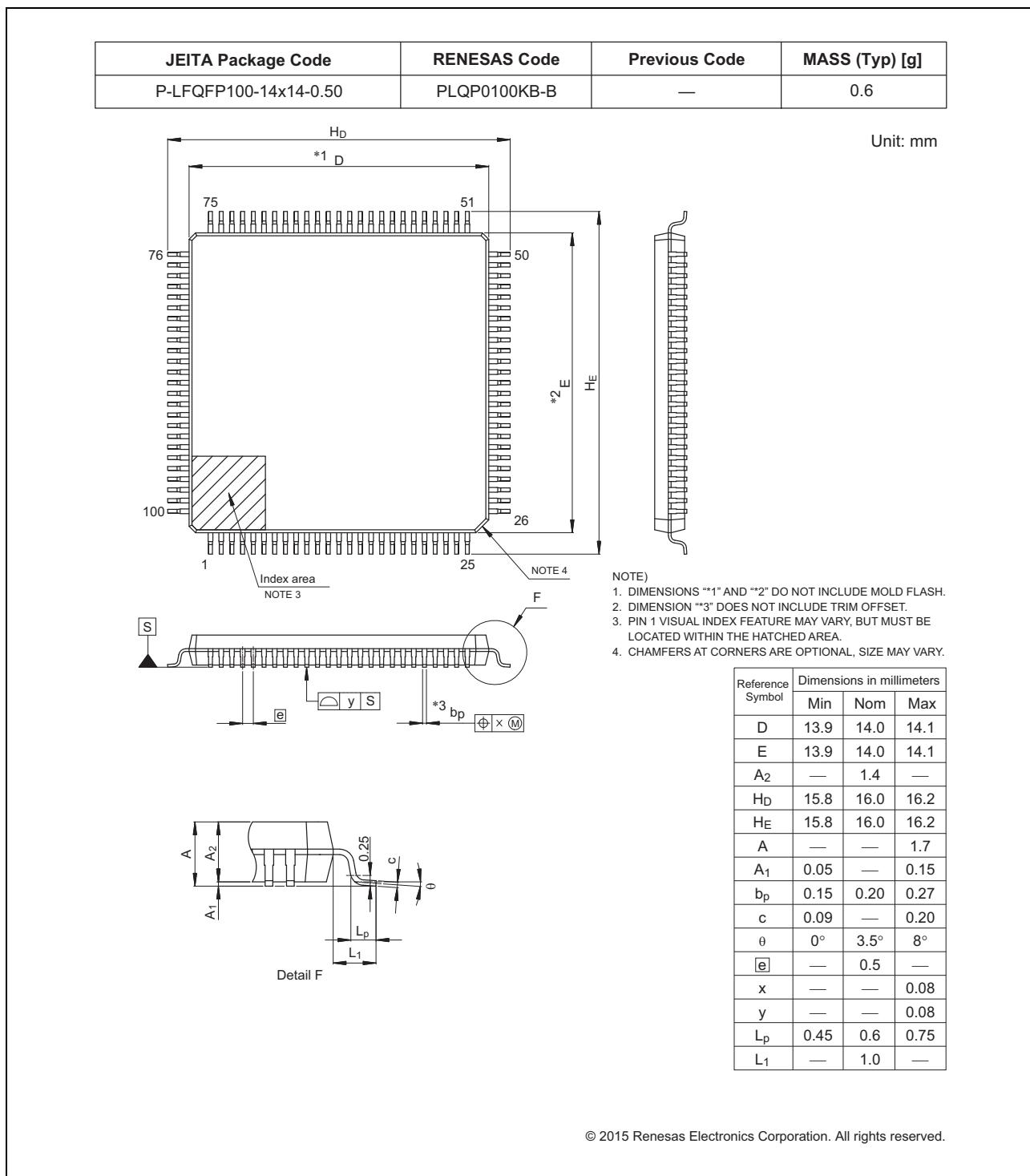


Figure 1.3 145-pin LGA

**Figure 1.4 144-pin LQFP**

**Figure 1.5** 100-pin LQFP

Revision History		S5D9 Microcontroller Group Datasheet
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Rev.	Date	Summary
1.00	Feb 23, 2016	1st release
1.10	Mar 23, 2018	Updated for 1.10
1.20	Aug 10, 2018	Updated for 1.20

Website and Support

Visit the following vanity URLs to learn about key elements of the Synergy Platform, download components and related documentation, and get support.

Synergy Software	renesassynergy.com/software
Synergy Software Package	renesassynergy.com/ssp
Software add-ons	renesassynergy.com/addons
Software glossary	renesassynergy.com/softwareglossary
Development tools	renesassynergy.com/tools
Synergy Hardware	renesassynergy.com/hardware
Microcontrollers	renesassynergy.com/mcus
MCU glossary	renesassynergy.com/mcuglossary
Parametric search	renesassynergy.com/parametric
Kits	renesassynergy.com/kits
Synergy Solutions Gallery	renesassynergy.com/solutionsgallery
Partner projects	renesassynergy.com/partnerprojects
Application projects	renesassynergy.com/applicationprojects
Self-service support resources:	
Documentation	renesassynergy.com/docs
Knowledgebase	renesassynergy.com/knowledgebase
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S5D9 Microcontroller Group Datasheet

Publication Date: Rev.1.20 Aug 10, 2018

Published by: Renesas Electronics Corporation

General Precautions

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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